

CITATION REPORT

List of articles citing

GaAs, AlAs, and Al_xGa_{1-x}As: Material parameters for use in research and device applications

DOI: 10.1063/1.336070

Journal of Applied Physics, 1985, 58, R1-R29.

Source: <https://exaly.com/paper-pdf/17922381/citation-report.pdf>

Version: 2024-04-27

This report has been generated based on the citations recorded by exaly.com for the above article. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

#	Paper	IF	Citations
2349	Barrier-width dependence of optical transitions involving unconfined energy states in GaAs-Al _x Ga _{1-x} As superlattices. 1986 , 34, 8958-8962		40
2348	Lattice mismatch and band offsets in strained layers. <i>Journal of Applied Physics</i> , 1986 , 60, 2893-2896	2.5	6
2347	Self-consistent energy bands and formation energy of the (GaAs) ₁ (AlAs) ₁ (001) superlattice. 1986 , 34, 5280-5286		77
2346	Photoluminescence in the band crossover region of Al _x Ga _{1-x} As. 1986 , 4, 229-231		
2345	Variable Angle of Incidence Spectroscopic Ellipsometric Measurement of the Franz-Keloysh Effect in Modfet Structures. 1986 , 77, 761		6
2344	Theory of the doped quantum well APD in the GaAs/AlGaAs and GaInAs/AlInAs material systems. 1986 , 2, 349-355		1
2343	Photoreflectance spectroscopy of GaAs?Al _x Ga _{1-x} As quantum wells under hydrostatic pressure. 1986 , 2, 569-573		14
2342	Indirect band-gap tunnelling through a (100) GaAs/AlAs/GaAs heterostructure. 1986 , 1, 320-326		21
2341	Orbital mismatch in semiconductor quantum wells. 1986 , 19, 3885-3893		2
2340	Effects of DX center and spatial distribution of electrons on the density of two-dimensional electron gas in modulation-doped AlGaAs/GaAs heterojunction structure. <i>Journal of Applied Physics</i> , 1986 , 60, 3789-3791	2.5	3
2339	Neutral impurity scattering in AlGaAs. 1986 , 48, 1144-1146		11
2338	Be-ion implantation in Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1986 , 60, 2814-2819	2.5	10
2337	Theory of high-field transport of holes in Al _{0.45} Ga _{0.55} As. <i>Journal of Applied Physics</i> , 1986 , 59, 964-966	2.5	12
2336	Picosecond time-of-flight measurements of minority electrons in GaAs/AlGaAs quantum well structures. 1986 , 48, 148-150		45
2335	Optical characterization of InGaAs-InAlAs strained-layer superlattices grown by molecular beam epitaxy. 1986 , 49, 794-796		34
2334	High-pressure studies of GaAs-Ga _{1-x} Al _x As quantum wells of widths 26 to 150 Å. 1986 , 33, 8416-8423		167
2333	Nucleation and initial growth of GaAs on Si substrate. 1986 , 49, 1764-1766		29

2332	Light-heavy-hole mixing in quantum well structures. <i>Journal of Applied Physics</i> , 1986 , 60, 445-447	2.5	3
2331	The effect of complex band structure and non-parabolicity on sub-bands of GaAs-Al _x Ga _{1-x} As heterostructures: band offset. 1987 , 20, 5125-5134		7
2330	Excitation Intensity Dependence of Ga _{1-x} Al _x As-GaAs-Superlattice Photoluminescence. 1987 , 35, 76-78		7
2329	Band bowing in semiconductor alloys and superlattices. 1987 , 2, 255-260		4
2328	Evidence for the role of the indirect-gap electron states in tunnelling through thin AlAs barriers. 1987 , 2, 244-247		18
2327	Coupled intra- and intersubband plasmon-phonon modes in double heterostructures. 1987 , 35, 5887-5890		41
2326	Theory of the surface acoustic soliton. IV. Superlattices. 1987 , 35, 1294-1299		14
2325	Effective electron-density variation and atomic configuration of Al in Al _x Ga _{1-x} As. 1987 , 35, 3799-3803		9
2324	Spectral photoconductivity in n-modulation-doped GaAs/AlGaAs quantum well structures. 1987 , 51, 106-108		14
2323	Thermal conversion of Al _x Ga _{1-x} As layers grown by molecular beam epitaxy. 1987 , 51, 1265-1267		7
2322	Experimental determination of hot-carrier scattering processes in Al _x Ga _{1-x} As. 1987 , 51, 605-607		48
2321	Use of the R-matrix propagation technique to calculate the electronic energy levels of aperiodic structures: Application to an AlAs/GaAs quasiperiodic superlattice. <i>Journal of Applied Physics</i> , 1987 , 62, 3237-3240	2.5	1
2320	Above barrier doublets in GaAs/Al _x Ga _{1-x} As superlattices. 1987 , 50, 1269-1271		24
2319	Ellipsometric analysis of built-in electric fields in semiconductor heterostructures. 1987 , 51, 770-772		14
2318	Measurement of conduction band offsets in Ga _{0.94} Al _{0.06} As:Ga _{0.57} Al _{0.43} As heterojunctions by electrochemical C-V profiling. <i>Journal of Applied Physics</i> , 1987 , 62, 4926-4928	2.5	6
2317	Coupled-mode stop bands of acoustic phonons in semiconductor superlattices. 1987 , 35, 2528-2531		62
2316	Resonant tunneling diodes with AlAs barrier: Guides for improving room-temperature operation. <i>Journal of Applied Physics</i> , 1987 , 62, 3474-3476	2.5	8
2315	Tight-binding studies of Ga _{1-x} Al _x As. 1987 , 35, 2988-2990		12

2314	Investigation of GaAs/Al _x Ga _{1-x} As and In _y Ga _{1-y} As/GaAs superlattices on Si substrates. 1987 , 50, 1748-1750		8
2313	Resonant Raman scattering by LO phonons in Al _x Ga _{1-x} As (x 1987, 35, 8030-8041		41
2312	Modification of dopant profiles due to surface and interface interactions: Applications to semiconductor materials. <i>Journal of Applied Physics</i> , 1987 , 61, 985-992	2.5	4
2311	Self-consistent Monte Carlo study of high-field carrier transport in graded heterostructures. <i>Journal of Applied Physics</i> , 1987 , 62, 3825-3835	2.5	13
2310	Electron interference effects in quantum wells: Observation of bound and resonant states. 1987 , 58, 816-819		86
2309	Electronic optical bistability in a GaAs/AlGaAs strip-loaded waveguide. 1987 , 51, 1209-1211		26
2308	New effects of structure in momentum and real space on nonlinear transport across heterojunction band discontinuities. 1987 , 51, 508-510		5
2307	Imaging of acoustic phonon stop bands in superlattices. 1987 , 58, 2446-2449		52
2306	Multistable quantum systems: Information processing at microscopic levels. 1987 , 58, 1792-1795		30
2305	A new model of deep donor centres in Al _x Ga _{1-x} As. 1987 , 2, 1-13		113
2304	Self-consistent analysis of resonant tunneling in a two-barrier-one-well microstructure. <i>Journal of Applied Physics</i> , 1987 , 62, 2392-2400	2.5	38
2303	Hole subbands in strained GaAs-Ga _{1-x} Al _x As quantum wells: Exact solution of the effective-mass equation. 1987 , 36, 5887-5894		216
2302	Optical evidence of the direct-to-indirect-gap transition in GaAs-AlAs short-period superlattices. 1987 , 35, 6207-6212		200
2301	Resonant tunneling through single layer heterostructures. 1987 , 51, 1019-1021		103
2300	Optical properties of (Al,Ga)As/GaAs multiple quantum well planar waveguides and the fabrication of single-mode rib waveguides and directional couplers by reactive ion etching. 1987 , 26, 2625-30		7
2299	GaAs directional coupler devices: design considerations. 1987 , 26, 4593-6		2
2298	Electronic subbands for Al _x Ga _{1-x} As/GaAs multilayer and superlattice structures. <i>Journal of Applied Physics</i> , 1987 , 61, 294-298	2.5	14
2297	Acoustic-phonon transmission in quasiperiodic superlattices. 1987 , 36, 3491-3494		66

2296	Optical investigation of highly strained InGaAs-GaAs multiple quantum wells. <i>Journal of Applied Physics</i> , 1987 , 62, 3366-3373	2.5	231
2295	Observation of quantum confinement effect away from the zone center in a spectroscopic ellipsometry study of the dielectric function of single Al _{0.3} Ga _{0.7} As/GaAs/Al _{0.3} Ga _{0.7} As square quantum wells. <i>Journal of Applied Physics</i> , 1987 , 61, 2973-2978	2.5	12
2294	Theory of the steady-state hole drift velocity in InGaAs. 1987 , 51, 995-997		18
2293	Deep levels as local probes for the study of superlattices. <i>Journal of Applied Physics</i> , 1987 , 62, 3772-3777	2.5	14
2292	Lateral- and Thickness-Field Coupling in Zincblende Structures. 1987 ,		2
2291	New formalism of the Kronig-Penney model with application to superlattices. 1987 , 36, 3237-3242		96
2290	Quantum-confined Stark effect in graded-gap quantum wells. <i>Journal of Applied Physics</i> , 1987 , 62, 3360-3365		54
2289	Manganese luminescence in AlGaAs-alloys and AlGaAs/GaAs quantum wells. 1987 , 61, 423-426		7
2288	Theoretical Analysis of the Carrier Effective Mass in Inversion Layers on II-VI Semiconductors. 1987 , 139, K25-K30		17
2287	Dynamical Screening, Collective Excitations, and Electron-Phonon Interaction in Heterostructures and Semiconductor Quantum Wells. Application to Double Heterostructures. 1987 , 141, 129-150		143
2286	Electron-Phonon Interaction in Semi-Infinite Semiconductor Superlattices. 1987 , 141, 493-505		30
2285	Electron-Phonon Interaction in Semiconductor Superlattices. 1987 , 143, 487-510		75
2284	Properties of red light-emitting (Al, Ga)As single-heterostructure diodes. II. Luminescence, injection, and photoeffect efficiencies. 1987 , 100, 369-377		5
2283	Optical properties of AlAs. 1987 , 61, 157-160		56
2282	Damping of polaritons in finite semiconductor superlattices. 1987 , 61, 341-346		14
2281	Indirect gap resonant tunneling in GaAs/AlAs. 1987 , 64, 283-286		13
2280	Thermally induced phenomena in Ga _{1-x} Al _x As optical filters. 1987 , 146, L41-L44		1
2279	Band offsets and zone-folding in GaAs/AlAs (001) superlattices. 1987 , 3, 121-126		13

2278	Polynomial kinetic energy approximation for direct-indirect heterostructures. 1987 , 3, 167-169	4
2277	Image force effects in heterostructures and quantum wells. 1987 , 3, 95-98	8
2276	Effective-mass Hamiltonian for abrupt heterojunctions. 1987 , 3, 413-415	19
2275	Transmission and photoreflectance spectra in highly strained InGaAs-GaAs multiple quantum wells. 1987 , 3, 539-545	36
2274	Infra-red transmission spectroscopy of GaAs during molecular beam epitaxy. 1987 , 81, 38-42	55
2273	. 1988 , 35, 570-577	64
2272	. 1988 , 35, 1232-1240	23
2271	Electroreflectance and photoreflectance measurements of GaAs/AlAs short period superlattices. 1988 , 67, 859-862	6
2270	Current noise in N-type Al _x Ga _{1-x} As. 1988 , 31, 279-282	21
2269	Photoreflectance characterization of OMVPE GaAs on Si. 1988 , 93, 481-486	42
2268	Crosstie overlay slow-wave structure for broadband traveling-wave type electro-optical modulators. 1988 , 9, 87-99	4
2267	Multi-quantum-well structures prepared by the flash evaporation technique. Growth, structural, and optical characterization. 1988 , 108, 257-264	3
2266	Photoacoustic spectroscopy of CdTe and (Hg, Cd)Te. 1988 , 108, 443-447	6
2265	Calculation of the C ₁₁ profiles of graded heterojunctions. 1988 , 108, 813-820	3
2264	The Quantum Corrections to the Conductivity in Strong Spin-Orbit Coupling Semiconductors. 1988 , 149, 649-655	1
2263	On the effective electron mass in ternary semiconductors in the presence of crossed electric and magnetic fields. 1988 , 131, 529-532	26
2262	Miniband dispersion of the confined and unconfined states of coupled multiple quantum wells. 1988 , 65, 929-934	13
2261	Anomalous conduction band density of states in Al _x Ga _{1-x} As alloys. 1988 , 68, 295-299	1

2260	Ensemble Monte Carlo simulation of semiclassical nonlinear electron transport across heterojunction band discontinuities. 1988 , 31, 877-885	6
2259	Persistent photoconductivity in free-standing layers of n-AlGaAs. 1988 , 31, 1123-1125	1
2258	Simulations of nonlinear transport in AlGaAs/GaAs single well heterostructures. 1988 , 31, 349-350	
2257	Energy and spin polarization analysis of near band gap photoemission in AlGaAs/GaAs heterostructures. 1988 , 31, 489-492	4
2256	Thermodynamic analysis of the molecular beam epitaxy of AlInAs alloys. 1988 , 88, 282-290	29
2255	Deformation potential LO-phonon Raman scattering near the EO-gap in Al _x Ga _{1-x} As-alloy. Excitonic effects. 1988 , 67, 459-463	6
2254	Magneto-optical studies of GaAs/AlAs quantum wells. 1988 , 4, 147-151	8
2253	Intersubband transition in quantum wells and triple-barrier diode infrared detector concepts. 1988 , 4, 343-349	14
2252	Band offsets, Fermi levels and impurity bands in doped contact layers. 1988 , 4, 705-707	2
2251	A novel asymmetrically coupled quantum well infrared modulator. 1988 , 4, 737-739	5
2250	Photoreflectance, Raman scattering, photoluminescence and transmission electron microscopy of MOCVD multiple quantum wells. 1988 , 4, 609-617	2
2249	Quantum wells and deep impurity levels under hydrostatic pressure. 1988 , 4, 107-114	8
2248	Tunnelling time in microstructures. 1988 , 38, 1260-1267	
2247	Sound velocity and index of refraction of AlAs measured by picosecond ultrasonics. 1988 , 53, 2023-2024	31
2246	Resonant tunneling via Landau levels in GaAs-Ga _{1-x} Al _x As heterostructures. 1988 , 38, 3994-3997	26
2245	Structural and electronic properties of bulk GaAs, bulk AlAs, and the (GaAs) ₁ (AlAs) ₁ superlattice. 1988 , 38, 1970-1977	51
2244	. 1988 , 35, 871-878	63
2243	Acoustic-phonon propagation in superlattices. 1988 , 38, 1427-1449	141

2242	Pseudomorphic In _{0.53} Ga _{0.47} As/AlAs/InAs resonant tunneling diodes with peak-to-valley current ratios of 30 at room temperature. 1988 , 53, 1545-1547		159
2241	Acoustic phonons in multiconstituent superlattices. 1988 , 38, 5610-5614		24
2240	Properties of the optical transitions within the Mn acceptor in Al _x Ga. 1988 , 37, 10111-10117		19
2239	Stationary nonlinear surface waves and their stability in diffusive Kerr media. 1988 , 13, 690		31
2238	Valence and conduction band molecular-orbital topologies and the optical and electrical properties of gallium arsenide and silicon. 1988 , 105, 101-106		2
2237	Femtosecond intervalley scattering in GaAs. 1988 , 53, 2089-2090		112
2236	Mode-Controlled Semiconductor Lasers. 1988 , 211-315		6
2235	Semiconductor Integrated Optic Devices. 1988 , 317-395		2
2234	Reflectance line shapes from GaAs/Ga _{1-x} Al _x As quantum well structures. 1988 , 52, 287-289		86
2233	Theoretical study of the effective electron mass in ternary chalcopyrite semiconductors in the presence of crossed electric and magnetic fields. 1988 , 69, 471-479		32
2232	Continuous transition from multiple quantum-well regime to superlattice regime in GaAlAs/GaAs system as observed by spectroscopic ellipsometry with high lateral resolution. <i>Journal of Applied Physics</i> , 1988 , 63, 465-474	2.5	18
2231	Acoustic interface waves in sandwich structures. 1988 , 206, 203-224		29
2230	. 1988 , 24, 737-749		13
2229	. 1988 , 24, 2017-2033		30
2228	. 1988 , 24, 2191-2214		155
2227	Optical properties of Al _x Ga _{1-x} As alloys. 1988 , 38, 12345-12352		111
2226	Room-temperature switching and negative differential resistance in the heterostructure hot-electron diode. 1988 , 53, 1623-1625		24
2225	Long-lived resonance states in n-doped AlGaAs. 1988 , 60, 2410-2413		28

2224	GaAs/AlGaAs optical waveguides on silicon substrates grown by molecular beam epitaxy. 1988 , 53, 1586-1587	6
2223	Si-ion implantation in GaAs and Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1988 , 63, 64-67	2.5 14
2222	Local valence-band densities of states of Al _x Ga _{1-x} As. 1988 , 38, 13277-13281	16
2221	Photoreflectance study of narrow-well strained-layer In _x Ga _{1-x} As/GaAs coupled multiple-quantum-well structures. 1988 , 38, 3375-3382	181
2220	High-pressure studies of GaAs-Al _x Ga _{1-x} As quantum wells at 300 and 80 K using photoreflectance spectroscopy. 1988 , 38, 9790-9796	17
2219	Structural basis of multistationary quantum systems. I. Effective single-particle dynamics. 1988 , 37, 8096-8110	45
2218	Angular dependence of phonon transmission through a Fibonacci superlattice. 1988 , 37, 8829-8836	52
2217	Photoluminescence and photoconductivity measurements on band-edge offsets in strained molecular-beam-epitaxy-grown In _x Ga. 1988 , 37, 4032-4038	107
2216	Multivalley single-band model for above-barrier optical transitions in arbitrarily shaped superlattices. 1988 , 38, 9667-9673	1
2215	Temperature dependence of the quantized states in a GaAs-Ga _{1-x} Al _x As superlattice. 1988 , 37, 1035-1038	27
2214	Abrupt interface AlGaAs/GaAs heterojunction bipolar transistors: Carrier heating and junction characteristics. <i>Journal of Applied Physics</i> , 1988 , 63, 809-820	2.5 24
2213	Photoreflectance, absorption, and nuclear resonance reaction studies of Al _x Ga _{1-x} As grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1988 , 63, 5447-5453	2.5 36
2212	Resonant Raman study of the LO-phonon energy fluctuation in III-V alloy semiconductors. 1988 , 37, 6393-6396	7
2211	Evidence of phonon drag in the thermopower of a GaAs-Ga _{0.68} Al. 1988 , 37, 3137-3140	45
2210	Theoretical investigation of hole transport in strained III-V semiconductors: Application to GaAs. 1988 , 53, 785-787	18
2209	Luminescence properties of (GaAs) _l (AlAs) _m superlattices with (l,m) ranging from 1 to 73. <i>Journal of Applied Physics</i> , 1988 , 63, 845-852	2.5 47
2208	Semiconductor superlattice electron wave interference filters. 1988 , 53, 2047-2049	20
2207	Resonant tunneling and negative differential resistance in a variably spaced superlattice energy filter. 1988 , 52, 132-134	22

2206	Two-step barrier diodes. 1988 , 52, 960-962		20
2205	Distribution of atoms in mixed III-V compounds. <i>Journal of Applied Physics</i> , 1988 , 63, 966-968	2.5	11
2204	Vibrational excitations in a-Si _{1-x} Gex:F, a-Si _{1-x} Gex:H, and Ga _{1-x} Al _x As alloys. 1988 , 37, 10729-10737		3
2203	.		3
2202	A novel superlattice infrared source. <i>Journal of Applied Physics</i> , 1988 , 63, 2856-2858	2.5	33
2201	Simple analytic model for heterojunction band offsets. 1988 , 37, 7112-7114		91
2200	Influence of broad Ga _{1/2} Al _{1/2} As interfaces on the dispersion of the interface modes in binary GaAs/AlAs superlattices. <i>Journal of Applied Physics</i> , 1988 , 64, 6806-6809	2.5	
2199	Theory of the velocity-field relation in AlGaAs. <i>Journal of Applied Physics</i> , 1988 , 63, 5004-5008	2.5	66
2198	Acoustic-wave transmission in semiconductor superlattices. 1988 , 38, 7717-7722		5
2197	Direct evidence of the DX center link to the L-conduction-band minimum in GaAlAs. 1988 , 52, 383-385		60
2196	Optical Spectroscopy of Condensed Phase Interfaces. 1988 , 24, 189-257		2
2195	Structured-base hot-electron transistors. I. Scattering rates. 1988 , 3, 101-110		19
2194	On the optimisation of bound electron concentration in a semiconductor quantum well. 1988 , 3, 675-679		5
2193	A search for trends in the thermopower of GaAs-Ga _{1-x} Al _x As heterojunctions. 1988 , 21, 2681-2694		29
2192	Sub-band energies of highly strained InGaAs-GaAs quantum wells. 1988 , 3, 597-600		12
2191	Considerations on geometry design of surface-emitting laser diodes. 1988 , 135, 233		9
2190	Optical Study of Al _x Ga _{1-x} As-AlAs Ternary Alloy Multi-Quantum-Well Structures around Two (γ) Crossovers. 1988 , 57, 4403-4408		10
2189	Reduction of Strain in Epitaxial GaAs on CaF ₂ /Si Substrates. 1988 , 116, 257		4

2188	Strain Relief by Tilting of Epitaxial GaAs Films on Si. 1988 , 130, 171		3
2187	Measurement of the Sound Velocity in AlAs by Picosecond Ultrasonics. 1988 , 130, 59		
2186	Chapter 3: Deep Levels in 111-V Compound Semiconductors Grown by Molecular Beam Epitaxy. 1988 , 26, 143-228		
2185	Optical properties of In _{1-x} Ga _x As _y P _{1-y} alloys. 1989 , 39, 12612-12621		67
2184	Electron trapping by metastable effective-mass states of DX donors in indirect-band-gap Al _x Ga _{1-x} As:Te. 1989 , 40, 9671-9682		67
2183	Quantum-well states under biaxial compression and tension. 1989 , 40, 3077-3080		13
2182	Band X-state influences on resonant tunneling current in single- and double-barrier GaAs/AlAs structures. 1989 , 54, 1341-1343		35
2181	Folded-acoustic phonons in GaAs/AlAs thin-layer superlattices under high pressure. 1989 , 40, 2988-2991		10
2180	Band X-band contributions to nonresonant tunneling in GaAs/Al _{0.35} Ga _{0.65} As double quantum wells. 1989 , 55, 2517-2519		24
2179	Semiconductor superlattice interference filter design. <i>Journal of Applied Physics</i> , 1989 , 65, 2535-2540	2.5	36
2178	. 1989 , 36, 2394-2404		15
2177	Observation and characterization of deep donor centers (DX centers) in Si-doped AlAs. <i>Journal of Applied Physics</i> , 1989 , 66, 3042-3046	2.5	14
2176	. 1989 , 7, 1044-1054		23
2175	Epitaxial CoGa and textured CoAs contacts on Ga _{1-x} Al _x As fabricated by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1989 , 65, 4753-4758	2.5	54
2174	Correspondence between the dependence of frequencies and intensities of GaAs and AlAs longitudinal-optical modes on the photon energy in a thin-layer GaAs-AlAs superlattice. 1989 , 39, 1703-1707		
2173	Absorptive electro-optic spatial light modulators: Effect of well profile on device performance. 1989 , 55, 930-932		5
2172	Uniaxial stress dependence of current-voltage characteristics in GaAs-Al _x Ga _{1-x} As-GaAs heterojunction barriers. 1989 , 55, 1336-1338		10
2171	Electron tunneling time measured by photoluminescence excitation correlation spectroscopy. 1989 , 54, 552-554		74

2170	First-principles calculation of the elastic constants of AlAs. 1989 , 40, 11934-11936		42
2169	Interlayer Gamma -X scattering in staggered-alignment Al _{0.34} Ga _{0.66} As-AlAs ternary alloy multiple-quantum-well structures. 1989 , 40, 8581-8584		25
2168	Theoretical comparison of electron real-space transfer in classical and quantum two-dimensional heterostructure systems. <i>Journal of Applied Physics</i> , 1989 , 65, 1156-1163	2.5	35
2167	Hole tunneling times in GaAs/AlAs double-barrier structures. 1989 , 55, 744-746		41
2166	Electrical behavior of a static hole inversion layer at the i-AlAs/n-GaAs heterojunction. <i>Journal of Applied Physics</i> , 1989 , 65, 3118-3126	2.5	4
2165	A combined single-phonon Raman and photoluminescence study of direct and indirect band-gap Al _x Ga _{1-x} As alloys grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1989 , 65, 1676-1682	2.5	14
2164	Transverse magnetotunneling in Al _x Ga _{1-x} As capacitors. II. Electron phase changes in resonant Fowler-Nordheim tunneling. 1989 , 40, 11683-11692		6
2163	Observation of single-optical-phonon emission. 1989 , 62, 1057-1060		48
2162	Resonant-tunneling lifetime comparison between double-barrier and delta -doped barrier structures. 1989 , 39, 8739-8742		33
2161	A high-gain (Ga,Al)As/GaAs heterostructure bipolar transistor with an equilibrium-depleted spike-doped base. 1989 , 10, 168-170		3
2160	Resonant Raman scattering by LO phonons in Al _x Ga _{1-x} As (0.2. 1989 , 40, 1238-1243		16
2159	Photocurrent spectroscopy of In _x Ga _{1-x} As/GaAs multiple quantum wells. 1989 , 54, 2230-2232		28
2158	Effect of alloy disorder on the vibrational spectrum of silicon donors in Al _x Ga _{1-x} As. 1989 , 40, 9779-9789		18
2157	Intraband absorption of infrared radiation in a semiconductor quantum dot. 1989 , 39, 7982-7984		31
2156	Laser fabricated GaAs waveguiding structures. 1989 , 54, 1839-1841		25
2155	Effect of Al mole fraction on carrier diffusion lengths and lifetimes in Al _x Ga _{1-x} As. 1989 , 55, 2622-2624		44
2154	Al _x Ga _{1-x} As band-edge dependence on alloy composition. 1989 , 40, 6417-6419		12
2153	Spin-polarized photoemission from AlGaAs/GaAs heterojunction: A convenient highly polarized electron source. 1989 , 54, 632-634		29

2152	Effect of biaxial strain on exciton transitions of Al _x Ga _{1-x} As epitaxial layers on (001) GaAs substrates. <i>Journal of Applied Physics</i> , 1989 , 66, 2108-2113	2.5	13
2151	Quasiclassical behavior of ballistic electrons in a perpendicular magnetic field. 1989 , 39, 12981-12984		7
2150	Analysis of the shallow and deep center occupancies in Si-doped Al _x Ga _{1-x} As using a multilevel donor model. <i>Journal of Applied Physics</i> , 1989 , 66, 4269-4274	2.5	13
2149	Subband structures of GaAs/Al _x Ga _{1-x} As multiple quantum wells. 1989 , 40, 8349-8356		26
2148	Surface acoustic wave properties of aluminum gallium arsenide. <i>Journal of Applied Physics</i> , 1989 , 66, 90-96	2.5	5
2147	Minority carrier lifetime and efficiency in single heterostructure AlGaAs red light emitting diodes. 1989 , 67, 853-864		3
2146	Negative U, acceptor-like, D model of the DX centre: transport properties of weakly doped Al _x Ga _{1-x} As. 1989 , 4, 579-581		9
2145	Two-dimensional electrons at a GaAs-AlAs heterojunction under hydrostatic pressure. 1989 , 4, 317-321		4
2144	High-pressure studies of resonant tunnelling in a graded parameter superlattice and in double barrier structures of GaAs/AlAs. 1989 , 4, 754-764		22
2143	Charge confinement in ultrathin GaAs/AlAs superlattices. 1989 , 4, 765-772		
2142	Photoluminescence of Zn-doped Al _x Ga _{1-x} As. 1989 , 4, 1159-1166		13
2141	Resonant-tunneling effects in a parabolic quantum well obtained by application of crossed magnetic and electric fields in a semiconductor quantum barrier. 1989 , 39, 8760-8763		8
2140	Epitaxial layer thickness measurements by reflection spectroscopy. 1989 , 18, 361-367		25
2139	. 1989 , 36, 289-299		11
2138	. 1989 , 36, 309-313		11
2137	. 1989 , 36, 1254-1263		25
2136	Infrared optical characterization of epitaxial layer / substrate systems (II). Experimental results for Al _x Ga _{1-x} As/GaAs. 1989 , 24, 909-919		4
2135	Band offset in GaAlAs and InGaAs: InP heterojunctions by electrochemical CV profiling. 1989 , 5, 507-510		6

2134	Strain-relief mechanisms and nature of misfit dislocations in GaAs/Si heterostructures. 1989 , 113, 57-63	10
2133	Critical thickness during three-dimensional epitaxial growth—self-consistent approach. 1989 , 113, 65-73	9
2132	Effect of magnetic quantization on the effective electron mass in n-Ge. 1989 , 32, 515-516	17
2131	Heterostructure semiconductor device analysis: A globally convergent solution method for the nonlinear poisson equation. 1989 , 32, 369-376	7
2130	On the effective electron mass in N-channel inversion layers of Ge. 1989 , 32, 177-178	33
2129	Femtosecond electron and hole thermalisation in AlGaAs. 1989 , 32, 1173-1177	36
2128	The effect of the X conduction band minima on resonant tunnelling and charge build-up in double barrier structures based on n-GaAs/(AlGa)As. 1989 , 32, 1731-1735	16
2127	GaAs/Ga _{1-x} Al _x As Bragg reflectors at absorption wavelengths. 1989 , 71, 129-132	1
2126	Reduction of strain in GaAs grown on CaF ₂ /Si heteroepitaxial substrates. 1989 , 95, 403-404	1
2125	Characterization of MOCVD Grown (Al, Ga)As/GaAs Single Quantum Well Structures by Rutherford Backscattering and Photoluminescence Spectroscopy. 1989 , 111, 541-550	6
2124	On the Effective Electron Mass in n-Channel Inversion Layers on Ternary Semiconductors in the Presence of a Parallel Magnetic Field. 1989 , 151, K135-K140	17
2123	Long-Wavelength Optical Phonons in GaAs/AlAs Superlattices. 1989 , 154, 565-582	30
2122	2.1.29 References for 2.1. 103-112	
2121	Resonant acousto-optical interaction in superlattices. 1989 , 55, 2292-2294	14
2120	Tunneling through AlAs barriers: \hbar transfer current. 1989 , 54, 1784-1786	66
2119	Optical investigations on the mobility of two-dimensional excitons in GaAs/Ga _{1-x} Al _x As quantum wells. 1989 , 39, 10901-10912	165
2118	Acoustic attenuation and optical-absorption effects on light scattering by acoustic phonons in superlattices. 1989 , 40, 1121-1129	15
2117	Modeling of riblike waveguides with isolation trenches of finite width. 1989 , 28, 5203-6	2

2116	Calculation of the electron wave function in a graded-channel double-heterojunction modulation-doped field-effect transistor. 1989 , 55, 1223-1225		4
2115	Diamagnetism as a probe of exciton localization in quantum wells. 1989 , 39, 10943-10954		42
2114	The X-valley transport in GaAs/AlAs triple barrier structures. <i>Journal of Applied Physics</i> , 1989 , 65, 5199-5201		9
2113	Optical dispersion relations for GaP, GaAs, GaSb, InP, InAs, InSb, Al _x Ga _{1-x} As, and In _{1-x} Ga _x AsyP _{1-y} . <i>Journal of Applied Physics</i> , 1989 , 66, 6030-6040	2.5	389
2112	Raman microprobe analysis of strain induced by patterned dielectric films of GaAlAs structures. 1989 , 25, 989-992		9
2111	Observation of extremely large quadratic susceptibility at 9.6-10.8 microm in electric-field-biased AlGaAs quantum wells. 1989 , 62, 1041-1044		318
2110	Order of the X conduction-band valleys in type-II GaAs/AlAs quantum wells. 1989 , 39, 13426-13433		145
2109	On the mechanisms of strain release in molecular-beam-epitaxy-grown In _x Ga _{1-x} As/GaAs single heterostructures. <i>Journal of Applied Physics</i> , 1989 , 66, 1975-1983	2.5	106
2108	.		2
2107	Direct determination of the ambipolar diffusion length in GaAs/AlGaAs heterostructures by cathodoluminescence. 1989 , 55, 1647-1649		58
2106	. 1989 , 36, 118-123		6
2105	Charge Carrier Recombination in AlGaAs Studied by Time-Resolved Microwave Conductivity Experiments. 1989 , 145, 481		
2104	Strain in Epitaxial GaAs on CaF ₂ /Si(111). 1989 , 160, 527		
2103	Magneto-Optical Studies of GaAs-AlGaAs Modulation Doped Quantum Wells Under Hydrostatic Pressure. 1989 , 160, 697		
2102	High Pressure Optical Studies of GaSb-AlSb Multiple Quantum Wells. 1989 , 160, 751		
2101	Theory of electronic transport in two-dimensional Ga _{0.85} In _{0.15} As/Al _{0.15} Ga _{0.85} As pseudomorphic structures. <i>Journal of Applied Physics</i> , 1989 , 65, 1615-1620	2.5	26
2100	A New Approach to Grow Strain-Free GaAs on Si. 1990 , 202, 609		1
2099	Selfconsistent Study of Coherent Tunneling Through a Double Barrier Structure. 1990 , T33, 219-226		8

2098	. 1990 , 37, 1245-1252	13
2097	Theoretical analysis of the effective electron mass in channel inversion layers on ternary semiconductors. 1990 , 67, 163-170	
2096	On the effective electron mass in quantum well wires of ternary chalcopyrite semiconductors. 1990 , 12, 891-900	14
2095	Epitaxial layer thickness measurements using Fourier Transform Infrared Spectroscopy (FTIR). 1990 , 19, 181-185	4
2094	Molecular beam epitaxy and characterization of $\text{Al}_x\text{Ga}_{1-x}\text{As}_y\text{Sb}_{1-y}$ ($0.0 \leq x \leq 1.0$) lattice matched to InAs substrates. 1990 , 19, 989-993	7
2093	A new algorithm for layer thickness and index step estimation in multi-layer hetero-epitaxial structures. 1990 , 19, 1383-1394	17
2092	. 1990 , 26, 2025-2035	165
2091	Investigation of Excess Carrier Diffusion in $\text{Ga}_{0.35}\text{Al}_{0.65}\text{As}$ by Cathodoluminescence. 1990 , 117, 485-494	2
2090	On the Concentration and Composition Dependence of the Acceptor Energy in $\text{Al}_x\text{Ga}_{1-x}\text{As}:\text{Ge}$ ($x \leq 0.40$). 1990 , 119, K135-K139	3
2089	Investigation of the effect of composition fluctuations on the parameters of variband light-emitting diodes of $\text{Al}_x\text{Ga}_{1-x}\text{As}(\text{Si}):\text{GaAs}$ structures by the method of numerical simulation. 1990 , 53, 877-880	
2088	Spectra of pre-breakdown electroluminescence of diode structures. 1990 , 53, 1037-1040	
2087	Deep levels in $\text{GaAs}/\text{AlGaAs}$ multi-quantum well structures. 1990 , 1, 75-78	
2086	Temperature dependence of persistent photo-conductivity due to DX centers in $\text{Al}_x\text{Ga}_{1-x}\text{As}:\text{Si}$. 1990 , 50, 515-517	7
2085	Ballistic-electron-emission microscopy of subsurface defects at the $\text{Au-GaAs}(100)$ interface. 1990 , 41-42, 17-24	6
2084	Role of carrier equilibrium in self-consistent calculations for double barrier resonant diodes. 1990 , 7, 17-21	20
2083	Coupled Γ electronic states in AlAs/GaAs quantum well structures. 1990 , 7, 35-38	13
2082	High pressure behavior of electronic states in $\text{GaAs}/\text{Ga}_{1-x}\text{Al}_x\text{As}$ multiple quantum wells. 1990 , 7, 175-178	2
2081	The temperature dependence of intersubband absorption in a barrier-doped $\text{GaAs}/\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ quantum well structure. 1990 , 8, 63-67	5

2080	Photoluminescence study of double barrier resonant tunneling diodes grown by metalorganic vapour phase epitaxy. 1990 , 8, 467-474	2
2079	Electronic structure of semiconductor quantum dots: Interband transitions and selection rules. 1990 , 8, 475-480	1
2078	Electron-phonon interaction, dynamical screening and collective excitations in heterostructures. 1990 , 167, 91-99	31
2077	Structural characterization of AlGaAs/GaAs multiquantum-well structures grown on silicon. 1990 , 184, 429-436	
2076	Strain relief of large lattice mismatch heteroepitaxial films on silicon by tilting. 1990 , 184, 437-445	27
2075	On the linewidth of Γ and X-valley intersubband optical transitions in semiconductor quantum wells. 1990 , 73, 421-424	3
2074	Electronic structure of (1 1 3)-grown GaAs-(GaAl)As single quantum wells under biaxial strain fields. 1990 , 75, 677-682	14
2073	Resonant tunnelling between X-levels in a GaAs/AlAs/GaAs/AlAs/GaAs device above 13 kbar. 1990 , 75, 697-702	12
2072	Mn impurity in Al _x Ga _{1-x} As/GaAs and heterojunction band lineup. 1990 , 76, 479-481	5
2071	Effect of the dielectric function and pressure on the binding energies of excitons in GaAs and GaAs/Ga _{1-x} Al _x As superlattices. 1990 , 76, 561-564	21
2070	Self-consistent calculation of electron density in a two-channel modulation-doped structure. 1990 , 33, 99-104	10
2069	Dependence of ionization coefficients on well and barrier widths for GaAs/AlGaAs multiple quantum wells. 1990 , 33, 1235-1245	8
2068	A study of base built-in field effects on the steady-state current gain of heterojunction bipolar transistors. 1990 , 33, 845-849	11
2067	Influence of doping dependent bandgap grading on electrical performance and design criteria of npn Al _x Ga _{1-x} As/GaAs abrupt heterojunction bipolar transistors. 1990 , 33, 339-344	7
2066	Power series approximation used in soft threshold lucky drift model of impact ionisation. 1990 , 5, 177-182	9
2065	Modelling of electroabsorption in coupled quantum wells with applications to low voltage optical modulation. 1990 , 5, 516-524	31
2064	A study of the collector-emitter offset voltage of InAlAs/InGaAs and AlGaAs/GaAs heterojunction bipolar transistors. 1990 , 5, 355-357	
2063	Generation-recombination noise in Al _x Ga _{1-x} As: temperature dependence. 1990 , 5, 1030-1039	4

2062	Photoluminescence in GaAs/AlGaAs heterojunction bipolar transistors: An investigation of the properties of the Mg acceptor. <i>Journal of Applied Physics</i> , 1990 , 68, 1310-1317	2.5	6
2061	Effects of wave-function delocalization on the optical properties of GaAs/AlAs short-period asymmetric superlattices. 1990 , 41, 7647-7652		9
2060	High-pressure magneto-optical studies of two-dimensional-electron and exciton transitions in GaAs-Al _x Ga _{1-x} As quantum-well heterostructures. 1990 , 42, 9657-9663		10
2059	Large Stark shifts of the local to global state intersubband transitions in step quantum wells. 1990 , 56, 1986-1988		60
2058	Strain-induced two-dimensional electron gas in [111] growth-axis strained-layer structures. 1990 , 56, 758-760		54
2057	Subpicosecond time-resolved coherent-phonon oscillations in GaAs. 1990 , 65, 764-766		355
2056	Application of a total-angular-momentum basis to quantum-dot band structure. 1990 , 65, 239-242		54
2055	The suppression by pressure of negative differential resistance in GaAs/GaAlAs double barrier structures. <i>Journal of Applied Physics</i> , 1990 , 68, 205-211	2.5	16
2054	Acoustic fields and velocities for surface-acoustic-wave propagation in multilayered structures: An extension of the Laguerre polynomial approach. <i>Journal of Applied Physics</i> , 1990 , 68, 4993-4997	2.5	57
2053	Femtosecond-pump, continuum-probe nonlinear absorption in GaAs. 1990 , 65, 231-234		49
2052	Quantum tunability of superlattice minibands. 1990 , 41, 10021-10027		27
2051	The carrier effects on the change of refractive index for n-type GaAs at \hbar 1.06, 1.3, and 1.55 \hbar . <i>Journal of Applied Physics</i> , 1990 , 67, 1497-1503	2.5	23
2050	Resonant tunneling through Landau levels in quantum wells in the presence of inelastic-scattering broadening. 1990 , 41, 3053-3059		22
2049	Optical constants of Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1990 , 68, 1848-1853	2.5	62
2048	Electron-phonon interaction in ternary mixed crystals. 1990 , 42, 8915-8922		19
2047	Stimulated visible light emission from ultrathin GaAs single and multiple quantum wells sandwiched between indirect-gap (Al _{0.49} Ga _{0.51} As) confining layers. 1990 , 56, 1998-2000		2
2046	Theoretical and experimental study of the longitudinal uniaxial stress dependence of I-V characteristics in GaAs-Al _x Ga _{1-x} As-GaAs heterojunction barriers. <i>Journal of Applied Physics</i> , 1990 , 67, 6360-6367	2.5	10
2045	Measurement of intersubband absorption in multi-quantum well structures with monolithically integrated photodetectors. <i>Journal of Applied Physics</i> , 1990 , 67, 4361-4363	2.5	30

2044	Numerical studies of femtosecond carrier dynamics in GaAs. 1990 , 42, 3423-3434		72
2043	Photoreflectance measurement of strain in epitaxial GaAs on silicon. <i>Journal of Applied Physics</i> , 1990 , 67, 4389-4392	2.5	19
2042	Study of resonant tunneling structures: A hybrid incremental Airy function plane-wave approach. <i>Journal of Applied Physics</i> , 1990 , 67, 3011-3017	2.5	14
2041	Intersubband infrared absorption in a GaAs/Al _{0.3} Ga _{0.7} As quantum well structure. 1990 , 57, 1790-1792		49
2040	Tunneling real-space transfer induced by wave function hybridization in modulation-doped heterostructures. 1990 , 57, 795-797		12
2039	Proximity effect in the collective excitations of the fractional quantum Hall state. 1990 , 42, 3183-3186		3
2038	Pressure dependence of photoluminescence in In _x Ga _{1-x} As/GaAs strained quantum wells. 1990 , 42, 2926-2931		23
2037	Effects of inelastic electron-phonon scattering on the resonant tunneling in double-barrier structure. <i>Journal of Applied Physics</i> , 1990 , 68, 2829-2832	2.5	2
2036	Energy level associated with the DX center in Ga _{1-x} Al _x As. 1990 , 41, 8485-8492		31
2035	One-phonon resonant Raman scattering in Al _x Ga _{1-x} As (0.5. 1990 , 42, 11875-11880		4
2034	Ensemble Monte Carlo characterization of graded Al _x Ga _{1-x} As heterojunction barriers. <i>Journal of Applied Physics</i> , 1990 , 68, 1114-1122	2.5	8
2033	The effect of interface roughness and island scattering on resonant tunneling time. <i>Journal of Applied Physics</i> , 1990 , 67, 593-595	2.5	8
2032	Valley current density activation energy and effective longitudinal optical phonon energy in triple well asymmetric resonant tunneling diode. 1990 , 57, 575-577		3
2031	Electro-optical bistability in strained In _x Ga _{1-x} As/Al _{0.15} Ga _{0.85} As multiple quantum wells. 1990 , 57, 2234-2236		24
2030	Effects of carrier mass differences on the current-voltage characteristics of resonant tunneling structures. 1990 , 56, 1793-1795		30
2029	Epitaxial layer thickness measurement of double heterostructures using reflectance spectroscopy. <i>Journal of Applied Physics</i> , 1990 , 68, 2927-2938	2.5	11
2028	Improved design of AlAs/GaAs resonant tunneling diodes. 1990 , 56, 1676-1678		25
2027	Temperature Dependence of the Linewidth and Peak Position of the Intersubband Infrared Absorption in GaAs/Al _{0.3} Ga _{0.7} As Quantum Wells. 1990 , 216, 341		

2026	Composition analysis of thin Al _x Ga _{1-x} As layers with TEM and SIMS. 1990 , 5, 578-586		15
2025	Photoluminescent Properties of AlAs/Al _x Ga _{1-x} As (x=0.5) Disordered Superlattices. 1990 , 29, L1055-L1058		8
2024	.		
2023	An AlGaAs/In/sub x/Ga/sub 1-x/As/AlGaAs (0. 1990 , 37, 1416-1421		5
2022	E2 interband transitions in Al _x Ga _{1-x} As alloys. 1990 , 41, 2959-2965		32
2021	.		12
2020	Anisotropic polarons near interfaces of polar semiconductors. 1990 , 41, 3572-3577		9
2019	.		2
2018	Evidence for the alloy broadening of the emission and capture rates of the DX center from the frequency dependence of capacitance of Schottky barriers on Al _x Ga _{1-x} As: Si. <i>Journal of Applied Physics</i> , 1990 , 67, 1121-1123	2.5	3
2017	Multicomponent structure in the temperature-dependent persistent photoconductivity due to different DX centers in Al _x Ga _{1-x} As:Si. 1990 , 57, 2225-2227		22
2016	Characterization of GaAs/Ga _{1-x} Al _x As heterojunction bipolar transistor structures using photoreflectance. 1990 , 56, 1278-1280		75
2015	Generalization of Bragg reflector geometry: Application to (Ga,Al)As-(Ca,Sr)F ₂ reflectors. <i>Journal of Applied Physics</i> , 1990 , 68, 5366-5368	2.5	4
2014	On the lifetime broadening of the Ev ₁₀ and Ev ₂₀ excitons in the GaAs/Al _x Ga _{1-x} As alloy system. <i>Journal of Applied Physics</i> , 1990 , 67, 4133-4139	2.5	8
2013	Si impurity-induced layer disordering of Al _x Ga _{1-x} -GaAs quantum-well heterostructures by As-free open-tube rapid thermal annealing. <i>Journal of Applied Physics</i> , 1990 , 68, 6199-6206	2.5	10
2012	Polaron energy and effective mass in a quantum well. 1990 , 42, 11063-11072		96
2011	Monte Carlo simulation of electron-hole thermalization in photoexcited bulk semiconductors. 1990 , 42, 5685-5692		36
2010	Effect of pressure on the low-temperature exciton absorption in GaAs. 1990 , 41, 10111-10119		103
2009	Photoluminescence Properties of GaAs/AlAs Short-Period Superlattices. 1990 , 29, 41-47		46

2008	Avalanche breakdown in p-n AlGaAs/GaAs heterojunctions. <i>Journal of Applied Physics</i> , 1990 , 67, 6917-6923	12
2007	Photoreflectance study of surface Fermi level in GaAs and GaAlAs. 1990 , 57, 2118-2120	119
2006	Line-shape analysis of reflectance spectra from GaAs/AlAs multiple-quantum-well structures. <i>Journal of Applied Physics</i> , 1990 , 67, 2501-2505	2.5 32
2005	. 1990 , 2, 181-183	19
2004	. 1990 , 37, 618-628	19
2003	Resonant-tunneling transfer times between asymmetric GaAs/Al _{0.35} Ga _{0.65} As double quantum wells. 1990 , 41, 12295-12298	59
2002	Calculation of the intersubband absorption strength in ellipsoidal-valley quantum wells. 1990 , 41, 7559-7568	50
2001	Magnetoplasmon-phonon coupling in semiconductor quantum wells. 1990 , 2, 8881-8904	20
2000	Exciton binding energy in type-II heterojunctions. 1990 , 42, 11701-11707	19
1999	Excitonic effects in the optical spectrum of GaAs. 1990 , 41, 1003-1013	79
1998	Effect of layer thickness variations in a distributed-Bragg-reflector mirror on the phase of the reflected light. 1990 , 15, 526-8	6
1997	.	
1996	Fermi-level-pinning-induced impurity redistribution in semiconductors during epitaxial growth. 1990 , 42, 1364-1368	42
1995	Experimental study of the Gamma-X electron transfer in type-II (Al,Ga)As/AlAs superlattices and multiple-quantum-well structures. 1990 , 42, 5809-5821	113
1994	. 1990 , 26, 972-981	17
1993	Photocurrent spectroscopy of strained-layer InGaAs/GaAs multiple quantum wells. 1990 , 228, 351-355	14
1992	Electron tunneling via Landau X-states in GaAs/Al _{0.35} Ga _{0.65} As double quantum well structures. 1990 , 229, 195-198	5
1991	Determination of EX transfer rates in type II (Al)GaAs/AlAs superlattices. 1990 , 229, 452-455	5

1990	Quantum Transport in Semiconductor Nanostructures. 1991 , 1-228		797
1989	. 1991 , 27, 40-45		8
1988	. 1991 , 27, 224-231		18
1987	. 1991 , 27, 232-237		5
1986	. 1991 , 27, 696-701		16
1985	. 1991 , 27, 788-795		27
1984	. 1991 , 27, 804-808		2
1983	. 1991 , 27, 921-930		13
1982	. 1991 , 27, 1182-1188		74
1981	. 1991 , 27, 1886-1899		3
1980	Multiple images theory in superlattices. <i>Journal of Applied Physics</i> , 1991 , 70, 7643-7644	2.5	1
1979	Defect-free growth of Al _x Ga _{1-x} As by liquid-phase epitaxy on V-grooved (001) GaAs substrates. <i>Journal of Applied Physics</i> , 1991 , 69, 8154-8157	2.5	
1978	Calculation of intervalley scattering rates in Al _x Ga _{1-x} As: Effects of alloy and phonon scattering. 1991 , 44, 12761-12768		21
1977	Effective electron mass in ultrathin films of bismuth in the presence of crossed electric and quantizing magnetic fields. 1991 , 70, 343-354		16
1976	Assessment of the performance potential of a quantum resonant tunnelling structure under current density constraint. 1991 , 70, 703-712		
1975	Experimental determination of the X ₆ shear tetragonal deformation potential of AlAs. 1991 , 44, 8312-8314		13
1974	Pd-on-GaAs Schottky Contact: Its Barrier Height and Response to Hydrogen. 1991 , 30, 906-913		48
1973	Acoustic-mode analysis of a homogeneous multilayer guiding structure. 1991 , 8, 443		8

1972	. 1991 , 79, 1643-1659		42
1971	Efficient band-structure calculations of strained quantum wells. 1991 , 43, 9649-9661		311
1970	Change in refractive index for p-type GaAs at \hbar 1.06, 1.3, and 1.55 eV due to free carriers. <i>Journal of Applied Physics</i> , 1991 , 70, 925-929	2.5	9
1969	Exciton binding energy in GaAs/Al _x Ga _{1-x} As multiple quantum wells. 1991 , 43, 12626-12629		13
1968	Direct determination of the electron-tunneling escape time from a GaAs/Al _x Ga _{1-x} As quantum well by transient-capacitance spectroscopy. 1991 , 44, 3157-3161		23
1967	Intersubband absorption and infrared photodetection at 3.5 and 4.2 eV in GaAs quantum wells. 1991 , 58, 2234-2236		89
1966	Deep level transient spectroscopy of DX centres in Al _{0.38} Ga _{0.62} As:Te under uniaxial stress. 1991 , 6, 825-829		5
1965	Raman study of longitudinal optical phonon-plasmon coupling and disorder effects in heavily Be-doped GaAs. <i>Journal of Applied Physics</i> , 1991 , 69, 4064-4070	2.5	59
1964	Donor transition energy in GaAs superlattices in a magnetic field along the growth axis. 1991 , 44, 5692-5702		78
1963	Second-order susceptibility in asymmetric quantum wells and its control by proton bombardment. 1991 , 58, 1724-1726		81
1962	Vibrational excitations in a-A ₁ B _x C alloys. 1991 , 63, 1313-1320		1
1961	Composition measurement by thickness fringe matching: The alloy-system-dependent sensitivity and accuracy of the method. 1991 , 63, 371-387		2
1960	Molecular beam epitaxy GaAs on Si: material and devices for optical interconnects. 1991 ,		1
1959	Theoretical study of energy levels of heterostructures in a transverse magnetic field: A transfer matrix approach. 1991 , 80, 367-370		5
1958	Monte Carlo investigation of acoustic, intervalley and intravalley deformation potentials for GaAs. 1991 , 79, 651-655		
1957	Interaction of hot electrons with two-dimensional gas in semiconductor superlattices. 1991 , 34, 559-564		7
1956	An analytical model for current-voltage characteristics of quantum-well heterojunction field-effect transistors. 1991 , 34, 467-479		11
1955	Generation-recombination noise in Al _x Ga _{1-x} As. 1991 , 34, 23-32		9

1954	Comment on A study of base built-in field effects on the steady-state current gain of heterojunction bipolar transistors□1991, 34, 927	1
1953	Spectral linewidths of quantum well intersubband transitions. 1991, 10, 1-4	5
1952	Acoustic and optic phonon energy relaxation in non-degenerate GaAsAlGaAs multiple quantum wells. 1991, 10, 203-206	9
1951	Tunneling time of electrons in modulation n- doped GaAlAs?GaAs?AlAs quantum wells. 1991, 10, 221-224	
1950	Exciton cooling and localization in GaAs/AlGaAs multiquantum well structures. 1991, 10, 415-420	14
1949	Intersubband relaxation of hot carriers in quantum well systems. 1991, 10, 461-466	7
1948	Large enhancement of spin polarization observed by photoelectrons from a strained GaAs layer. 1991, 158, 345-349	114
1947	The influence of non-linear interference processes on the HREM contrast of AlGaAs in <100> projection. 1991, 35, 77-97	26
1946	Simultaneous verification of pairs of liquidus and solidus data in the Ga-Al-As system. 1991, 110, 626-630	1
1945	On the effective electron mass in semiconductor superlattices. 1991, 70, 77-81	3
1944	. 1991, 38, 634-649	447
1943	. 1991, 38, 1262-1270	23
1942	. 1991, 38, 1986-1992	25
1941	. 1991, 38, 2410-2416	11
1940	. 1991, 38, 2427-2432	10
1939	. 1991, 39, 1847-1854	23
1938	Monte Carlo simulation of semiconductor devices. 1991, 67, 1-61	23
1937	Simulation of advanced semiconductor devices using supercomputers. 1991, 67, 73-92	15

1936	Influence of magnetic quantization on the effective electron mass in Kane-type semiconductors. 1991 , 13, 867-880		21
1935	Correlation between Electrochemical approach for Modeling Band Discontinuities. 1991 , 125, K21-K25		
1934	Effect of Electric Field on the Effective Electron Mass in Quantum Wires of Kane-Type Semiconductors. 1991 , 126, K53-K58		2
1933	Improved implanted, planar buried heterostructure lasers through enhanced optical confinement. 1991 , 23, S959-S965		1
1932	DLDS-related near-bandgap photoluminescence peak in current degraded GaAlAs LEDs. 1991 , 6, 810-814		2
1931	Observation of tunnelling real-space transfer in pseudomorphic MODFETS at T=300 K. 1991 , 6, 1096-1099		3
1930	Room Temperature Hot Electron Transistors with InAs-Notched Resonant-Tunneling-Diode Injector. 1991 , 30, 921-925		23
1929	High pressure studies of resonant tunnelling and superlattice phenomena. 1991 , 6, 422-427		5
1928	Pressure experiments and self-consistent modelling of the transport properties in delta -doped AlGaAs layers. 1991 , 6, 445-448		11
1927	.		
1926	Rectification in heavily doped p-type GaAs/AlAs heterojunctions. <i>Journal of Applied Physics</i> , 1991 , 70, 1081-1083	2.5	6
1925	Dynamic optical reflectivity to monitor the real-time metalorganic molecular beam epitaxial growth of AlGaAs layers. 1991 , 59, 1203-1205		40
1924	Piezoelectric properties of GaAs for application in stress transducers. <i>Journal of Applied Physics</i> , 1991 , 70, 914-918	2.5	36
1923	Experimental measurement of bulk and edge generation in Al _{0.4} Ga _{0.6} As PiN structures. 1991 , 58, 1175-1177		4
1922	Gap properties of Al _n Ga _{8-n} As ₈ ordered compounds. 1991 , 43, 4170-4173		20
1921	Effect of the X point on the escape of electrons from the quantum well of a double-barrier heterostructure. 1991 , 43, 4856-4862		8
1920	Lattice damage and atomic mixing induced by As ⁺⁺ implantation and thermal annealing in AlAs/GaAs multiple quantum-well structures. <i>Journal of Applied Physics</i> , 1991 , 70, 4181-4189	2.5	12
1919	Determination of epitaxial Al _x Ga _{1-x} As composition from x-ray diffraction measurements. 1991 , 59, 2269-2271		50

1918	Pressure-induced Gamma -X electron-transfer rates in a (GaAs) ₁₅ /(AlAs) ₅ superlattice. 1991 , 44, 8129-8137	22
1917	Exciton binding energy in a GaAs/Al _x Ga _{1-x} As quantum well with uniform electric field. 1991 , 44, 8054-8060	10
1916	Temperature dependence of the dielectric function and the interband critical-point parameters of Al _x Ga _{1-x} As. 1991 , 43, 11950-11965	60
1915	Optically detected magnetic resonance of group-IV and group-VI impurities in AlAs and Al _x Ga _{1-x} As with $x \geq 0.35$. 1991 , 43, 14540-14556	19
1914	Electron-phonon interaction and electron scattering by modified confined LO phonons in semiconductor quantum wells. 1991 , 44, 1850-1860	63
1913	Pressure dependence of the indirect band gap of Al _x Ga _{1-x} As alloys ($x=0.70$ and 0.92) at low temperatures. 1991 , 44, 2985-2990	24
1912	Hartree-Fock core local-density-approximation valence pseudopotentials. 1991 , 43, 12070-12073	19
1911	Deep-level photoluminescence studies on Si-doped, metalorganic chemical vapor deposition grown Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1991 , 69, 3266-3277	2.5 26
1910	Modulation spectroscopy of the complex photoluminescence band of Ga _{0.7} Al _{0.3} As:Si. 1991 , 43, 12335-12340	2
1909	Spin relaxation in GaAs-Al _x Ga _{1-x} As heterostructures in high magnetic fields. 1991 , 43, 14228-14231	21
1908	Nonperturbative treatment of excitons in semiconductors coherently pumped near the absorption edge. 1991 , 44, 3638-3649	6
1907	Theory of bound polarons near interfaces of polar semiconductors. 1991 , 43, 4113-4118	15
1906	Pressure tuning of strains in semiconductor heterostructures: (ZnSe epilayer)/(GaAs epilayer). 1991 , 44, 11307-11314	73
1905	Origin of the blueshift in the intersubband infrared absorption in GaAs/Al _{0.3} Ga _{0.7} As multiple quantum wells. 1991 , 43, 9996-9999	57
1904	Light-activated telegraph noise in AlGaAs tunnel barriers: Optical probing of a single defect. 1991 , 67, 1330-1333	15
1903	Calculation of the base current components and determination of their relative importance in AlGaAs/GaAs and InAlAs/InGaAs heterojunction bipolar transistors. <i>Journal of Applied Physics</i> , 1991 , 69, 3328-3334	2.5 22
1902	Model of Γ to X transition in thermally activated tunnel currents across Al _x Ga _{1-x} As single barriers. <i>Journal of Applied Physics</i> , 1991 , 69, 3641-3645	2.5 21
1901	Energy-loss rates of two-dimensional electrons at a GaAs/Al _x Ga _{1-x} As interface. 1991 , 43, 9033-9044	84

1900	Novel photoacoustic spectroscopy of semiconductor thin films by a transparent transducer: Pyroelectric and piezoelectric effects. 1991 , 59, 715-717		4
1899	Electro-optic switching in a p-i-n doped multiple quantum well directional coupler. <i>Journal of Applied Physics</i> , 1991 , 69, 1760-1762	2.5	5
1898	Lateral-nonuniformity effect on the I-V spectrum in a double-barrier resonant-tunneling structure. 1991 , 44, 13631-13634		5
1897	Analysis of visible surface-emitting second-harmonic generators. <i>Journal of Applied Physics</i> , 1991 , 70, 5205-5210	2.5	20
1896	Resonant-Raman-scattering study of disorder effects in Al _x Ga _{1-x} As alloys. 1991 , 44, 8605-8620		6
1895	Exciton binding energy and subband structures of GaAs/Al _x Ga _{1-x} As superlattices. 1991 , 43, 14504-14512		15
1894	Magneto-optical study of donor-level crossing in tipped GaAs/(Ga,Al)As quantum wells. 1991 , 44, 1754-1761		13
1893	Resonant level lifetime in GaAs-AlAs double-barrier structures including Γ X mixing. <i>Journal of Applied Physics</i> , 1991 , 69, 8387-8391	2.5	4
1892	Magnetic susceptibility of InP, InAs, and InSb. 1991 , 43, 2415-2418		13
1891	Temperature dependence of the direct band gap of In _x Ga _{1-x} As (x=0.06 and 0.15). 1991 , 44, 10546-10550		54
1890	Thermionic emission across Al _x Ga _{1-x} As single barriers under hydrostatic pressure. 1991 , 44, 3168-3174		13
1889	Constraints on the polar-optical-phonon influence functional in heterostructures. 1991 , 44, 3850-3853		3
1888	Piezoelectrically induced stress tuning of electro-optic devices. 1991 , 59, 3598-3600		4
1887	Optical characterizations of (111) oriented InGaAs/InAlAs strained quantum wells grown on InP substrates. <i>Journal of Applied Physics</i> , 1991 , 70, 5004-5009	2.5	25
1886	.		
1885	Model for longitudinal-optical phonons and electron-phonon coupling in GaAs-Ga _{1-x} Al _x As multilayer structures. 1991 , 44, 6249-6261		15
1884	Resonant Raman scattering in. 1991 , 43, 9152-9157		12
1883	Photoreflectance Spectra from GaAs Buffer Layer of GaAs/AlAs Multiple Quantum Well/GaAs Buffer/GaAs Substrate. 1991 , 30, 1367-1372		5

1882	The effect of hydrostatic pressure on the band structure of the monolayer superlattice GaAs-Ga _{1-x} Al _x As(001). 1991 , 3, 6553-6558	1
1881	Energy relaxation in GaAs/AlGaAs two-dimensional structures. 1992 , 7, B343-B345	8
1880	Intersubband relaxation of photoexcited carriers in asymmetric coupled quantum wells. 1992 , 7, B98-B101	14
1879	Alloy broadening of the near-gap luminescence and the natural band offset in semiconductor alloys. 1992 , 7, 547-551	15
1878	Spatially resolved composition measurements of ternary epitaxial layers. 1992 , 7, A69-A72	6
1877	Investigation of the L6-X6 intervalley scattering in Al _x Ga _{1-x} As by measuring hot carrier dynamics in a K not=0 satellite valley. 1992 , 7, B173-B175	
1876	Pressure studies of tunnelling processes in a double-barrier structure with a two-dimensional emitter contact. 1992 , 7, 271-274	3
1875	Characterization of Ultrahigh-Speed Pseudomorphic InGaAs/AlGaAs Inverted High Electron Mobility Transistors. 1992 , 31, 1272-1279	3
1874	Response of binding energy of donors in semiconductor quantum wells to realistic multiple images. 1992 , 45, 280-282	1
1873	The thermopower of 2D electron gases in Al _x Ga _{1-x} As/GaAs heterostructures over a wide temperature range. 1992 , 4, 4491-4498	4
1872	Semiempirical self-energy corrections to LDA bands of semiconductors, and a scaling law for the scissor operator. 1992 , 4, 5967-5976	25
1871	On the effective electron mass in strained layer superlattices of non-parabolic semiconductors under strong magnetic quantization. 1992 , 72, 541-552	41
1870	Ordering of conduction band states in (GaAs) _n (AlAs) _n [001] and [110] superlattices. 1992 , 7, 648-653	10
1869	New theory of linewidths of radiative transitions due to disordering in semiconductor alloys. 1992 , 60, 853-855	14
1868	Photoreflectance study of hole-subband structures in GaAs/In _x Al _{1-x} As strained-layer superlattices. <i>Journal of Applied Physics</i> , 1992 , 72, 2372-2376	2.5 15
1867	Pressure studies of gallium nitride: Crystal growth and fundamental electronic properties. 1992 , 45, 13307-13313	38
1866	Influence of Al content in the barrier on the optical properties of GaAs/Al _x Ga _{1-x} As (x=0.1-1) multiple-quantum-well structures. 1992 , 46, 6947-6954	14
1865	Optical properties and electronic structure of thin (Ga,In)As-AlAs multiple quantum wells and superlattices under internal and external strain fields. 1992 , 45, 8413-8423	5

1864	On the transmission coefficient of graded composition GaAs/Al _x Ga _{1-x} As heterojunctions under an electric field. <i>Journal of Applied Physics</i> , 1992 , 71, 4076-4078	2.5	1
1863	Orientation dependence of intersubband absorption in AlAs/Ga _{1-x} Al _x As X valley superlattices. <i>Journal of Applied Physics</i> , 1992 , 72, 3681-3685	2.5	9
1862	Brillouin scattering study of surface acoustic waves in crystalline GaP. <i>Journal of Applied Physics</i> , 1992 , 72, 3504-3508	2.5	5
1861	Alloy scattering in p-type Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1992 , 71, 260-266	2.5	56
1860	Piezospectroscopy of GaAs and GaAs/GaAlAs single quantum wells grown on (001) Si substrates. 1992 , 60, 2651-2653		12
1859	Photoelectrochemical depth profiling of molecular beam epitaxy grown group III-V heterostructures. 1992 , 60, 1348-1350		2
1858	Optical transitions in symmetric, compositionally graded triangular AlGaAs quantum wells grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1992 , 71, 3486-3491	2.5	11
1857	An analysis of surface acoustic wave propagation in a piezoelectric film over a GaAs/AlGaAs heterostructure. <i>Journal of Applied Physics</i> , 1992 , 71, 2136-2142	2.5	10
1856	Characterization of GaAs/Al _x Ga _{1-x} As multiple quantum well infrared detector structures using photoreflectance. <i>Journal of Applied Physics</i> , 1992 , 71, 5154-5160	2.5	9
1855	Investigation of (111) strained layers: Growth, photoluminescence, and internal electric fields. <i>Journal of Applied Physics</i> , 1992 , 71, 5531-5538	2.5	7
1854	Bias dependence of responsivity and transport in asymmetric quantum well infrared detectors. 1992 , 61, 1341-1343		19
1853	Analysis of normal-incident absorption in p-type quantum-well infrared photodetectors. 1992 , 61, 2799-2801		33
1852	AlGaAs diode laser blue shift resulting from fast neutron irradiation. <i>Journal of Applied Physics</i> , 1992 , 71, 5323-5331	2.5	2
1851	Direct and exchange-correlation carrier interaction effects in a resonant tunnel diode. <i>Journal of Applied Physics</i> , 1992 , 72, 3562-3569	2.5	18
1850	Forward and reverse high-pressure transitions in bulklike AlAs and GaAs epilayers. 1992 , 45, 9237-9247		50
1849	Optical dephasing in semiconductor mixed crystals. 1992 , 46, 4564-4581		51
1848	Low-temperature exciton linewidth in short-period superlattices. 1992 , 46, 13268-13273		4
1847	Band-gap renormalization in semiconductors with multiple inequivalent valleys. 1992 , 45, 1139-1154		56

1846	Surface collective modes of non-neutral jellium. 1992 , 46, 7284-7287		29
1845	Linewidth broadening factor of a microcavity semiconductor laser. 1992 , 61, 1883-1885		21
1844	Possible origin of degradation mechanisms in AlGaAs/GaAs laserlike structures. 1992 , 60, 2654-2656		4
1843	Interface-phonon dispersion and confined-optical-mode selection rules of GaAs/AlAs superlattices studied by micro-Raman spectroscopy. 1992 , 46, 4071-4076		46
1842	Luminescence characteristics of quantum wires grown by organometallic chemical vapor deposition on nonplanar substrates. 1992 , 60, 477-479		64
1841	GaAs/AlAs quantum wells for electroabsorption modulators. 1992 , 60, 2779-2781		21
1840	Grating coupling and intersubband absorption at 10 μm in GaAs/Al _x Ga _{1-x} As infrared quantum well waveguides. <i>Journal of Applied Physics</i> , 1992 , 71, 3562-3565	2.5	6
1839	Electrical characteristics of symmetric, compositionally graded triangular heterostructure diodes grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1992 , 71, 3370-3380	2.5	2
1838	A physics-based fitting and extrapolation method for measured impact ionization coefficients in III-V semiconductors. <i>Journal of Applied Physics</i> , 1992 , 72, 531-538	2.5	27
1837	Growth orientation dependence of normal incidence absorption in ellipsoidal-valley quantum wells. 1992 , 61, 2694-2696		12
1836	Giant electropleochroism in GaAs-(Al,Ga)As heterostructures: The quantum-well Pockels effect. 1992 , 69, 973-976		61
1835	Strain, doping, and disorder effects in GaAs/Ge/Si heterostructures: A Raman spectroscopy investigation. <i>Journal of Applied Physics</i> , 1992 , 71, 422-427	2.5	6
1834	Chemical changes accompanying facet degradation of AlGaAs quantum well lasers. <i>Journal of Applied Physics</i> , 1992 , 72, 3884-3896	2.5	17
1833	Nonspectroscopic approach to the determination of the chemical potential and band-gap renormalization in quantum wells. 1992 , 45, 8535-8541		6
1832	Analysis and optimization of quantum-well thickness for GaAs/AlGaAs and InGaAs/GaAs/AlGaAs quantum-well lasers. <i>Journal of Applied Physics</i> , 1992 , 72, 5047-5054	2.5	6
1831	Quantum thermoelectric effects in resonant tunneling real-space transfer. <i>Journal of Applied Physics</i> , 1992 , 72, 4390-4398	2.5	
1830	Experimental evidence of Bragg confinement of carriers in a quantum barrier. 1992 , 61, 949-951		41
1829	One-LO-phonon resonant Raman scattering in wide-gap diluted magnetic semiconductors. 1992 , 45, 11709-11720		12

1828	Al L _{2,3} core excitons in Al _x Ga _{1-x} As studied by soft-x-ray reflection and emission. 1992 , 46, 15116-15122		2
1827	Diffusion and electronic states of hydrogen in n-type GaAs and n-type Ga _{1-x} Al _x As. 1992 , 45, 8803-8806		15
1826	Amplification of the interface-phonon population under an intense laser field. 1992 , 46, 7627-7631		8
1825	Polymorphic stability of AlAs/GaAs superlattices at high pressure. 1992 , 45, 9248-9265		11
1824	Ordering of lowest conduction-band states in (GaAs) _n /(AlAs) _m . 1992 , 46, 15150-15155		15
1823	Quasi-two-dimensional electron system in a GaAs/Al _x Ga _{1-x} As heterojunction. 1992 , 45, 6709-6714		1
1822	Charge accumulation and band edge in the double barrier tunneling structure. <i>Journal of Applied Physics</i> , 1992 , 71, 3877-3882	2.5	12
1821	Composition modulation and inhomogeneous strain field in In _x Ga _{1-x} As/InP strained layers. 1992 , 46, 10453-10456		5
1820	. 1992 ,		
1819	Nonlinear Optical Coefficient of AlAs Thin Film on GaAs Substrate. 1992 , 31, L843-L845		6
1818	Diffusion of Hydrogen and Hydrogen-Dopant Interactions in Si Doped GaAs and GaAlAs Alloys. 1992 , 262, 461		
1817	Semiconductor band structures at zero pressure. 1992 , 46, 2086-2091		54
1816	Confined electron states in ultrathin AlAs single quantum wells under pressure. 1992 , 45, 11846-11853		16
1815	Ab initio calculations of electronic structure and elastic constants in AlP. 1992 , 7, 1437-1440		31
1814	Fine structure of heavy excitons in GaAs/AlAs superlattices. 1992 , 46, 4644-4650		53
1813	Effective mass and ground state of AlAs quantum wells studied by magnetoresistance measurements. <i>Journal of Applied Physics</i> , 1992 , 71, 296-299	2.5	23
1812	Temperature dependence of shallow donor states in GaAs-Al _x Ga _{1-x} As compositional superlattice. 1992 , 46, 473-475		23
1811	Effect of image forces on the binding energies of impurity atoms in Ga _{1-x} Al _x As/GaAs/Ga _{1-x} Al _x As quantum wells. 1992 , 46, 2621-2624		19

1810	Nature of band bending at semiconductor surfaces by contactless electroreflectance. 1992 , 60, 1336-1338	26
1809	The interaction of interface optical phonons with an electron in an asymmetric quantum well. 1992 , 4, 9769-9778	15
1808	. 1992 ,	2
1807	Effect of interdiffusion on the subbands in an $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ single-quantum-well structure. 1992 , 46, 15181-15192	53
1806	Birefringent properties of GaAlAs multiple quantum well planar optical waveguides. 1992 , 28, 1678-1688	26
1805	Transient carrier and field dynamics in quantum-well parallel transport: From the ballistic to the quasi-equilibrium regime. 1992 , 28, 2445-2455	35
1804	Thermal behavior of visible AlGaInP-GaInP ridge laser diodes. 1992 , 28, 2582-2588	36
1803	Comment on the compositional dependence of bandgap in AlGaAs and band-edge discontinuities in AlGaAs-GaAs heterostructures. 1992 , 7, 1113-1116	14
1802	Optical properties of InGaAs films embedded in plasma etched InP wells. 1992 , 61, 798-800	3
1801	Electron velocity-field characteristics of $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$. 1992 , 61, 1202-1204	13
1800	. 1992 , 4, 676-679	11
1799	Ensemble Monte Carlo simulation of intervalley scattering in $\text{Al}_x\text{Ga}_{1-x}\text{As}$. 1992 , 46, 15309-15316	7
1798	.	0
1797	Band Offsets in Semiconductor Heterojunctions. 1992 , 1-146	82
1796	Determination of the critical value of x_c for the direct-to-indirect band-gap transition in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ by measuring hot-carrier dynamics in the X valley. 1992 , 46, 15828-15832	3
1795	Conduction-band universality in GaAs-based systems. 1992 , 7, 165-167	
1794	Resonant Raman scattering in GaAs/AlAs superlattices under electric fields. 1992 , 46, 6990-7001	44
1793	Photoelectronic Processes in Semiconductors Activated to Negative Electron Affinity. 1992 , 397-460	1

1792	On a Simplified Analysis of the Carrier Contribution to Elastic Constants of Ternary and Quaternary Compounds. 1992 , 170, 57-65	7
1791	Temperature Dependence of the Direct Energy Gap in Al _x Ga _{1-x} As. 1992 , 171, K79-K84	9
1790	On the Composition Dependence of the Be Acceptor Energy Level in Al _x Ga _{1-x} As (0 ≤ x ≤ 1). 1992 , 132, K43-K46	5
1789	Thermal Conversion and Hydrogenation Effects on Undoped Al _x Ga _{1-x} As (x = 0.28 and 0.36) Grown on GaAs by Molecular Beam Epitaxy. 1992 , 133, 69-75	
1788	Ellipsoidal valley donor binding energies in a quantum well. 1992 , 84, 885-888	1
1787	The ground state energy of the shallow bound polaron in ternary mixed crystal. 1992 , 81, 457-460	1
1786	Evidence of Γ -band X-X coupling using a single abrupt isotype n-GaAs/Al _{0.5} Ga _{0.5} As heterojunction. 1992 , 35, 1065-1071	1
1785	Numerical studies of thermal effects on heterojunction bipolar transistor current-voltage characteristics using one-dimensional simulation. 1992 , 35, 579-585	20
1784	Effect of base grading on the Early voltage of HBTs. 1992 , 35, 1378-1380	1
1783	Exciton cooling in short period superlattices. 1992 , 12, 7-15	2
1782	Interface induced anisotropic splitting of exciton states in short period superlattices. 1992 , 12, 321-325	4
1781	Hole-subband-order reversal in strained-layer superlattices investigated by photoreflectance spectroscopy. 1992 , 12, 333-336	
1780	Resonant peaks in the transmission coefficient of compositionally nonabrupt GaAs/Al _x Ga _{1-x} As heterojunctions. 1992 , 11, 17-22	11
1779	Orientation dependence of subband structure and optical properties in GaAs/AlGaAs quantum wells: [001], [111], [110] and [310] growth directions. 1992 , 11, 31-40	28
1778	Effective mass in the barriers of GaAs/AlAs resonant tunneling double barrier diodes. 1992 , 11, 55-59	6
1777	New aluminium precursors for MOMBE (CBE): a comparative study. 1992 , 120, 124-129	13
1776	Splitting of degeneracy of valence band in strained GaAs layers observed from polarization of photoelectrons. 1992 , 124, 346-351	11
1775	Laser-induced damaged formation and tungsten deposition on GaAs. 1992 , 54, 60-63	8

- 1774 Photoemission from AlGaAs/GaAs superlattices. **1992**, 56-58, 632-636
- 1773 Strain dependence of spin polarization of photoelectrons from a thin GaAs layer. **1992**, 167, 415-420 29
- 1772 Exact model calculations for band structure applied to superlattices. **1992**, 32, 263-266
- 1771 Influence of quantization of band states on the effective electron mass in quaternary alloys. **1992**, 14, 903-925 16
- 1770 . **1992**, 35, 60-68 4
- 1769 . **1992**, 39, 257-263 18
- 1768 . **1992**, 39, 297-304 6
- 1767 . **1992**, 39, 1355-1362 15
- 1766 Numerical modelling of hot electron transport in A graded heterojunction diode. **1992**, 5, 3-9 1
- 1765 Theoretical calculations of the broadening of dilute Si, Al and Be doped layers in GaAs during SIMS depth profiling. **1993**, 44, 331-335 4
- 1764 Effective mass theory for abrupt heterojunctions. **1993**, 86, 613-616 6
- 1763 Elastic constant C11 of Al_xGa_{1-x}As determined by near infrared Brillouin scattering. **1993**, 88, 267-270 3
- 1762 Characterization of GaAs/Ga_{1-x}Al_xAs multilayer systems by infrared spectroscopy at normal incidence. **1993**, 87, 1039-1044 2
- 1761 Intervalley scattering in indirect gap Al_{0.48}Ga_{0.52}As alloy. **1993**, 85, 953-955 5
- 1760 An analytical model for current transport in AlGaAs/GaAs abrupt HBTs with a setback layer. **1993**, 36, 819-825 39
- 1759 Influence of sulfur concentration on the current-voltage characteristics of Au/GaAs(1-x)S_x/Mo structures. **1993**, 36, 927-932 3
- 1758 Novel AlGaAs/GaAs heterojunction bipolar transistors fabricated by two-stage molecular beam epitaxy. **1993**, 36, 485-487
- 1757 Characteristics of heavily carbon-doped GaAs by LPMOCVD and critical layer thickness. **1993**, 126, 441-446 23

1756	Accurate determination of lattice mismatch in the epitaxial AlAs/GaAs system by high-resolution X-ray diffraction. 1993 , 132, 427-434	27
1755	Improvement of high brightness AlGaAs/GaAs DH red LED under optimum growth conditions. 1993 , 128, 527-532	3
1754	Structural and electronic properties of GaAs : C and Al _x Ga _{1-x} As : C grown by solid-source molecular beam epitaxy. 1993 , 127, 724-727	4
1753	An AlGaAs/GaAs OEIC structure for the integration of LEDs, MESFETs and photodetectors. 1993 , 21, 300-303	1
1752	First step of degradation mechanisms in AlGaAs/GaAs laser-like structures. 1993 , 20, 29-32	10
1751	Flexural vibrations in piezoelectric semi-insulating GaAs. 1993 , 39, 133-139	11
1750	Physical models for predicting the performance of Si/Si, AlGaAs/GaAs, and Si/SiGe solar cells. 1993 , 29, 261-276	14
1749	Influence of a Quantizing Magnetic Field on the Effective Electron Mass in HgTe/CdTe Superlattices with Graded Structures. 1993 , 175, 113-121	14
1748	Intra- and Intersubband Plasmon-Polaritons in Semiconductor Quantum Wells. 1993 , 177, 9-67	35
1747	Effective Mass Theory for Abrupt Heterostructures. 1993 , 178, 141-149	5
1746	Pressure Dependent Donor Ionization Energies in a Quantum Well. 1993 , 178, 167-172	13
1745	Diamagnetic and Dielectric Susceptibilities of AlSb and GaSb. 1993 , 178, 343-351	2
1744	On a Simplified Analysis of the Effective Electron Mass in Ultrathin Films of Nonparabolic Semiconductors in the Presence of a Parallel Magnetic Field. 1993 , 179, 383-389	3
1743	The energy barrier for electron trapping in Al _x Ga _{1-x} As. 1993 , 139, 145-152	4
1742	. 1993 , 40, 285-291	11
1741	. 1993 , 40, 480-486	8
1740	. 1993 , 40, 846-851	1
1739	. 1993 , 40, 878-884	11

1738	. 1993 , 40, 1583-1588	28
1737	. 1993 , 40, 1950-1956	21
1736	. 1993 , 40, 35-43	38
1735	Intermediate-coupling polaron in a ternary mixed crystal. 1993 , 91, 455-461	9
1734	Hall and drift mobilities in molecular beam epitaxial grown GaAs. 1993 , 22, 1317-1321	8
1733	Spectroscopic transmission ellipsometry studies of intersub-band transitions in As quantum wells. 1993 , 233, 194-198	1
1732	Two-photon interband transitions in crossed electric and magnetic fields in semiconductors. Non-local effects. 1993 , 15, 1321-1329	
1731	Novel differentially strained p-doped quantum well infrared detector. 1993 , 34, 153-161	7
1730	Electron-optical-phonon interaction in a trilayer system of polar crystals. 1993 , 298, 225-240	16
1729	. 1993 , 29, 311-321	17
1728	. 1993 , 29, 1880-1884	11
1727	. 1993 , 29, 1963-1974	60
1726	. 1993 , 29, 1364-1382	47
1725	. 1993 , 29, 2731-2740	48
1724	. 1993 , 29, 2825-2834	4
1723	Temperature dependence of the Γ_v - Γ_c gap of GaAs. <i>Journal of Applied Physics</i> , 1993 , 74, 2742-2747	2.5 10
1722	Dependence of conduction-band effective mass on quaternary alloy composition of $(\text{In}_{0.52}\text{Al}_{0.48}\text{As})_z(\text{In}_{0.53}\text{Ga}_{0.47}\text{As})_{1-z}$ lattice matched to InP. 1993 , 63, 1804-1806	11
1721	Hydrostatic pressure dependence of binding energies for donors in quantum well heterostructures. 1993 , 48, 376-378	95

1720	Electron optical-phonon coupling in GaAs/Al _x Ga _{1-x} As quantum wells due to interface, slab, and half-space modes. 1993 , 48, 4666-4674		75
1719	Experimental determination of the GaAs and Ga _{1-x} Al _x As band-gap energy dependence on temperature and aluminum mole fraction in the direct band-gap region. 1993 , 48, 4398-4404		56
1718	Gamma -X mixing in GaAs/Al _x Ga _{1-x} As coupled double quantum wells under hydrostatic pressure. 1993 , 47, 1991-1997		63
1717	Direct mapping of electronic structure across Al _{0.3} Ga _{0.7} As/GaAs heterojunctions: Band offsets, asymmetrical transition widths, and multiple-valley band structures. 1993 , 71, 1883-1886		46
1716	Pressure tuning of strain in CdTe/InSb epilayer: A photoluminescence and photomodulated reflectivity study. <i>Journal of Applied Physics</i> , 1993 , 74, 4136-4144	2.5	13
1715	Dipole relaxation current in n-type Al _x Ga _{1-x} As. 1993 , 63, 2658-2660		2
1714	Monte Carlo modeling of high-field transport in III-V heterostructures. <i>Journal of Applied Physics</i> , 1993 , 74, 6274-6280	2.5	18
1713	Transmission coefficient and Stark shifts in double-barrier quantum well structures. 1993 , 8, 243-253		3
1712	X-Ray Diffraction Methods for the Determination of Stresses and Strains in Multilayer Monocrystal Films. 1993 , 3, 257-324		2
1711	Compositional dependence of optical-phonon frequencies in Al _x Ga _{1-x} As. 1993 , 47, 13466-13470		26
1710	EX phonon-assisted thermionic currents in the GaAs/Al _x Ga _{1-x} As interface system. <i>Journal of Applied Physics</i> , 1993 , 73, 8536-8543	2.5	6
1709	X- and Gamma -related tunneling resonances in GaAs/AlAs double-barrier structures at high pressure. 1993 , 47, 1419-1433		24
1708	EX intervalley transfer in single AlAs barriers under hydrostatic pressure. 1993 , 62, 1955-1957		19
1707	Self-consistent simulation of quantum wires in periodic heterojunction structures. <i>Journal of Applied Physics</i> , 1993 , 74, 1199-1204	2.5	16
1706	Tunneling resonances at high pressure in double-barrier structures with AlAs barriers thicker than 50. 1993 , 48, 11905-11911		10
1705	. 1993 , 5, 1421-1423		
1704	A quantum statistical theory of linewidths of radiative transitions due to compositional disordering in semiconductor alloys. <i>Journal of Applied Physics</i> , 1993 , 73, 1788-1796	2.5	51
1703	Resonant tunneling diodes: The effect of structural properties on their performance. 1994 , 37-62		19

1702	Aluminium valence and core excitonic states in GaAs-Ga _{0.7} Al _{0.3} As systems. 1993 , 5, 1691-1700	5
1701	Electron-interface phonon scattering in GaAs/Ga _{1-x} Al _x As quantum-well structures with interface roughness. 1993 , 5, 2859-2868	16
1700	Optical Constants of ZnSexTe1-xTernary Alloys. 1993 , 32, 2620-2625	11
1699	A computer simulation of local amorphization in III-V compounds. 1993 , 5, 7907-7922	1
1698	The use of realistic band structure in impact ionization calculations for wide bandgap semiconductors: thresholds, anti-thresholds and rates in GaAs and AlGaAs. 1993 , 8, 1944-1956	4
1697	Highly Repetitive Picosecond Polarization Switching in Type-II AlGaAs/AlAs Multiple Quantum Well Structures. 1993 , 32, L1756-L1759	21
1696	Photomodulation study of partially strained In _x Ga _{1-x} As layers. 1993 , 8, 1420-1425	7
1695	Thermally induced absorptive optical bistability in GaAs/(Al,Ga)As multiple quantum wells. 1993 , 8, 1399-1407	8
1694	Hydrostatic pressure studies of thin-barrier resonant tunnelling diodes. 1993 , 8, 1352-1356	9
1693	Direct measurement of hot electron energy distributions in Al _{0.35} Ga _{0.65} As field-assisted photocathodes. 1993 , 8, 1803-1809	2
1692	Coupling between in-plane and longitudinal motion in resonant tunnelling structures. 1993 , 8, 1810-1814	1
1691	DX states in GaAs/AlAs short-period superlattices doped selectively with silicon. 1993 , 8, 1977-1984	3
1690	Unambiguous identification of X-point-related resonances in GaAs/AlAs/GaAs tunnel diodes under hydrostatic pressure. 1993 , 8, 1483-1486	5
1689	Long-wavelength polar optical modes in GaAs semiconductor layered structures. 1993 , 5, 5389-5400	28
1688	All-optical measurement of the giant ambipolar diffusion constant in a hetero-nipi reflection modulator. 1993 , 8, 1750-1754	11
1687	Confined and interface phonon scattering in finite barrier GaAs/AlGaAs quantum wires. <i>Journal of Applied Physics</i> , 1993 , 74, 1652-1659	2.5 14
1686	Evidence of silicon interdiffusion in selectively doped GaAs-AlAs superlattices by Hall measurements. <i>Journal of Applied Physics</i> , 1993 , 74, 7166-7172	2.5 8
1685	Polaron-cyclotron-resonance spectrum resulting from interface- and slab-phonon modes in a GaAs/AlAs quantum well. 1993 , 47, 10358-10374	51

1684	Optical properties of bulk Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1993 , 74, 6341-6348	2.5	14
1683	Electro-optic sampling using an aluminum gallium arsenide probe. 1993 , 62, 1733-1735		8
1682	Ultrafast all-optical switching in GaAlAs directional couplers at 1.55 μ m without multiphoton absorption. 1993 , 63, 3562-3564		34
1681	Modeling the optical dielectric function of the alloy system Al _x Ga _{1-x} As. 1993 , 47, 1876-1888		77
1680	Optical modes in GaAs-based quantum wells. 1993 , 48, 5672-5674		10
1679	Capacitance studies of charge redistribution between Γ and X states in a GaAs/AlAs double barrier structure at high pressure. <i>Journal of Applied Physics</i> , 1993 , 74, 7340-7343	2.5	7
1678	Transmission coefficient of electrons through a single graded barrier. 1993 , 48, 8446-8449		8
1677	Effects of hydrostatic pressure on the optic and transverse-acoustic vibrations of a (012) GaAs/AlAs superlattice. 1993 , 48, 11057-11061		1
1676	Measurement of the exciton binding energy in a narrow GaAs-Al _x Ga _{1-x} As quantum well by photoluminescence excitation spectroscopy. 1993 , 47, 2042-2047		10
1675	Effects of the Coulomb interaction on the optical spectra of quantum wires. 1993 , 47, 4315-4326		31
1674	Band-offset ratio dependence on the effective-mass Hamiltonian based on a modified profile of the GaAs-Al _x Ga _{1-x} As quantum well. 1993 , 47, 12760-12770		75
1673	Origin of current instabilities in GaAs/Al _x Ga _{1-x} As heterostructures: Avalanche ionization in the Al _x Ga _{1-x} As layer. <i>Journal of Applied Physics</i> , 1993 , 73, 2381-2385	2.5	4
1672	Supermode analysis of electron wave directional coupling using a multilayer waveguide approach. <i>Journal of Applied Physics</i> , 1993 , 73, 3352-3366	2.5	13
1671	Electron-interface LO phonon scattering rates in quantum wells in a quantizing magnetic field. <i>Journal of Applied Physics</i> , 1993 , 74, 4561-4564	2.5	6
1670	Magnetopolaron effect on shallow donor states in GaAs. 1993 , 48, 5202-5216		51
1669	Thermally activated real-space-transfer noise in pseudomorphic high-electron-mobility transistors. <i>Journal of Applied Physics</i> , 1993 , 74, 1143-1150	2.5	5
1668	High-quality two-dimensional electron system confined in an AlAs quantum well. 1993 , 62, 3120-3122		45
1667	Determination of quadratic nonlinear optical coefficient of Al _x Ga _{1-x} As system by the method of reflected second harmonics. <i>Journal of Applied Physics</i> , 1993 , 74, 596-601	2.5	71

1666	Tunneling through Al _x Ga _{1-x} As single barriers under hydrostatic pressure. 1993 , 63, 937-939		4
1665	Cavity design for improved electrical injection in InAlGaP/AlGaAs visible (639-661 nm) vertical-cavity surface-emitting laser diodes. 1993 , 63, 917-919		18
1664	Observation of a linear dependence of the frequency splitting between GaAs and AlAs optical surface phonons as a function of Al concentration in Al _x Ga _{1-x} As. 1993 , 48, 4380-4387		4
1663	Exciton states in GaAs/AlGaAs Bragg confining structures studied by resonant Raman scattering. 1993 , 71, 420-423		16
1662	Photoluminescence up-conversion induced by intersubband absorption in asymmetric coupled quantum wells. 1993 , 70, 1018-1021		36
1661	Space-charge effects in photovoltaic double barrier quantum well infrared detectors. 1993 , 63, 782-784		28
1660	Second-harmonic generation using heavy-hole/light-hole intersubband transitions in asymmetric quantum wells. 1993 , 62, 1946-1948		19
1659	Photothermal luminescence spectroscopy of GaAs/Al _x Ga _{1-x} As quantum wells. <i>Journal of Applied Physics</i> , 1993 , 73, 4555-4559	2.5	7
1658	Determination of the lattice parameter and Poisson ratio for AlAs via high-resolution x-ray-diffraction studies of epitaxial films. 1993 , 48, 9154-9157		13
1657	Photoluminescence of AlAs/GaAs superlattice quantum wells. 1993 , 62, 2655-2657		1
1656	Optical anisotropy in GaAs/Al _x Ga _{1-x} As multiple quantum wells under thermally induced uniaxial strain. 1993 , 47, 13933-13936		34
1655	Exciton linewidth limited by polar optic-phonon scattering in a short-period superlattice: Anisotropic-effective-medium model. 1993 , 47, 15958-15960		4
1654	Clustering-induced phonon linewidth anomalies in Al _x Ga _{1-x} As. 1993 , 47, 9492-9500		4
1653	Interface optical phonons near perfectly conducting boundaries and their coupling to electrons. 1993 , 48, 11931-11935		4
1652	Ballistic-electron-emission microscopy of electron transport through AlAs/GaAs heterostructures. 1993 , 48, 18324-18327		37
1651	Two coupled parabolic wells under an electric field. <i>Journal of Applied Physics</i> , 1993 , 74, 4006-4014	2.5	9
1650	Enhanced refractive index change in asymmetrical quantum wells with an applied electric field. <i>Journal of Applied Physics</i> , 1993 , 74, 6872-6875	2.5	7
1649	Effects of interdiffusion on the sub-band-edge structure of In _{0.53} Ga _{0.47} As/InP single quantum wells. <i>Journal of Applied Physics</i> , 1993 , 73, 7524-7532	2.5	39

1648	Ultrathin delta doped GaAs and AlAs tunnel junctions as interdevice ohmic contacts. <i>Journal of Applied Physics</i> , 1993 , 74, 4207-4212	2.5	20
1647	An optical study of the lateral motion of two-dimensional electron-hole pairs in GaAs/AlGaAs quantum wells. 1993 , 5, 5563-5580		9
1646	Optical Constants of Zn _{1-x} Cd _x Te Ternary Alloys: Experiment and Modeling. 1993 , 32, 3496-3501		71
1645	OPTICAL GAIN IN III-V BULK AND QUANTUM WELL SEMICONDUCTORS. 1993 , 17-96		31
1644	A COMPOUND EMITTER HETEROJUNCTION BIPOLAR TRANSISTOR. 1993 , 12, 319-330		
1643	High speed devices: Properties and applications. 1992 , 151-197		
1642	Creation of In-Plane Anisotropic Strain in GaAs/Al _x Ga _{1-x} As Multiple Quantum Well Structures. 1993 , 300, 537		5
1641	Raman and Photoluminescence Characterization of FIB Patterned AlGaAs/GaAs Multiple Quantum Wells. 1993 , 324, 193		2
1640	Characterization of Electronic Materials by Optical Reflectance Spectroscopy and Digital Signal Processing. 1993 , 324, 75		
1639	Optical Characterization of Focused Ion Beam Implanted AlGaAs/GaAs Multiple Quantum Well Structures. 1993 , 326, 241		
1638	Combined Optical, Structural and Theoretical Assessment Of MOCVD Grown Multiple GaAs Quantum Wells. 1993 , 326, 359		
1637	.		
1636	Layered Semiconductor Photorefectance Diagnostics. 1993 , 324, 175		
1635	Semiconductor Quantum Wells and Superlattices. 1994 , 251-278		1
1634	The piezoelectric effect of GaAs used for resonators and resonant sensors. 1994 , 4, 28-34		44
1633	Optical studies of strained pseudomorphic semiconductor heterostructures under external pressure. 1994 , 70, 369-380		21
1632	Monte Carlo formulation of velocity-field characteristics and expressions for Al _x Ga _{1-x} As. 1994 , 76, 1049-1062	3	
1631	"Vertical" vs. "Horizontal" Nonlinear Directional Couplers in Epitaxial AlGaAs Structures with MQW Layers. 1994 , 15,		

1630	Interaction Hamiltonian Between an Electron and Interface Optical Phonons in a Four-Layer Heterostructure. 1994 , 11, 439-442		1
1629	The electron mobility transition in n-GaAs heavily doped channels. 1994 , 9, 811-814		1
1628	Magnetopolaron effect on shallow donors in bulk and in weakly and strongly coupled superlattices. 1994 , T55, 57-64		7
1627	Dynamical screening of excitons in a semiconductor electron-hole plasma. 1994 , 6, 9335-9348		8
1626	Photoexcitation of coupled plasmon-LO phonon modes in Al _x Ga _{1-x} As. 1994 , 9, 1659-1665		
1625	Analysis of normal-incident absorption in a proposed p-type very-narrow-quantum-well infrared photodetector. 1994 , 64, 321-323		
1624	Dielectric response induced by intersubband transitions in quantum wells: Transmission ellipsometry studies at Brewster angle. <i>Journal of Applied Physics</i> , 1994 , 75, 5347-5353	2.5	6
1623	Coupled finite element/boundary element method for semiconductor quantum devices with exposed surfaces. <i>Journal of Applied Physics</i> , 1994 , 75, 2545-2554	2.5	18
1622	Enhancement of electron-wave reflection by superlattices with multiple stacks of multiquantum barriers. 1994 , 64, 1108-1110		11
1621	A study of Franz-Keldysh oscillations of GaAs/Si/GaAs and AlAs/Si/AlAs heterostructures. <i>Journal of Applied Physics</i> , 1994 , 76, 3616-3619	2.5	3
1620	Electron-interface-phonon scattering in graded quantum wells of Ga _{1-x} Al _x As. 1994 , 49, 14403-14408		19
1619	Diffraction from optically written persistent plasma gratings in doped compound semiconductors. 1994 , 65, 16-18		63
1618	Zone-center optical phonons in In _x Ga _{1-x} As alloys. 1994 , 50, 18644-18646		3
1617	Optical generation of high-frequency acoustic waves in GaAs/Al _x Ga _{1-x} As periodic multilayer structures. <i>Journal of Applied Physics</i> , 1994 , 75, 2761-2768	2.5	33
1616	Motion of electrons in semiconductors under inhomogeneous strain with application to laterally confined quantum wells. 1994 , 49, 14352-14366		46
1615	Molecular-beam-epitaxial growth and characterization of high-quality alloys and multiple quantum wells on InP substrates using a post-evaporation-heated arsenic source. <i>Journal of Applied Physics</i> , 1994 , 76, 3429-3442	2.5	13
1614	Guided Acoustic Phonons in Quantum Wires: Theory of Phonon Fiber. 1994 , 33, 2852-2858		19
1613	Shallow donor impurities in GaAs/Al _x Ga _{1-x} As superlattices in a magnetic field. 1994 , 50, 15182-15190		58

1612	Elastic and inelastic scattering in quantum dots in the Coulomb-blockade regime. 1994 , 50, 5484-5496		15
1611	Electron capture in GaAs quantum wells. 1994 , 49, 7543-7547		25
1610	Hydrostatic-pressure dependence of band offsets in GaAs/Al _x Ga _{1-x} As heterostructures. 1994 , 49, 10444-10449		1
1609	Built-in biaxial strain dependence of EX transport in GaAs/In _x Al _{1-x} As/GaAs pseudomorphic heterojunction barriers (x=0, 0.03, and 0.06). <i>Journal of Applied Physics</i> , 1994 , 76, 7907-7914	2.5	0
1608	Enhanced field control of second-harmonic generation in compositionally asymmetrical quantum wells. <i>Journal of Applied Physics</i> , 1994 , 75, 8222-8224	2.5	6
1607	Vertical drift mobility of excited carriers in multi quantum well structures. <i>Journal of Applied Physics</i> , 1994 , 75, 3536-3543	2.5	7
1606	Temperature and many-body effects on the intersubband transition in a GaAs/Al _{0.3} Ga _{0.7} As multiple quantum well. 1994 , 50, 11618-11623		19
1605	Assessment of interface composition in superlattices by far-infrared reflectivity. 1994 , 49, 2604-2607		3
1604	Demonstration of gallium-defect annealing at 280 K in irradiated GaAs and Al _x Ga _{1-x} As. 1994 , 49, 5695-5698		6
1603	Thermal characteristics of blue-green II-VI semiconductor lasers. <i>Journal of Applied Physics</i> , 1994 , 76, 3988-3993	2.5	10
1602	Characterization of process-induced strains in GaAs/Ga _{0.7} Al _{0.3} As quantum dots using room-temperature photoreflectance. 1994 , 64, 2830-2832		29
1601	The double resonant enhancement of optical second harmonic susceptibility in the compositionally asymmetric coupled quantum well. <i>Journal of Applied Physics</i> , 1994 , 75, 2177-2183	2.5	14
1600	Quantum state transfer in double-quantum-well devices. <i>Journal of Applied Physics</i> , 1994 , 76, 7428-7436	2.5	3
1599	Theory of absorption spectra for above-barrier excitons in semiconductor superlattices. 1994 , 49, 16585-16592		5
1598	Electron-phonon scattering in Ga _{1-x} Al _x As quantum-well structures in an electric field. 1994 , 50, 5473-5479		10
1597	Validity of the connection-matrix approach to GaAs-Al _x Ga _{1-x} As quantum wells. 1994 , 49, 2608-2614		3
1596	Effect of bulk dispersion on the electron-optical-phonon interaction in a single quantum well. 1994 , 49, 17065-17071		19
1595	Evidence of bistable shallow-deep silicon donors in GaAs-AlAs superlattices. <i>Journal of Applied Physics</i> , 1994 , 75, 7356-7360	2.5	6

1594	Electron wave-packet response of above-all-band-edges semiconductor quantum resonant structures. <i>Journal of Applied Physics</i> , 1994 , 75, 5415-5422	2.5	4
1593	Electrophonon resonance in Al _x Ga _{1-x} As-GaAs quasi-two-dimensional quantum wells. 1994 , 50, 7640-7654		4
1592	Characterization of an AlGaAs/GaAs asymmetric triangular quantum well grown by a digital alloy approximation. <i>Journal of Applied Physics</i> , 1994 , 75, 4551-4556	2.5	18
1591	Enhancement of second harmonic generation at 1.06 μ m using a quasi-phase-matched AlGaAs/GaAs asymmetric quantum well structure. 1994 , 65, 3176-3178		10
1590	Electronic structure of. 1994 , 49, 10749-10752		8
1589	Localized phonon-assisted cyclotron resonance in GaAs/AlAs quantum wells. 1994 , 49, 16459-16466		43
1588	Determination of the deformation potentials of GaAs _{0.80} P _{0.20} . <i>Journal of Applied Physics</i> , 1994 , 76, 1951-1953	2.5	13
1587	Multilayers as microlabs for point defects: Effect of strain on diffusion in semiconductors. 1994 , 73, 448-451		21
1586	Model calculation of the femtosecond carrier dynamics in Al _{0.48} Ga _{0.52} As. <i>Journal of Applied Physics</i> , 1994 , 76, 3749-3753	2.5	
1585	Influence of the AlAs mode fraction on the luminescence efficiency of As quantum well structures. 1994 , 248, 32-35		2
1584	Theory of the photoacoustic effect of semiconductor quantum wells. 1994 , 58, 167-175		1
1583	A Simple Analysis of the Magnetic Susceptibilities in Quantum Dots of Optoelectronic Materials in the Presence of a Parallel Magnetic Field. 1994 , 181, 127-131		5
1582	Free Carrier Absorption in Quantum Well Structures Due to Confined and Interface Optical Phonons. 1994 , 182, 119-131		9
1581	A comparison of force constants, mechanical and thermal properties in Hg _{1-x} Cd _x Te and Hg _{1-x} Zn _x Te mixed crystals. 1994 , 183, 395-406		10
1580	Effect of stabilisation of lattice constant in the Ga _{1-x} In _x As system. 1994 , 144, 371-375		2
1579	Influence of the interface on contact supersaturation of GaInPAs alloys. 1994 , 146, K19-K22		2
1578	The investigation of growth characteristics of single quantum wells grown on (311) GaAs substrates. 1994 , 27, 7-12		1
1577	Phonon polariton modes in quantum well wire superlattices. 1994 , 89, 459-462		12

1576	An efficient and accurate self-consistent calculation of electronic states in modulation doped heterostructures. 1994 , 37, 27-30	6
1575	High frequency noise and diffusion coefficient of hot electrons in bulk Al _{0.25} Ga _{0.75} As. 1994 , 37, 1477-1483	4
1574	Closed-form calculations of two-dimensional scattering rates in semiconductor heterostructures. 1994 , 37, 1817-1824	4
1573	Reassessment of the piezoelectric constant in GaAs by studying the electron transport of high purity MBE-grown GaAs. 1994 , 37, 1345-1347	4
1572	Comparative modelling of current gain and cutoff frequency for heterostructure confinement and heterojunction bipolar transistors. 1994 , 37, 1783-1785	
1571	Hydrostatic pressure sensors based on solid state tunneling devices. 1994 , 37, 801-804	7
1570	GaAs/AlGaAs quantum well infrared photodetectors. 1994 , 37, 1187-1190	1
1569	Hardness, internal stress and fracture toughness of epitaxial Al _x Ga _{1-x} As films. 1994 , 250, 157-163	12
1568	In situ control of the growth of GaAs / GaAlAs structures in a metalorganic vapour phase epitaxy reactor by laser reflectometry. 1994 , 145, 61-67	8
1567	Effect of the Gamma -X crossover on the binding energies of confined donors in single GaAs/Al _x Ga _{1-x} As quantum-well microstructures. 1994 , 6, 10025-10030	100
1566	A simple theoretical analysis of the effective electron mass in NIPI structures of non-parabolic semiconductors. 1994 , 74, 257-268	6
1565	In situ spectral reflectance monitoring of III-V epitaxy. 1994 , 23, 179-183	49
1564	Growth of InAlGaAs strained quantum well structures for reliable 0.8 μ m lasers. 1994 , 23, 207-216	7
1563	. 1994 , 41, 484-490	10
1562	. 1994 , 41, 511-518	31
1561	. 1994 , 41, 1778-1783	32
1560	Gallium arsenide as a mechanical material. 1994 , 4, 1-13	116
1559	. 1994 , 6, 330-333	

1558	High power AlGaAs-GaAs visible diode lasers. 1994 , 6, 775-777		20
1557	. 1994 , 6, 811-813		28
1556	. 1994 , 6, 1427-1429		18
1555	Electron mobilities in gallium, indium, and aluminum nitrides. <i>Journal of Applied Physics</i> , 1994 , 75, 7365-7372		447
1554	Effect of half-space and interface phonons on the transport properties of Al _x Ga _{1-x} As/GaAs single heterostructures. 1994 , 49, 8178-8190		25
1553	Photoluminescence of Al _x Ga _{1-x} As alloys. <i>Journal of Applied Physics</i> , 1994 , 75, 4779-4842	2.5	418
1552	The photonic band edge laser: A new approach to gain enhancement. <i>Journal of Applied Physics</i> , 1994 , 75, 1896-1899	2.5	512
1551	Optical properties of GaAs/Al _x Ga _{1-x} As multiple quantum wells versus electric field including exciton transition broadening effects in optical modulators. <i>Journal of Applied Physics</i> , 1994 , 75, 2618-2627	2.5	16
1550	Optical dispersion of Al _x Ga _{1-x} As at crystal growth temperature. <i>Journal of Applied Physics</i> , 1994 , 76, 8048-8050	2.5	4
1549	Observation of miniband transport in GaAs/Al _{0.33} Ga _{0.67} As superlattices. <i>Journal of Applied Physics</i> , 1994 , 75, 320-324	2.5	25
1548	Compressibility of the two-dimensional electron gas: Measurements of the zero-field exchange energy and fractional quantum Hall gap. 1994 , 50, 1760-1778		235
1547	Empirical formula for the dielectric constant of cubic semiconductors. 1994 , 65, 1938-1939		20
1546	Raman study of gallium arsenide thin films. 1994 , 170, 263-269		11
1545	Polar optical phonons at semiconductor interfaces. 1994 , 319, 184-192		10
1544	Calculation of photogenerated carrier escape rates from GaAs/AlGa/sub 1-x/As quantum wells. 1994 , 30, 1015-1026		23
1543	Experimental and theoretical studies of a novel hetero-nipi reflection modulator. 1994 , 30, 1027-1035		5
1542	A low-voltage, high-reflectance-change normally off refractive GaAs/Al/sub 0.2/Ga/sub 0.8/As MQW reflection modulator. 1994 , 30, 1234-1240		4
1541	Anomalous thermionic-field emission in epitaxial Al/n-AlGaAs junctions. 1994 , 28, 429-432		27

1540	Optical constants of ZnSxSe1-x ternary alloys. <i>Journal of Applied Physics</i> , 1994 , 75, 7470-7475	2.5	46
1539	Spectrum and binding of an off-center donor in a spherical quantum dot. 1994 , 50, 4497-4502		163
1538	Refractive index of (AlxGa1-x)0.5In0.5P quaternary alloys. <i>Journal of Applied Physics</i> , 1994 , 75, 478-480	2.5	27
1537	Phase transformation of AlAs to NiAs structure at high pressure. 1994 , 72, 2045-2048		62
1536	.		
1535	Dielectric properties of electron-beam deposited Ga2O3 films. 1994 , 64, 2715-2717		158
1534	Laser heating and photoluminescence in GaAs and AlxGa1-xAs. 1994 , 65, 2469-2471		6
1533	Local-field study of the optical second-harmonic generation in a symmetric quantum-well structure. 1994 , 49, 13616-13623		32
1532	Effects of interface and bulk optical phonons on polarons in a quantum well. 1994 , 49, 1796-1801		39
1531	Multiband tight-binding approach to tunneling in semiconductor heterostructures: Application to Gamma X transfer in GaAs. 1994 , 49, 16494-16504		32
1530	Polaronic effect on the electron energy spectrum in a quantum well. 1994 , 6, 10307-10316		1
1529	Optical Studies of The Uniformity of Thermally Induced In-Plane Strain in Thin Gallium Arsenide Films. 1994 , 340, 333		
1528	Thermal Expansion Behavior of ZnSe and ZnS0.03Se0.97 Epilayers on GaAs at Temperatures in the Range, 25°C - 250°C. 1994 , 340, 475		
1527	Effects of uniaxial stress on the optical properties of GaAs and GaAs/Ga1-xAlxAs single quantum wells grown on Si(001) substrates. 1994 , 70, 381-395		3
1526	Intraband magnetoabsorption in semiconductor quantum wells.		
1525	Transport studies of AlxGa1-xAs/GaAs quantum heterostructures using BEEM. 1996 , 243-256		
1524	. 1995 , 42, 15-22		61
1523	. 1995 , 42, 1070-1080		7

1522	. 1995 , 42, 1393-1403	17
1521	Modeling and experimental FTS investigation of IR reflectance spectra from multilayered semiconductor structures. 1995 , 349, 293-296	
1520	Chemical composition fluctuations at interfaces in quantum well structures: effect on interface phonon modes. 1995 , 200, 329-334	1
1519	Al _x Ga _{1-x} In _{0.65} As monolithic multijunction solar cells. 1995 , 36, 349-356	
1518	Electrical behaviour of epitaxial Al/n-Al _{0.25} Ga _{0.75} As junctions: effect of the composition of undoped Al _x Ga _{1-x} As cap layer. 1995 , 46, 959-961	2
1517	Dependence of propagation loss on etching depth in Al _{0.3} Ga _{0.7} As/GaAs/Al _{0.3} Ga _{0.7} As strip-loaded type waveguides. 1995 , 27, 363-369	
1516	Erosive dissolution of InP substrates during liquid phase heteroepitaxy. 1995 , 148, 469-474	1
1515	Effective Mass Theory for Strained Superlattices. 1995 , 187, 517-522	1
1514	On the Effective Electron Mass in Quantum Wires of Non-Parabolic Semiconductors under a Parallel Magnetic Field. 1995 , 187, 523-531	9
1513	Model Effective-Mass Hamiltonians for Abrupt Degraded Heterojunctions. 1995 , 189, 389-399	3
1512	Exciton Energies as a Function of Electric Field in Quantum Wells Finite Potential Barrier Case. 1995 , 190, 211-217	17
1511	The control and modification of metal-semiconductor interfaces using multi quantum barriers. 1995 , 35, 145-148	2
1510	Infrared thermopile sensor based on AlGaAs/GaAs micromachining. 1995 , 47, 432-436	35
1509	Effective masses of electrons and heavy holes in GaAs, InAs, AlAs and their ternary compounds. 1995 , 210, 1-25	77
1508	Effect of interface energy on erosion of AlIIIbV substrates during liquid phase heteroepitaxy. 1995 , 153, 11-18	5
1507	Investigation of the conduction bandstructure in (001) oriented type II GaAs/AlAs short period superlattices using (100) uniaxial stress. 1995 , 56, 429-434	12
1506	New resonant tunneling processes between longitudinal and transverse X-states in GaAs/AlAs double barrier structures beyond the type II transition. 1995 , 56, 435-443	2
1505	Pressure and temperature induced detuning of gain and reflectivity spectra in vertical cavity surface emitting lasers. 1995 , 56, 663-667	2

1504	Kinetic energy operator for strained heterostructures. 1995 , 93, 97-101		
1503	Angular dispersion of confined optical phonons in superlattices studied by micro-Raman spectroscopy. 1995 , 93, 847-851		24
1502	Calculation of elastic constants of Al _x Ga _{1-x} As alloys. 1995 , 95, 131-135		1
1501	Optical properties of ultrathin 50nm GaAs membranes. 1995 , 96, 359-365		3
1500	Nonparabolicity effects on transition rates due to confined phonons in GaAs-AlGaAs quantum wells. 1995 , 96, 763-766		6
1499	Combined effects of graded and setback layers on the AlGaAsGaAs HBT current-voltage characteristics. 1995 , 38, 627-632		
1498	An analytical model for the current transport of graded heterojunction bipolar transistors. 1995 , 38, 946-948		2
1497	Current transport in heterojunction bipolar transistors operating between 300 and 500 K. 1995 , 38, 1759-1763		
1496	Infrared multiple-quantum-well phototransistor. 1995 , 38, 149-155		2
1495	High temperature operation of GaAs based FETs. 1995 , 38, 339-343		12
1494	Electron transfer between two coupled quantum wells in a resonant tunneling diode structure. 1995 , 38, 1899-1904		5
1493	Thermal stabilization of power HBTs using n-Al _x Ga _{1-x} As emitter ballast resistors with high thermal coefficient of resistance. 1995 , 38, 1657-1661		10
1492	Conception of HEMTs threshold voltage based on the MOSFET model. 1995 , 38, 1109-1112		4
1491	Modelling of amorphous zones in semiconductors by using the randomization-and-relaxation method. 1995 , 102, 202-206		1
1490	Stark effect and Stark-ladder effect in Al _{0.4} Ga _{0.6} As/GaAs asymmetric coupled multiple quantum wells. <i>Journal of Applied Physics</i> , 1995 , 77, 2486-2494	2.5	5
1489	Optical constants of Ga _x In _{1-x} P lattice matched to GaAs. <i>Journal of Applied Physics</i> , 1995 , 77, 3416-3419	2.5	89
1488	Photoluminescence thermal-quenching and carrier localization of AlGaAs disordered superlattices. <i>Journal of Applied Physics</i> , 1995 , 77, 4693-4700	2.5	11
1487	Characteristics of surface acoustic wave propagation in III-V semiconductor quantum well structures. <i>Journal of Applied Physics</i> , 1995 , 78, 5002-5007	2.5	11

1486	Monte Carlo simulation of bulk hole transport in $\text{Al}_x\text{Ga}_{1-x}\text{As}$, $\text{In}_x\text{Al}_{1-x}\text{As}$, and $\text{GaAs}_x\text{Sb}_{1-x}$. <i>Journal of Applied Physics</i> , 1995 , 77, 661-664	2.5	10
1485	Direct Observation of Quasi-Bound States and Band-Structure Effects in a Double Barrier Resonant Tunneling Structure Using Ballistic Electron Emission Microscopy. 1995 , 74, 3427-3430		52
1484	D- states in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ superlattices in a magnetic field. 1995 , 51, 7714-7724		66
1483	Theory of the anisotropy of ultrafast nonlinear refraction in zinc-blende semiconductors. 1995 , 52, 8150-8159		43
1482	In situ study of Fermi-level pinning on n- and p-type GaAs (001) grown by molecular-beam epitaxy using photoreflectance. 1995 , 52, 4674-4676		14
1481	Theoretical study of hole initiated impact ionization in bulk silicon and GaAs using a wave-vector-dependent numerical transition rate formulation within an ensemble Monte Carlo calculation. <i>Journal of Applied Physics</i> , 1995 , 77, 225-232	2.5	19
1480	Nature of anticrossing between donor energy levels in GaAs . 1995 , 51, 4687-4690		4
1479	Low temperature photoluminescence study in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ alloys in the indirect band gap region ($x \geq 0.4$). <i>Journal of Applied Physics</i> , 1995 , 78, 5090-5097	2.5	8
1478	Heavy- and light-hole band crossing in a variable-strain quantum-well heterostructure. 1995 , 51, 5461-5464		4
1477	A double S-type instability in semiconductor heterostructures. <i>Journal of Applied Physics</i> , 1995 , 77, 6067-6069		0
1476	Electronic structure of $(\text{GaAs})_m(\text{AlAs})_n$ superlattices grown in the. 1995 , 52, 7830-7833		
1475	Temperature and doping dependence of the photon recycling effect in $\text{GaAs}/\text{AlGaAs}$ heterostructures. <i>Journal of Applied Physics</i> , 1995 , 77, 4611-4615	2.5	2
1474	Optical intensity modulator based on electrically induced periodic structure.		
1473	Dynamic interaction of bulk acoustic waves with a two-dimensional electron gas at an $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterojunction in strong magnetic fields. 1995 , 52, 2619-2631		4
1472	Magnetotransport in a pseudomorphic $\text{GaAs}/\text{Ga}_{0.8}\text{In}_{0.2}\text{As}/\text{Ga}_{0.75}\text{Al}_{0.25}\text{As}$ heterostructure with a Si delta-doping layer. 1995 , 52, 12218-12231		48
1471	Raman study of band bending at ZnSe/GaAs interfaces. <i>Journal of Applied Physics</i> , 1995 , 77, 1241-1248	2.5	34
1470	Consistent formula for the refractive index of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ below the band edge. <i>Journal of Applied Physics</i> , 1995 , 77, 4667-4672	2.5	19
1469	Free-standing $\text{Al}_{0.30}/\text{Ga}_{0.70}/\text{As}$ thermopile infrared sensor.		

1468	Photoreflectance temperature dependence of graded InAlAs/InGaAs heterojunction bipolar transistor layers. <i>Journal of Applied Physics</i> , 1995 , 78, 4035-4038	2.5	2
1467	Lattice relaxation of AlGaAs layers grown on GaAs(100) substrate plane by organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 1995 , 77, 420-422	2.5	2
1466	Photoluminescence of quaternary GaInAsSb/AlGaAsSb strained multiple quantum wells. <i>Journal of Applied Physics</i> , 1995 , 78, 5696-5700	2.5	23
1465	Lattice constants and thermal expansion of Al _x Ga _{1-x} As:Te. <i>Journal of Applied Physics</i> , 1995 , 78, 6994-6998.	2.5	7
1464	Optimized resonant tunneling light emitting diodes. <i>Journal of Applied Physics</i> , 1995 , 78, 1391-1393	2.5	
1463	Acoustical and optical properties of Ga _{0.52} In _{0.48} P: A Brillouin scattering study. <i>Journal of Applied Physics</i> , 1995 , 77, 6569-6571	2.5	3
1462	Determination of alloy composition in modulation doped Al _x Ga _{1-x} As/GaAs heterostructure. <i>Journal of Applied Physics</i> , 1995 , 77, 172-174	2.5	6
1461	Electron mobility in two-dimensional modulation-doped In _{1-x} Al _x As/In _{1-y} Ga _y As alloy systems. 1995 , 52, 11989-11997		10
1460	Electron-electron interactions, coupled plasmon-phonon modes, and mobility in n-type GaAs. 1995 , 51, 14256-14264		23
1459	Electron transmission through a single nonabrupt GaAs/Al _x Ga _{1-x} As barrier subjected to an electric field. 1995 , 52, 5777-5780		7
1458	Influence of nonuniform doping on the uniformity of current gain, base transit time, and related properties of AlGaAs/GaAs heterojunction bipolar transistors. <i>Journal of Applied Physics</i> , 1995 , 78, 2105-2112	2.5	5
1457	Current characteristics of the double-barrier Al _{0.25} Ga _{0.75} As/Al _{0.45} Ga _{0.55} As/GaAs single-quantum-well structures. 1995 , 52, 5202-5209		3
1456	Phonon satellite strengths in the photoluminescence spectra of a type-II GaAs/Al _{0.3} Ga _{0.7} As superlattice at elevated pressures. 1995 , 51, 9735-9741		7
1455	The effective-medium theory of magnetoplasma superlattices. 1995 , 7, 315-326		12
1454	Molecular Beam Epitaxy of High-Quality GaAs and AlGaAs. 1995 , 114-274		7
1453	Analysis of the capacitance behaviour of Al _x Ga _{1-x} As graded p-n junctions using a model with frozen dopant levels. 1995 , 10, 183-189		
1452	Detection and evaluation of self-heating effects in n ⁺ n ⁺ Al _x Ga _{1-x} As devices by noise temperature measurements. 1995 , 10, 515-522		6
1451	Raman spectroscopic study of the H-CAs complex in epitaxial AlAs. 1995 , 10, 639-644		9

- 1450 The dynamic interaction of bulk acoustic waves with a 2DEG at an AlGaAs/GaAs heterojunction in strong magnetic fields. Elastic field distribution. **1995**, 10, 1089-1098
- 1449 Electronic states in GaAs/Al_{0.3}Ga_{0.7}As non-periodic superlattices. **1995**, 7, 1729-1736 3
- 1448 Polar optical modes in GaAs-AlAs superlattices. **1995**, 51, 526-530 12
- 1447 Valley mixing in resonant tunnelling diodes with applied hydrostatic pressure. **1995**, 10, 1673-1679 16
- 1446 Surface and guided wave polariton modes of magnetoplasma effective films in the Voigt geometry. **1995**, 7, 7023-7035 3
- 1445 Electron-interface phonon scattering in asymmetric semiconductor quantum well structures. **1995**, 4, 356-364
- 1444 Investigation of optical transitions in superlattices using photovoltage spectra. **1995**, 7, 9693-9700 3
- 1443 High temperature optical properties of GaAs/AlGaAs double heterostructures. **1995**, 10, 841-845 1
- 1442 Field dependence of carrier capture in GaAs/AlAs/AlGaAs double-barrier quantum well structures. **1995**, 10, 1329-1338 5
- 1441 Large Lateral Modulation in InAs/GaAs In-Plane Strained Superlattice on Slightly Misoriented (110) InP Substrate. **1995**, 34, L915-L917 3
- 1440 Molecular Beam Epitaxy. **1995**, 84-169
- 1439 The interaction of electrons with optical phonons in embedded circular and elliptical GaAs quantum wires. **1995**, 7, 9819-9831 20
- 1438 Al_xGa_{1-x}As intervalley scattering rates from field-assisted photoemission spectroscopy. **1995**, 51, 4264-4271 4
- 1437 Binding energies and intra-donor absorption spectra in GaAs-GaAlAs quantum wells. **1995**, 10, 41-44 12
- 1436 A simple theoretical analysis of the thermo-electric power in quantum dots of nonparabolic semiconductors in the presence of a parallel magnetic field. **1995**, 5, 769-776 10
- 1435 High-breakdown AlGaAs/InGaAs/GaAs PHEMT with tellurium doping. **1995**, 31, 586-588 8
- 1434 . **1995**, 7, 452-454 32
- 1433 Dynamical screening effects in a coupled quasi-one-dimensional electron-phonon system. **1995**, 7, L669-L673 3

1432	Pressure-induced Hall-effect spectroscopy of silicon DX states in planar doped GaAs-AlAs superlattices. 1995 , 51, 16778-16784		7
1431	Microscopic calculation of the electron-optical-phonon interaction in ultrathin GaAs/Al _x Ga _{1-x} As alloy quantum-well systems. 1995 , 51, 7046-7057		40
1430	Electron-interface-phonon interaction and scattering in asymmetric semiconductor quantum-well structures. 1995 , 51, 17681-17688		29
1429	Interface phonons in spherical GaAs/Al _x Ga _{1-x} As quantum dots. 1995 , 52, 1489-1492		47
1428	In situ measurement of AlAs and GaAs refractive index dispersion at epitaxial growth temperature. 1995 , 67, 244-246		11
1427	Ga ₂ O ₃ films for electronic and optoelectronic applications. <i>Journal of Applied Physics</i> , 1995 , 77, 686-693	2.5	347
1426	Self-consistent BPM model of a waveguide coupler with distributed gain.		
1425	. 1995 , 16, 448-450		5
1424	Influence of cavity length and emission wavelength on the characteristic temperature in AlGaAs lasers. <i>Journal of Applied Physics</i> , 1995 , 77, 4259-4262	2.5	3
1423	First-principles pseudopotential study of the phase stability of the III-V semiconductors GaAs and AlAs. 1995 , 52, 8881-8892		78
1422	Characterization of low-temperature Al _x Ga _{1-x} As lattice properties using high resolution x-ray diffraction. <i>Journal of Applied Physics</i> , 1995 , 77, 4452-4454	2.5	2
1421	. 1995 , 1, 110-116		10
1420	. 1995 , 1, 442-450		21
1419	. 1995 , 1, 638-648		11
1418	High-speed photoluminescence mapping of III-V epitaxial layers for light-emitting diodes. 1995 , 1, 987-992		2
1417	Interferometric near-field imaging technique for phase and refractive index profiling in large-area planar-waveguide optoelectronic devices. 1995 , 1, 1017-1029		2
1416	Nonequilibrium electron distributions and high-field electron transport in an Al _x Ga _{1-x} As-based p-i-n nanostructure semiconductor-a picosecond Raman probe. 1995 , 1, 1093-1099		2
1415	Photoluminescence, Raman, and infrared diagnosis of GaAs-AlGaAs superlattices for intersubband infrared detection. 1995 , 1, 1119-1125		0

1414	. 1995 , 31, 101-112		6
1413	. 1995 , 31, 228-232		5
1412	. 1995 , 31, 1216-1222		9
1411	. 1995 , 31, 1648-1658		10
1410	. 1995 , 31, 1668-1673		33
1409	. 1995 , 31, 1863-1875		17
1408	Band structure calculations of Ga _{1-x} Al _x As, GaAs _{1-x} P _x and AlAs under pressure. 1995 , 3, 393-401		11
1407	Hole transport properties of bulk zinc-blende and wurtzite phases of GaN based on an ensemble Monte Carlo calculation including a full zone band structure. <i>Journal of Applied Physics</i> , 1996 , 80, 4429-4436	2.5	64
1406	Contribution of single InGaAs quantum wells to the guided mode dispersion of InGaAs/GaAs/AlGaAs waveguides: Model and experimental results. <i>Journal of Applied Physics</i> , 1996 , 80, 6039-6044	2.5	
1405	Thermal crosstalk in 4 x 4 vertical-cavity surface-emitting laser arrays. 1996 , 8, 980-982		28
1404	Modeling the optical dielectric function of GaAs and AlAs: Extension of Adachi's model. <i>Journal of Applied Physics</i> , 1996 , 80, 5909-5914	2.5	91
1403	Excitons in Multi-Valley Semiconductors. 1996 , 17-40		
1402	Summary and Outlook. 1996 , 173-177		
1401	Resonant Raman scattering in GaAs/AlAs superlattices: The role of electron state mixing. 1996 , 53, 3960-3965		7
1400	Screening effects on the confined and interface polarons in cylindrical quantum wires. 1996 , 53, 10866-10870		15
1399	A computational approach to the analysis of distributed Bragg reflectors in direct-gap solar cells. 1996 ,		2
1398	Spatially localized band-gap renormalization and band-filling effects in three growth-interrupted multiple asymmetric coupled narrow quantum wells. 1996 , 13, 536		3
1397	Effect of four-wave mixing on copropagating spatial solitons. 1996 , 13, 1419		8

1396	Characterisation of buried lateral period superlattices by ballistic electron emission microscopy. 1996 , 352-354, 802-806	4
1395	An optical and electrical study of tunnelling mechanisms through indirect gap single barrier GaAs/AlAs/GaAs heterostructures. 1996 , 361-362, 197-200	1
1394	Measurement of spontaneous-emission enhancement near the one-dimensional photonic band edge of semiconductor heterostructures. 1996 , 53, 2799-2803	118
1393	Binding energy of the complex (D ⁺ -X) with Gamma -X mixing in GaAs/AlAs quantum wells. 1996 , 54, 13996-14002	2
1392	Modeling the near-gap refractive index properties of semiconductor multiple quantum wells and superlattices. 1996 , 2, 197-209	7
1391	Nonlinear gain coefficients in semiconductor lasers: effects of carrier heating. 1996 , 32, 201-212	49
1390	Characteristics of multistack multiquantum barrier and its application to graded-index separate confinement heterostructure lasers. 1996 , 32, 442-447	3
1389	Low-voltage vertical directional coupler switch with suppressed electroabsorption. 1996 , 32, 1048-1053	1
1388	Optimized second-harmonic generation in asymmetric double quantum wells. 1996 , 32, 1334-1346	26
1387	Eigenstates and absorption spectra of interdiffused AlGaAs-GaAs multiple-quantum-well structures. 1996 , 32, 1399-1416	36
1386	On the thermal characterization of two-layer systems by means of the photoacoustic effect. 1996 , 29, 981-986	23
1385	Electrical conduction in semiconductor junctions with interface dipole layers. <i>Journal of Applied Physics</i> , 1996 , 80, 941-947	2.5 3
1384	AlGaAs below half bandgap: a laboratory for spatial soliton physics. 1996 , 5, 583-594	9
1383	Flexible approach to exciton binding energies in type-I and type-II quantum wells. 1996 , 53, 1485-1489	13
1382	High-finesse resonant-cavity photodetectors with an adjustable resonance frequency. 1996 , 14, 1081-1089	28
1381	A modified charge-control model for HEMTs.	
1380	Vertical transport of hot carriers in multibarrier heterostructure diode.	
1379	GaAs monolithic integrated microwave power sensor in coplanar waveguide technology.	2

1378	Polaron properties in quantum wells. 1996 , 53, 1438-1445			18
1377	Photoelectric emission from quantum wells with various potential profiles.			
1376	Schottky contacts and conduction band offsets in bandgap engineered InGaAlAs/InP heterostructures.			1
1375	Transport mechanism of Gamma - and X-band electrons in Al _x Ga _{1-x} As/AlAs/GaAs double-barrier quantum-well infrared photodetectors. 1996 , 54, 2059-2066			8
1374	Modal characteristics of graded multilayer optical waveguides. 1996 , 14, 894-900			4
1373	Effect of magnetic field on the binding energy of a hydrogenic donor in a z ^{2/3} quantum well. 1996 , 54, 651-656			3
1372	Spectroscopic investigation of single quantum well structures of semiconductors.			
1371	Characteristics of a quantum waveguide: Effects of finite confinement potential and geometrical deformations and comparison with simple theoretical approach. <i>Journal of Applied Physics</i> , 1996 , 79, 7021-7028	2.5		11
1370	Ion Implantation for High Performance III-V Jfets and Hfets. 1996 , 421, 209			
1369	Structural and Optical Characterization of Al _x Ga _{1-x} As Grown at Low Temperatures by Organometallic Vapor Phase Epitaxy. 1996 , 442, 479			2
1368	Optical Determination of the Heavy-hole Effective Mass of (In, Ga)As/GaAs Quantum Wells. 1996 , 17, 13-24			9
1367	Hydrostatic-pressure coefficient of the direct band-gap energy of Al _x Ga _{1-x} As for x=0-0.35. 1996 , 53, 10916-10920			8
1366	1890P1 - 71A4. 333-345			
1365	Design of flat-band AlGaAs heterojunction Bragg reflectors. 1996 , 43, 40-46			4
1364	Free-standing AlGaAs thermopiles for improved infrared sensor design. 1996 , 43, 1193-1199			8
1363	An accurate large-signal physical model for microwave GaAs/AlGaAs HBTs. 1996 , 6, 153-165			1
1362	Resonant spin-flip Raman scattering and localized exciton luminescence in submonolayer InAs-GaAs structures. 1996 , 97, 169-174			17
1361	Strain and critical layer thickness analysis of carbon-doped GaAs. 1996 , 97, 875-878			9

1360	Comment on phonon polariton modes in semiconductor superlattices 1996 , 98, 337-339	3
1359	Quantum confined Stark shift in arbitrarily shaped single quantum wells by Fourier series method. 1996 , 99, 299-303	8
1358	AlGaAs optical phonon replicas in the photoluminescence spectra of GaAs layer in an Al _{0.3} Ga _{0.7} As/GaAs heterostructure. 1996 , 98, 1053-1056	3
1357	Effective-phonon approximation of polarons in ternary mixed crystals. 1996 , 100, 629-634	34
1356	Monte Carlo simulation of real and reciprocal space transfer of electrons in a pseudomorphically strained GaAs/In _{0.15} Ga _{0.85} As/GaAs quantum well. 1996 , 39, 601-610	2
1355	Growth and optical investigation of quaternary quantum wells. 1996 , 40, 143-147	1
1354	Electromodulation spectroscopy study of symmetry forbidden transitions in a single quantum well grown using a tertiarybutylarsine source. 1996 , 39, 885-890	
1353	Carrier transport simulation for bulk Al _x Ga _{1-x} As with a Γ -X band structure based on Lei-Ting balance equations. 1996 , 39, 971-975	3
1352	Resonant tunneling characteristics of a delta-doped strained-layer quantum-well switching device (ESQSD). 1996 , 39, 1637-1641	1
1351	Tunneling phenomena from non-equilibrium carrier distributions in semiconductor heterostructures. 1996 , 225, 76-88	2
1350	Effect of an electric field on electron-interface-phonon scattering in a graded quantum well. 1996 , 215, 309-316	1
1349	Photoreflectance study of resonant asymmetric double quantum wells with Si doping in side barriers. 1996 , 92, 543-546	1
1348	Properties of metal-clad dielectric waveguides in near cutoff. 1996 , 129, 173-176	3
1347	Nonlinear phase shift by cascaded quasi-phase-matched second harmonic generation. 1996 , 131, 102-106	9
1346	Study of generation of GaIn _{1-x} PyAs _{1-y} transition layers obtained by liquid phase epitaxy. 1996 , 158, 241-247	3
1345	Photoluminescence studies on the interaction of near-surface GaAs/Al _x Ga _{1-x} As quantum wells with chemical adsorbates. 1996 , 101, 113-117	2
1344	Photoluminescence of heavily doped GaAs/AlGaAs quantum wells in high magnetic fields. 1996 , 217-218, 184-188	
1343	Ultra-thin AlAs films on GaAs (001) investigated by high-resolution electron-energy-loss spectroscopy. 1996 , 104-105, 601-607	

- 1342 Very large blue and red Stark shifts of the excitonic transition in InGaAs-InP-InAsP antisymmetric coupled quantum wells. **1996**, 28, 1305-1320
- 1341 The ground state energy of a bound polaron in the presence of a magnetic field. **1996**, 197, 411-419 5
- 1340 Investigation of Dopant Segregation in GaAs/AlAs Short-Period Superlattices by Hall Effect under High Pressure. **1996**, 198, 301-305 3
- 1339 Intersubband transitions in strained In_{0.07}Ga_{0.93}As/Al_{0.40}Ga_{0.60}As multiple quantum wells and their application to a two-colors photodetector. **1996**, 54, 5620-5628 32
- 1338 Interband transitions in Al_xGa_{1-x}As/AlAs quantum-well structures. **1996**, 53, 12912-12916
- 1337 Photoconductivity measurement of the phonon absorption by a two-dimensional hole gas in a GaAs heterojunction. **1996**, 54, 2019-2027 24
- 1336 Pressure dependence of the optic phonon energies in Al_xGa_{1-x}As. **1996**, 54, 8714-8720 39
- 1335 Optical observation of impurity localized states at the edges of Landau subbands in doped quantum wells. **1996**, 54, 2756-2762 5
- 1334 E1 transition in (113)-oriented GaAs/AlAs multiple quantum wells: Confinement effects and optical anisotropy. **1996**, 53, 6912-6914 3
- 1333 Electric-field-dependent intersubband transition via optical phonons in a doped-thin-layer inserted quantum-well structure. **1996**, 54, 16983-16988 10
- 1332 Strain-induced band-gap modulation in GaAs/AlGaAs quantum-well structure using thin-film stressors. *Journal of Applied Physics*, **1996**, 79, 1763-1771 2.5 4
- 1331 Hot carrier transport in multibarrier heterostructure diode. *Journal of Applied Physics*, **1996**, 80, 1242-1244 12
- 1330 Observation of Internal Transitions of Confined Excitons in GaAs/AlGaAs Quantum Wells. **1996**, 77, 1135-1138 55
- 1329 Magnetophonons in short-period superlattices. **1996**, 54, 14540-14549 11
- 1328 Dissipative quantum transport in a quantum wire. **1996**, 53, 10951-10972 1
- 1327 Direct calculation of the transport properties of disordered AlAs/GaAs superlattices from the electronic and phonon spectra. **1996**, 53, 2010-2019 18
- 1326 Bound and resonant electron states in quantum dots: The optical spectrum. **1996**, 54, 2667-2674 82
- 1325 Monte Carlo study of electron transport in III-V heterostructures with doped quantum wells. *Journal of Applied Physics*, **1996**, 80, 928-935 2.5 14

1324	Theory of Raman spectra of heavily doped semiconductor multiple quantum wells. 1996 , 54, 11517-11527		1
1323	Optimization of light emitting diodes based on bipolar double-barrier resonant-tunneling structures.		
1322	Piezoelectric effect in (001)- and (111)-oriented double-barrier resonant tunneling devices. <i>Journal of Applied Physics</i> , 1996 , 79, 7770-7774	2.5	15
1321	Resonant tunneling in (001)- and (111)-oriented III-V double-barrier heterostructures under transverse and longitudinal stresses. <i>Journal of Applied Physics</i> , 1996 , 79, 7763-7769	2.5	6
1320	Majority and minority electron and hole mobilities in heavily doped gallium aluminum arsenide. <i>Journal of Applied Physics</i> , 1996 , 80, 3844-3853	2.5	14
1319	Deep acceptorlike states in Si doped molecular-beam-epitaxial-grown Al _x Ga _{1-x} As. <i>Journal of Applied Physics</i> , 1996 , 80, 859-863	2.5	1
1318	Effect of disorder-induced band mixing on the conduction-band effective mass of InAlGaAs alloys lattice matched to InP. <i>Journal of Applied Physics</i> , 1996 , 80, 1239-1241	2.5	10
1317	Indented barrier resonant tunneling rectifiers. <i>Journal of Applied Physics</i> , 1996 , 80, 4174-4176	2.5	12
1316	Tunneling escape time of electrons from the quasibound Stark localized states in ultrathin barrier GaAs/AlAs superlattices. 1996 , 54, 17724-17729		8
1315	n-type ion implantation doping of Al _x Ga _{1-x} As (0 ≤ x ≤ 0.7). <i>Journal of Applied Physics</i> , 1996 , 80, 2132-2137	2.5	1
1314	A model for the current instabilities in GaAs-AlGaAs heterojunction. <i>Journal of Applied Physics</i> , 1996 , 79, 1955-1960	2.5	1
1313	Nonlocal Photorefractive Screening from Hot Electron Velocity Saturation in Semiconductors. 1996 , 77, 4249-4252		26
1312	Electrooptical Properties of the Si Doped GaAs/AlGaAs Triple-Barrier Resonant Tunneling Structure. 1996 , 35, 551-556		1
1311	The indentation response of GaAs/AlAs heterostructures. 1996 , 74, 1185-1194		5
1310	Capacitance and conductance of semiconductor heterojunctions with continuous energy distribution of interface states. <i>Journal of Applied Physics</i> , 1996 , 80, 6839-6848	2.5	26
1309	Intra- and Intersubband Transition Rates Due to Emission of Optic Phonons in Quantum Wells: Effects of The Subband Nonparabolicity. 1996 , 73-75		
1308	Optical properties of quaternary GaInAsSb/AlGaAsSb strained quantum wells. 1996 , 8, 4751-4766		7
1307	Magneto-optical absorption spectra of periodic superlattices under in-plane magnetic fields. 1996 , 8, 8705-8716		

1306	.	
1305	Pulsed characterization of vertical gallium arsenide (GaAs) optically activated switches. 1996 , 29, 2179-2185	
1304	Far-infrared spectra of reflectivity, transmission and hot-hole emission in p-doped multiple quantum wells. 1996 , 11, 323-330	10
1303	Picosecond photoluminescence studies of carrier escape processes in a single quantum well. 1996 , 11, 331-339	12
1302	A dual-wavelength vertical-cavity surface-emitting laser involving both the first and the second quantum states. 1996 , 5, 35-44	1
1301	Optical-phonon modes and electron-optical-phonon interaction in a coupled quantum well. 1996 , 5, 438-449	
1300	The electronic contribution to the elastic constants in ultrathin films of ternary and quaternary alloys in the presence of an arbitrarily oriented magnetic field: theory and suggestion for experimental determination. 1996 , 7, 110-116	22
1299	Modification of Fano resonances by resonant polaron coupling in bulk GaAs. 1996 , 11, 1411-1415	6
1298	Electroluminescence from double-barrier resonant-tunnelling structures. 1997 , 12, 535-543	2
1297	Submillimetre negative differential conductivity at the cyclotron frequency in As in strong fields. 1997 , 9, 4659-4667	
1296	The effect of electron effective mass mismatch on the electron - optical-phonon scattering rate in a quantum well structure. 1997 , 12, 1235-1239	5
1295	Heterojunction Bipolar Transistor with an Additional Minority Carrier Reflection Barrier in the Emitter. 1997 , 36, 6694-6698	
1294	Corrections to the calculation of bulk electron densities in quantum wells of HEMTs. 1997 , 12, 100-110	8
1293	Tailored carrier escape rates in asymmetric double quantum wells. 1997 , 12, 35-41	8
1292	Monte Carlo study of diffusion phenomena in III - V modulation doped heterostructures. 1997 , 12, 69-76	7
1291	Nonparabolicity effects on electron-optical-phonon scattering rates in quantum wells. 1997 , 56, 9619-9624	14
1290	Effective-mass reproducibility of the nearest-neighbor sp^3s^* models: Analytic results. 1997 , 56, 4102-4107	48
1289	Dipole relaxation in dispersive photonic band-gap structures. 1997 , 55, 1454-1461	11

1288	Charge transfer between In and Ga in InGaAs-based alloys. 1997 , 56, 3567-3570		4
1287	Investigation of L-related indirect transitions in GaAs/GaAlAs multi-quantum wells under hydrostatic pressure. <i>Journal of Applied Physics</i> , 1997 , 82, 6359-6361	2.5	2
1286	Theory of potential modulation in lateral surface superlattices. II. Piezoelectric effect. 1997 , 56, 15242-15251		37
1285	Local modulation of the quantum-well quasicontinuum states using charged-carrier transfer induced by intersubband transitions. 1997 , 56, 9239-9242		9
1284	Observation of EX resonances in type-I GaAs/AlAs semiconductor superlattices: Anomaly in photoluminescence. 1997 , 55, 13689-13696		14
1283	Effects of electron-hole energy transfer on the nonlinear gain coefficients in the small-signal modulation response of semiconductor lasers. 1997 , 71, 1747-1749		7
1282	Electronic confinement in a single GaAs quantum well probed by low-frequency resonant Raman scattering. 1997 , 56, 1486-1490		13
1281	Observation of Standing Acoustic Waves by Resonant Raman Scattering. 1997 , 78, 4119-4122		8
1280	Effects of quantum size and potential shape on the spectra of an electron and a donor in quantum dots. 1997 , 55, 1673-1679		48
1279	Dynamics of the single barrier heterostructure hot electron diode. <i>Journal of Applied Physics</i> , 1997 , 82, 1706-1710	2.5	9
1278	Self-consistent calculation of discrete and continuous states in spherical semiconductor quantum dots. 1997 , 55, 15681-15687		8
1277	Coupled-mode description for the polarization state of a vertical-cavity semiconductor laser. 1997 , 55, 1473-1484		38
1276	Effect of the type-I to type-II transition on the binding energy of shallow donors in GaAs/AlAs quantum wells. 1997 , 55, 15420-15422		4
1275	On the inversion in GaAs metal-insulator-semiconductor heterostructures. 1997 , 70, 228-230		2
1274	The effect of electron effective mass mismatch on electron - phonon scattering rate in a quantum well. 1997 , 12, 296-299		5
1273	The influence of the self-consistency on intraband optical transitions in semiconductor quantum dot.		
1272	Multilayer analysis of anisotropic heat flux in vertical cavity surface emitting lasers with quarter wave semiconducting mirrors.		
1271	High Temperature Characteristics of Strained InGaAs/InGaAlAs Quantum Well Lasers. 1997 , 36, 3528-3530		4

1270	Photoreflectance Study of Barrier-Width Dependence of Above-Barrier States in GaAs-AlxGa1-xAs Multiple Quantum Wells. 1997 , 36, 5448-5450		1
1269	Aluminum Arsenide (AlAs). 1997 , 489-499		1
1268	Aluminum Gallium Arsenide (AlxGa1-xAs). 1997 , 513-558		2
1267	Exciton-phonon interaction effects in quantum wells. 1997 , 56, 2058-2061		17
1266	Thickness effect on impurity-bound polaronic energy levels in a parabolic quantum dot in magnetic fields. 1997 , 56, 14913-14916		51
1265	Linear in-plane uniaxial stress effects on the device characteristics of AlGaAs/GaAs modulation doped field effect transistors. <i>Journal of Applied Physics</i> , 1997 , 81, 502-505	2.5	7
1264	Coupling coefficient, temperature stability and mass sensitivity of the Rayleigh-type mode on (001) [110] AlAs/GaAs. 1997 , 6, 721-729		4
1263	Ballistic-electron-emission spectroscopy of AlxGa1-xAs/GaAs heterostructures: Conduction-band offsets, transport mechanisms, and band-structure effects. 1997 , 56, 2026-2035		34
1262	Optical properties of bulk AlGaAs. <i>Journal of Applied Physics</i> , 1997 , 82, 792-797	2.5	15
1261	Chapter 5 AlGaInP Light-Emitting Diodes. 1997 , 48, 149-C3		20
1260	Chapter 3 AlGaAs Red Light-Emitting Diodes. 1997 , 48, 65-96		9
1259	Controlled type-I/type-II transition in GaAs/AlAs/AlxGa1-xAs double-barrier quantum wells. 1997 , 55, 2393-2400		9
1258	Electron-wave interference effects in a Ga1-xAlxAs single-barrier structure measured by ballistic electron emission spectroscopy. 1997 , 71, 2292-2294		4
1257	Polaron effects in asymmetric semiconductor quantum-well structures. 1997 , 55, 4670-4679		30
1256	Calculation of the Refractive Index of Compound Semiconductors Below the Band Gap. 1997 , 125-149		
1255	Energy relaxation via confined and interface phonons in quantum-wire systems. 1997 , 55, 7165-7169		15
1254	Temperature dependence of luminescence spectra related to free carrier and exciton recombination in GaAs quantum wells. 1997 , 56, 308-314		16
1253	Infrared Reflectivity Determination of Alloy Composition in AlxGa1-xAs and InxGa1-xAs Structures. 1997 , 51, 433-437		3

1252	Effect of four-wave mixing on spatial soliton collisions. 1997 , 14, 298		4
1251	Field-induced refractive index variations in GaAs/AlGaAs multiple quantum well waveguide modulator. 1997 , 1, 48-51		
1250	Transfer matrix method for interface optical-phonon modes in multiple-interface heterostructure systems. <i>Journal of Applied Physics</i> , 1997 , 82, 3363-3367	2.5	72
1249	Electronic structure of strained-layer quantum wells. 1997 , 387, 371-382		3
1248	Sol-gel synthesis of fluoride optical materials for planar integrated photonic applications. 1997 , 213-214, 126-136		27
1247	Composition of AlGaAs. <i>Journal of Applied Physics</i> , 1997 , 81, 1683-1694	2.5	78
1246	Electro-opto-thermal modeling of threshold current dependence on temperature. 1997 , 3, 640-648		9
1245	Optical modeling of quantum wire arrays. 1997 , 33, 375-381		8
1244	Acoustooptic interactions in AlGaAs-GaAs planar multilayer waveguide structures. 1997 , 33, 1601-1607		9
1243	Selective quantum-well intermixing in GaAs-AlGaAs structures using impurity-free vacancy diffusion. 1997 , 33, 1784-1793		104
1242	Numerical simulation of broad-area high-power semiconductor laser amplifiers. 1997 , 33, 2240-2254		21
1241	Relaxation of hot quasi-two-dimensional excitons. 1997 , 71, 245-253		2
1240	Analysis of the temperature dependence of current gain in heterojunction bipolar transistors. 1997 , 44, 17-24		11
1239	Performance of antireflecting coating-AlGaAs window layer coupling for terrestrial concentrator GaAs solar cells. 1997 , 44, 1499-1506		19
1238	Acoustic phonon modes of rectangular quantum wires. 1997 , 9, 5751-5764		82
1237	Interaction between an electron and optical phonons in polar semiconductor heterostructures. 1997 , 100, 353-364		4
1236	Polariton modes in semiconductor superlattices. 1997 , 101, 367-371		7
1235	Critical review of the epitaxial growth of semiconductors by rapid thermal chemical vapor deposition. 1997 , 20, 1-36		4

1234	Calculation of the elastic properties of CuCl. 1997 , 228, 378-382	12
1233	Polar optical modes in semiconductor nanostructures. 1997 , 28, 123-176	38
1232	Surface potential mapping: A qualitative material contrast in SPM. 1997 , 69, 39-49	174
1231	Photoreflectance investigations of complex structures. 1997 , 48, 283-287	3
1230	Alloy composition and temperature dependence of the direct energy gap in Al _x Ga _{1-x} As. 1997 , 58, 1111-1114	11
1229	A transient method of thermal characterization of double heterostructure laser diodes. 1997 , 28, 301-312	4
1228	Resonant Raman scattering by interface phonons in type II GaAs/AlAs superlattices. 1997 , 104, 361-365	
1227	Intrasubband electron-phonon scattering in doped thin-layer inserted quantum well. 1997 , 104, 689-694	
1226	The self-consistent electronic structure of spherical semiconductor quantum dots including bound and free states. 1997 , 103, 319-323	3
1225	A Ga ₂ O ₃ passivation technique compatible with GaAs device processing. 1997 , 41, 643-646	9
1224	Physical models for strained and relaxed GaInAs alloys: Band structure and low-field transport. 1997 , 41, 1139-1152	38
1223	Analytical model for abrupt HBTs with application to type. 1997 , 41, 1277-1283	5
1222	Electric field induced shifts of electronic energy levels in spherical quantum dot. 1997 , 41, 1383-1385	13
1221	Interfacial behaviour of a quantum well electrode electrolyte: EER spectra of an SQW GaAs Al _x Ga _{1-x} As electrode in HQ + BQ non-aqueous electrolyte. 1997 , 430, 91-95	2
1220	Temperature Dependence of τ_{0} to Xz Electron Transfer Times in Type-II GaAs/AlAs Superlattices. 1997 , 204, 198-200	
1219	Coherent Plasmon-Phonon Oscillations in a GaAs Schottky Barrier Sample. 1997 , 204, 91-94	
1218	Photoreflectance Study of [111] GaAs/AlGaAs Quantum Wells at Room Temperature. 1997 , 164, 117-121	6
1217	SOLUTION OF THE COUPLED POISSON-SCHRÖDINGER EQUATIONS USING THE MULTIGRID METHOD. 1997 , 10, 121-136	5

1216	Setting limits on the accuracy of X-ray determination of Al concentration in epitaxial layers. 1997 , 172, 25-36		19
1215	Determination of Al _x Ga _(1-x) As composition: the MBE perspective. 1997 , 175-176, 238-243		2
1214	Formation mechanism of volcano-like structural defects in multiple periods of InAs quantum dots on GaAs. 1997 , 182, 292-298		9
1213	Simultaneous determination of the thermal diffusivity of semiconductor lasers and resistance of their adhesive joints. 1998 , 41, 1585-1599		2
1212	Heterojunction band offsets and Schottky-barrier heights: Tersoff's theory in the presence of strain. 1998 , 58, 7864-7871		18
1211	Elastic and piezoelectric fields around a buried quantum dot: A simple picture. <i>Journal of Applied Physics</i> , 1998 , 84, 1358-1365	2.5	140
1210	Resolution and contrast in Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 1998 , 84, 1168-1173.	3.5	424
1209	Negative dynamic differential conductivity at the cyclotron frequency in Ga _{1-x} Al _x As under conditions of ballistic intervalley electron transfer. 1998 , 32, 148-153		
1208	Photoelectrical memory in GaAs/AlGaAs multilayer quantum-well structures. 1998 , 32, 189-194		
1207	Local neutrality and pinning of the chemical potential in III-V solid solutions: Interfaces and radiation effects. 1998 , 32, 284-287		5
1206	Influence of defects on the temperature dependence of the density of electrons in the two-dimensional and doped channels of selectively doped Al _x Ga _(1-x) As/GaAs heterostructures. 1998 , 43, 1266-1268		
1205	Giant population inversion of hot electrons in GaAs/AlAs type heterostructures with quantum wells. 1998 , 68, 78-83		7
1204	Study of the nature of light hole excitonic transitions in InGaAs/GaAs quantum well. 1998 , 50, 199-201		3
1203	Lateral resolution in laser-patterned thermal processing of GaAs. 1998 , 125, 325-331		1
1202	Real-time photo-spectroscopic ellipsometry measurement of electric field and composition in semiconductors. 1998 , 313-314, 579-582		2
1201	Spin splitting effect on the effective mass of GaAs/Al Ga _{1-x} As quantum wells. 1998 , 43-44, 147-152		
1200	The influence of interfacial growth patterns on the transmission of electrons through nonabrupt GaAs/Al Ga _{1-x} As double-barriers. 1998 , 43-44, 371-375		
1199	Predicting nonlinear electrical performance in single and multiple quantum-barrier varactors (QBV's) by the Monte Carlo technique. 1998 , 45, 1399-1406		

1198	Simulation and design of InAlAs/InGaAs pnp heterojunction bipolar transistors. 1998 , 45, 1634-1643	30
1197	Multilayer analysis of anisotropic heat flux in vertical cavity-surface emitting lasers with quarter-wave semiconducting mirrors. 1998 , 46, 208-214	6
1196	Effects of carrier heating, nonequilibrium LO phonons and lattice heating on small-signal modulation response of semiconductor lasers. 1998 , 145, 13-20	3
1195	Interface phonons in cylindrical GaAsAl _x Ga _{1-x} As quantum dots. 1998 , 106, 341-345	9
1194	Validity of Vegard's rule for the lattice parameter and the stiffness elastic constant ratios of the AlGaAs ternary compound. 1998 , 108, 77-81	9
1193	Validity of Vegard's rule for the lattice parameter and the stiffness elastic constant ratios of the AlGaAs ternary compound. 1998 , 108, 599-603	11
1192	HBT thermal element design using an electro/thermal simulator. 1998 , 42, 857-864	11
1191	Perturbation calculation of donor states in a spherical quantum dot. 1998 , 42, 1661-1663	45
1190	Improvement of life time of minority carriers in GaAs epi-layer grown on Ge substrate. 1998 , 50, 273-280	4
1189	Polaron in a quantum disk. 1998 , 245, 92-102	26
1188	Stability of regular orbits in ballistic quantum dots. 1998 , 249-251, 368-372	3
1187	Effect of a parabolic potential on the impurity binding energy in spherical quantum dots. 1998 , 253, 238-241	83
1186	Theoretical study of pion damage in A ₃ B ₅ compounds. 1998 , 413, 242-248	9
1185	Direct band gap determination in Al _x Ga _{1-x} As epitaxial layers in the indirect gap region 0.4 1998 , 123-124, 513-516	4
1184	Interdiffusion induced modification of surface-acoustic-wave AlGaAs-GaAs quantum-well modulators. 1998 , 4, 758-764	2
1183	The effects of surface acoustic waves on the optical properties of AlGaAs-GaAs quantum-well structures. 1998 , 34, 300-306	2
1182	Theoretical model for intravalley and intervalley free-carrier absorption in semiconductor lasers: beyond the classical Drude model. 1998 , 34, 552-559	44
1181	. 1998 , 34, 700-706	27

1180	A versatile impedance boundary method of moments computational technique for solving the one-dimensional Schrodinger equation with application to quantum well and quantum wire problems. 1998 , 34, 1171-1179	3
1179	Impact of planar microcavity effects on light extraction-Part II: selected exact simulations and role of photon recycling. 1998 , 34, 1632-1643	101
1178	Mode analysis of semiconductor lasers using lateral confinement by native-oxide layers. 1998 , 34, 1953-1958	2
1177	On the capacitance-voltage modeling of strained quantum-well MODFETs. 1998 , 34, 2314-2320	8
1176	Nonequilibrium spatiotemporal dynamics of the Wigner distributions in broad-area semiconductor lasers. 1998 , 57, 2150-2162	15
1175	Apparent metallic behavior at B=0 of a two-dimensional electron system in AlAs. 1998 , 57, R15068-R15071	81
1174	Photoluminescence detection of the X-electron resonance in a GaAs/AlAs type-II superlattice. 1998 , 58, 7216-7221	1
1173	Minimum temperature sensitivity of 1.55 μ m vertical-cavity lasers at 50 nm gain offset. 1998 , 72, 1814-1816	62
1172	.	
1171	Self-consistent calculation of facet heating in asymmetrically coated edge emitting diode lasers. 1998 , 13, 265-276	17
1170	Thermal degradation of Al/AlGaAs Schottky junctions.	0
1169	Role of the X minimum in transport through AlAs single-barrier structures. 1998 , 58, 10619-10628	19
1168	Band-tail parameter modeling in semiconductor materials. 1998 , 58, 1907-1911	30
1167	Exciton binding energies in polar quantum wells with finite potential barriers. 1998 , 58, 10769-10777	33
1166	Observation of direct and phonon-assisted indirect transitions in GaAs/GaxAl $_{1-x}$ As multiquantum wells under hydrostatic pressure. 1998 , 57, 6566-6572	13
1165	Polarization-insensitive electroabsorption by use of quantum well interdiffusion. 1998 , 37, 1674-81	10
1164	Intersubband laser coupled three-level asymmetric quantum wells: new dynamics of quantum interference. 1998 , 15, 1578	9
1163	Binding energy of impurity states in spherical quantum dots with parabolic confinement. <i>Journal of Applied Physics</i> , 1998 , 83, 3089-3091	2.5 118

1162	Tunneling under Pressure: High-Pressure Studies of Vertical Transport in Semiconductor Heterostructures. 1998 , 55, 45-116		4
1161	A simple method for the determination of superlattice band structures. <i>Journal of Applied Physics</i> , 1998 , 83, 867-869	2.5	7
1160	Negative-differential-resistance characteristics in a triangular-barrier resonant tunnelling switch. 1998 , 13, 231-235		3
1159	Spin Dependent Luminescence of GaAs Thin Layers under Tensile Strain and Compressive Strain Induced by Interface Stress. 1998 , 37, 854-857		
1158	Monte Carlo simulation of electron transport in highly delta-doped GaAs/AlGaAs quantum wells. 1998 , 13, 43-53		7
1157	3D simulation of GaAs/AlGaAs quantum dot point contact structures. 1998 , 13, A37-A40		10
1156	Interface-related band-bending effects on intersubband transitions in doped single quantum wells. 1998 , 10, 9681-9686		
1155	Influence of the undoped spacer layer thickness on the DC characteristics of n-type GaAs/AlAs MESFETs. 1998 , 13, 318-321		1
1154	Calculation of hole mobilities in relaxed and strained SiGe by Monte Carlo simulation. 1998 , 13, 680-691		12
1153	First-principles calculations of band offsets. 1998 , 10, 577-580		5
1152	Carrier pocket engineering to design superior thermoelectric materials using GaAs/AlAs superlattices. 1998 , 73, 2950-2952		98
1151	In-line fiber-optic filter using GaAs ARROW waveguide. 1998 ,		
1150	Thermopower measurements of the coupling of phonons to electrons and composite fermions. 1998 , 58, 2017-2025		42
1149	Electrophonon resonance in cylindrical quantum wires. 1998 , 58, 3580-3583		19
1148	Electron self-energy in quantum dots. 1998 , 57, R2061-R2064		64
1147	Impact ionization in Al _x Ga _{1-x} As/GaAs single heterostructures. <i>Journal of Applied Physics</i> , 1998 , 84, 4363-4369		15
1146	Holographic storage media based on optically active bistable defects. <i>Journal of Applied Physics</i> , 1998 , 83, 661-673	2.5	22
1145	Optical-phonon scattering in quasi-two-dimensional heterojunction systems. 1998 , 58, 2102-2106		6

1144	Theory of potential modulation in lateral surface superlattices. III. Two-dimensional superlattices and arbitrary surfaces. 1998 , 58, 10789-10799		12
1143	Magnetically tuned wide-band quantum well infrared photodetectors. <i>Journal of Applied Physics</i> , 1998 , 83, 4531-4539	2.5	1
1142	A combined scanning tunneling microscopy and electron energy loss spectroscopy study on the formation of thin, well-ordered Ga_2O_3 films on $\text{CoGa}(001)$. <i>Journal of Applied Physics</i> , 1998 , 83, 2533-2538	2.5	58
1141	Wave propagation in layered piezoelectric structures. <i>Journal of Applied Physics</i> , 1998 , 83, 4652-4659	2.5	21
1140	Interface effects on magnetopolarons in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells at high magnetic fields. 1998 , 58, 7822-7828		5
1139	In-plane uniaxial stress effects of $\text{AlGaAs}/\text{GaAs}$ modulation doped heterostructures characterized by the transmission line method. <i>Journal of Applied Physics</i> , 1998 , 84, 3741-3746	2.5	10
1138	High dopant and carrier concentration effects in gallium aluminum arsenide: Densities of states and effective intrinsic carrier concentrations. <i>Journal of Applied Physics</i> , 1998 , 83, 3102-3110	2.5	20
1137	Optical coupling in quantum well infrared photodetector by diffraction grating. <i>Journal of Applied Physics</i> , 1998 , 84, 5750-5755	2.5	24
1136	Interaction of surface acoustic waves with a narrow electron channel in a piezoelectric material. 1998 , 57, 1654-1663		11
1135	Temperature dependence of the Raman spectrum of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ternary alloys. 1998 , 58, 10463-10469		23
1134	Screening of the surface-acoustic-wave potential by a metal gate and the quantization of the acoustoelectric current in a narrow channel. 1998 , 58, 10589-10596		66
1133	Multiexciton Spectroscopy of a Single Self-Assembled Quantum Dot. 1998 , 80, 4991-4994		300
1132	Influence of EX Resonance on Photocurrent-Voltage Characteristics in $\text{GaAs}/\text{InAlAs}$ Strained Superlattices. 1998 , 37, 1650-1653		
1131	III: Thermal Properties of Vertical-Cavity Surface-Emitting Semiconductor Lasers. 1998 , 38, 165-262		21
1130	Investigation of temperature influence on photo-induced conductivity in n-type $\text{Al}_x\text{Ga}_{1-x}\text{As}$. 1998 , 146, 175-186		0
1129	Carrier Pocket Engineering to Design Superior Thermoelectric Materials Using GaAs/AlAs Superlattices. 1998 , 545, 375		4
1128	Aluminum Arsenide (AlAs). 1998 , 489-499		16
1127	High-Power Semiconductor Lasers. 1999 , 259-321		2

1126	Sign inversion of the Stark shift in single non-abrupt GaAs/Al _x Ga _{1-x} As quantum wells. 1999 , 11, 5593-5602	4
1125	S-type negative differential conductivity and voltage switching due to the avalanche in semiconductor heterostructures. 1999 , 14, 341-344	4
1124	Modeling the optical constants of Al/sub x/Ga/sub 1-x/As alloys.	
1123	Consideration of Space Charge Effects and Effective Mass Non-parabolicity when Optimising Multi Quantum Barriers. 1999 , 38, 5839-5846	2
1122	Effect of surface recombination on the Early voltage in HBTs. 1999 , 14, 840-847	
1121	Photo-induced electron trapping in indirect bandgap at low temperature. 1999 , 11, 425-433	2
1120	Optical interface phonon modes in graded quantum well structures: perturbation theory. 1999 , 11, 8855-8865	1
1119	DX centers in Al _{0.37} Ga _{0.63} As/GaAs and In _{0.34} Al _{0.66} As/In _{0.36} Ga _{0.64} As heterostructures. 1999 , 17, 1761	
1118	Monte Carlo simulation of high-field transport and impact ionization in AlGaAs p ⁺ in ⁺ diodes. 1999 , 14, 994-1000	4
1117	Carrier capture into a GaAs quantum well with a separate confinement region: comment on quantum and classical aspects. 1999 , 14, 790-796	5
1116	Disorder-induced phonon modes, built-in electric fields and structural properties of CdTe/GaAs heterostructures grown by MBE. 1999 , 14, 350-356	5
1115	Effect of Electron Scattering on Second Derivative Ballistic Electron Emission Spectroscopy in Au/GaAs/AlGaAs Heterostructures. 1999 , 82, 3677-3680	19
1114	Investigation of DX center in silicon doped GaAs/AlAs short period superlattices. <i>Journal of Applied Physics</i> , 1999 , 85, 6520-6525	2.5 4
1113	Dispersion and tunneling analysis of the interfacial gate resistance in Schottky barriers. 1999 , 59, 13102-13113	19
1112	DX centers in In _x Al _{1-x} As. <i>Journal of Applied Physics</i> , 1999 , 85, 3380-3382	2.5 9
1111	Modeling the optical constants of Hg _x Cd _{1-x} Te alloys in the 1.5-0 eV range. <i>Journal of Applied Physics</i> , 1999 , 85, 2854-2860	2.5 5
1110	Modeling the optical constants of Al _x Ga _{1-x} As alloys. <i>Journal of Applied Physics</i> , 1999 , 86, 445-451	2.5 18
1109	Piezoresistive response induced by piezoelectric charges in n-type GaAs mesa resistors for application in stress transducers. <i>Journal of Applied Physics</i> , 1999 , 85, 333-340	2.5 12

1108	High-power GaAs/AlGaAs quantum fountain unipolar laser emitting at 14.5 μm with 2.5% tunability. 1999 , 74, 1537-1539		51
1107	Multibarrier heterostructure GaAs/AlAs switch. <i>Journal of Applied Physics</i> , 1999 , 85, 2007-2009	2.5	2
1106	Analysis of the scattering of electrons by special vibrational modes in a GaAs quantum well with a thin AlAs middle barrier: Mobility modulated by a transversal electric field. <i>Journal of Applied Physics</i> , 1999 , 85, 6598-6605	2.5	4
1105	Electron-phonon interaction in mixed crystals. 1999 , 59, 15422-15429		19
1104	Band-gap shift in heavily doped n-type Al _{0.3} Ga _{0.7} As alloys. 1999 , 60, 2463-2467		10
1103	Two-dimensional magnetoplasma/Bernstein modes coupled with bulk and surface optical phonons. 1999 , 59, 2261-2266		2
1102	Comparative study of the intra- and intervalley contributions to the free-carrier induced optical nonlinearity in n-GaAs. <i>Journal of Applied Physics</i> , 1999 , 85, 3807-3818	2.5	12
1101	Zn _{0.85} Cd _{0.15} Se active layers on graded-composition In _x Ga _{1-x} As buffer layers. <i>Journal of Applied Physics</i> , 1999 , 85, 8160-8169	2.5	7
1100	Raman studies of delta-doped semiconductors and quantum wells. <i>Journal of Applied Physics</i> , 1999 , 85, 1616-1621	2.5	3
1099	General Introduction. 1-47		1
1098	Graded base profiles on the performance of AlGaAs HBTs. 1999 , 86, 699-705		
1097	Multi-domain Gunn diodes with multiple hot electron launchers: a new approach to MM wave GaAs Gunn oscillator optimization.		1
1096	Growth and optical characterization of indirect-gap Al _x Ga _{1-x} As alloys. <i>Journal of Applied Physics</i> , 1999 , 86, 418-424	2.5	14
1095	Bound polaron in a polar semiconductor heterojunction. 1999 , 59, 2276-2283		12
1094	Modeling the optical constants of GaP, InP, and InAs. <i>Journal of Applied Physics</i> , 1999 , 85, 3638-3642	2.5	16
1093	Anomalous spin splitting of two-dimensional electrons in an AlAs quantum well. 1999 , 59, R12743-R12746		21
1092	Weak localization in ballistic quantum dots. 1999 , 60, 2680-2690		25
1091	Gain optimization in intersubband quantum well lasers by inverse spectral theory. 1999 , 113, 221-226		1

- 1090 A charge-control HEMT model incorporating deep level effects. **1999**, 43, 473-480 1
- 1089 Measurement of quasibound states in semiconductor heterostructures using ballistic electron emission spectroscopy. **1999**, 30, 975-983 3
- 1088 Perturbation calculation of impurity states in spherical quantum dots with parabolic confinement. **1999**, 4, 180-184 42
- 1087 Study of coherent folded acoustic phonons in semiconductor superlattices by pump-probe technique. **1999**, 263-264, 48-50 3
- 1086 Non-uniform strain in epitaxial surface gratings: Beyond the ordinary elastic description. **1999**, 251, 61-66 2
- 1085 π electron transfer in GaAs/AlAs type-I superlattices. **1999**, 142, 624-628 1
- 1084 Dominant direct transitions in annealed GaAs/AlAs multiple quantum wells. **1999**, 151, 29-32
- 1083 Residual strain mapping in III-V materials by spectrally resolved scanning photoluminescence. **1999**, 30, 651-657 4
- 1082 Investigation of two-dimensional electron gas concentration in selectively doped n-Al_xGa_{1-x}As/In_yGa_{1-y}As/GaAs heterostructures. **1999**, 30, 705-709 6
- 1081 Mechanisms of radiative recombination in InGaAsSb/InAsSbP lasers operating in the 3.0 to 3.6- μ m spectral range. **1999**, 33, 200-205 1
- 1080 Magnetopolaron states involving confined phonons in a semiconductor quantum well. **1999**, 88, 105-113 1
- 1079 Optical phonons in nanosize GaAs and AlAs clusters in an InAs matrix. **1999**, 70, 469-475
- 1078 Excitonic state in quantum wells formed from π -above-barrier π -electronic states. **1999**, 70, 621-627 4
- 1077 Passivation of the facets of 980 nm GaAs pump lasers by a pulsed UV laser-assisted technique. **1999**, 28, 83-90 5
- 1076 Low temperature transformations of defects in GaAs and AlGaAs. **1999**, 148, 401-405 18
- 1075 Bound-to-extended state absorption in quantum wells confined by π -like barriers. **1999**, 26, 263-277 2
- 1074 Electronic bandstructure of disordered superlattices. **1999**, 26, 195-209 6
- 1073 Observation of coherent folded acoustic phonons propagating in a GaAs/AlAs superlattice by two-color pump-probe spectroscopy. **1999**, 60, 8262-8266 67

1072	Electron-phonon interaction in quantum wells consisting of mixed crystals. 1999 , 60, 4937-4943		28
1071	Electron mobility in Si-doped AlGaAs alloy and GaAs-AlAs pseudo-alloy. 1999 , 14, 64-69		7
1070	Legendre polynomial approach for modeling free-ultrasonic waves in multilayered plates. <i>Journal of Applied Physics</i> , 1999 , 85, 3419-3427	2.5	67
1069	Acoustic wave propagation in continuous functionally graded plates. 1999 ,		
1068	Demonstration of high-brightness-mode propagation in a compound waveguide structure. 1999 , 75, 169-171		
1067	Above-barrier states in GaAs/AlGaAs superlattices studied by photoconductivity and photoreflectance. <i>Journal of Applied Physics</i> , 1999 , 86, 1460-1462	2.5	7
1066	MEMS based on III-V-compounds for sensing applications and optical communication.		3
1065	A comparative study of GaAs/AlGaAs quantum well infrared photodetectors grown by molecular beam epitaxy and metal organic vapour phase epitaxy.		
1064	Design and characteristics of high-power (>0.5-W CW) diode-pumped vertical-external-cavity surface-emitting semiconductor lasers with circular TEM ₀₀ /sub 00/ beams. 1999 , 5, 561-573		225
1063	The simulation of charge transport in the nanostructure Γ -channel heterotransistors. 1999 , 12, 373-376		
1062	Predicted band-gap pressure coefficients of all diamond and zinc-blende semiconductors: Chemical trends. 1999 , 60, 5404-5411		480
1061	Band structure of In _x Ga _{1-x} As _{1-y} N _y alloys and effects of pressure. 1999 , 60, 4430-4433		166
1060	At or Below the Fundamental Absorption Edge. 1999 , 179-250		3
1059	Localization and anticrossing of electron levels in GaAs _{1-x} N _x alloys. 1999 , 60, R11245-R11248		197
1058	Size and strain effects in the E1-like optical transitions of InAs/InP self-assembled quantum dot structures. 1999 , 74, 99-101		23
1057	Optical-phonon modes and electron-phonon interaction in arbitrary semiconductor planar microcavities. 1999 , 60, 16031-16038		9
1056	Design of an all-optical wavelength router based on spatial solitons. 1999 , 17, 1670-1681		1
1055	A tunable filter with collinear acoustooptical TE-TM mode conversion in a GaAs-AlAs multi-quantum-well waveguide. 1999 , 35, 820-826		10

- 1054 Micromechanical Resonators. **1999**,
- 1053 Optical Spectroscopy of Single Self Assembled Quantum Dots. **1999**, 571, 135
- 1052 Second Derivative Ballistic Electron Emission Spectroscopy in Au/(AlGa)As. **1999**, 584, 207
- 1051 Chapter 2 High-Efficiency AlGaInP Light-Emitting Diodes. **1999**, 64, 49-128 6
- 1050 Raman spectroscopy for characterizing compositional intermixing in GaAs/AlGaAs heterostructures. **1999**, 74, 3978-3980 11
- 1049 The quantum foundation. **2000**, 1-53 2
- 1048 A multi-valley model for hot free-electron nonlinearities at 10.6 μ m in highly doped n-GaAs. **2000**, 12, 169-180 11
- 1047 Binding Energy of Impurity States in Spherical GaAs $_{1-x}$ Al $_x$ As Quantum Dots. **2000**, 218, 461-469 57
- 1046 Light Emitting Diode with Charge Asymmetric Resonance Tunneling. **2000**, 180, 121-126 28
- 1045 Excitonic processes in GaAs/AlAs type-II superlattices. **2000**, 87-89, 15-19 7
- 1044 Photoluminescence and carrier transport properties via the intersubband scattering in a GaAs/AlAs superlattice under applied electric field. **2000**, 87-89, 411-414
- 1043 Nonalloyed GaAs metal-semiconductor field effect transistor. **2000**, 44, 143-146
- 1042 Brillouin scattering study of surface acoustic waves in indium-implanted GaAs. **2000**, 58, 543-550 3
- 1041 Photoreflectance study of doped semiconductor layers by a fast Fourier transformation. **2000**, 380, 243-245 20
- 1040 Effective mass dependence of resonant quasi-level lifetime in GaAs $_{1-x}$ Al $_x$ As double-barrier structures. **2000**, 292, 233-237 8
- 1039 Gaussian semiconductor superlattices. **2000**, 7, 832-835 9
- 1038 Binding energy of impurity in a size-quantized coated semiconductor wire: role of the dielectric-constant mismatch. **2000**, 8, 281-289 23
- 1037 Fast-particle energy loss to a quantum well. **2000**, 8, 248-253

1036	Magnetic-field effects on shallow impurities in semiconductor GaAs(Ga,Al)As quantum wells and superlattices within a fractional-dimensional space approach. 2000 , 8, 239-247	16
1035	Material parameters of InGaAsP and InAlGaAs systems for use in quantum well structures at low and room temperatures. 2000 , 5, 215-273	187
1034	High-power tunable quantum fountain unipolar lasers. 2000 , 7, 12-19	15
1033	First room temperature lasing from the fundamental state of V-grooved quantum wire lasers. 2000 , 7, 508-512	18
1032	The mathematical and computer modelling of microwave semiconductor devices. 2000 , 31, 15-34	4
1031	Multiphonon capture of charge carriers by deep-level centers in a depletion region of a semiconductor. 2000 , 34, 634-640	1
1030	Fano resonances and electron localization in heterobarriers. 2000 , 91, 361-368	2
1029	Piezoelectric effect and the long-term resistance relaxations induced by uniaxial compression in p-GaAs/Al _x Ga _{1-x} As heterostructures. 2000 , 91, 1250-1260	4
1028	Avalanche multiplication in Al _x Ga _{1-x} As (x=0 to 0.60). 2000 , 47, 1089-1097	41
1027	The effect of GaAs/AlGaAs compositional intermixing on second-order susceptibility. 2000 , 51-52, 195-200	
1026	Excitons and shallow impurities in GaAs(Ga,Al)As semiconductor heterostructures within a fractional-dimensional space approach: Magnetic-field effects. 2000 , 61, 13104-13114	59
1025	Characterizing the layer properties of AlGaAs/GaAs heteroface solar cell structures by specular spectral reflectance. 2000 , 29, 436-442	6
1024	Optimum antireflection coatings for heteroface AlGaAs/GaAs solar cells Part I: The influence of window layer oxidation. 2000 , 29, 984-991	12
1023	General Introduction. 1-47	
1022	Band structure estimation for Gaussian superlattices by applying image parameters in circuit theory.	1
1021	CHARACTERISTICS OF LOCALIZED ACOUSTIC MODES IN A N -LAYER-BASED SUPERLATTICE WITH DEFECT LAYERS. 2000 , 14, 571-581	3
1020	Regularity in difference in transmission characteristics for Gaussian superlattices and periodic superlattices.	1
1019	Electron transport mobility in a doped double quantum well structure. <i>Journal of Applied Physics</i> , 2000 , 88, 2658-2664	2.5 11

1018	Carrier transport in GaAs/AlAs type-II superlattices under electric field: Switch from X \bar{X} to \bar{X} transfer. 2000 , 76, 1866-1868		2
1017	The effect of As ₄ pressure on material qualities of AlGaAs/GaAs heterostructures grown on (111)B GaAs substrates. 2000 , 77, 2764-2766		5
1016	X-ray and optical characterization of multilayer AlGaAs waveguides. 2000 , 77, 3884-3886		8
1015	Properties of Ga _{1-x} In _x N mixed crystals and Ga _{1-x} In _x N/GaN quantum wells. <i>Journal of Applied Physics</i> , 2000 , 87, 2526-2532	2.5	19
1014	Tunneling through X-valley-related impurity states in GaAs/AlAs resonant-tunneling diodes. 2000 , 61, 10898-10904		4
1013	Complete minigaps for effective-mass carriers in three-dimensional semiconductor superlattices. 2000 , 62, 7133-7137		9
1012	A nearly universal critical conductivity for semiconductor-metal alloys. 2000 , 84, 2905-8		2
1011	Abnormal selection rules of interface modes in ultrathin GaAs/AlAs superlattice. <i>Journal of Applied Physics</i> , 2000 , 88, 6403-6407	2.5	3
1010	Room temperature study of low temperature grown Al _{0.3} Ga _{0.7} As/GaAs multiple quantum wells by modulation reflectance. <i>Journal of Applied Physics</i> , 2000 , 87, 8589-8593	2.5	3
1009	The optimization of optical gain in the intersubband quantum well laser. <i>Journal of Applied Physics</i> , 2000 , 87, 7965-7972	2.5	18
1008	Exciton-LO-phonon interaction in zinc-compound quantum wells. 2000 , 61, 9960-9963		10
1007	Electric-field-induced combination of Wannier-Stark localization and type-I/type-II crossover in a marginal type-I GaAs/AlAs superlattice. 2000 , 61, 7505-7510		4
1006	The alloy concentration as a control parameter of the electron capture mechanism. 2000 , 12, 10535-10542		3
1005	IN-LINE FIBER EVANESCENT FIELD ELECTROOPTIC MODULATORS. 2000 , 09, 79-94		4
1004	Pulse broadening and shaping by parametric amplification of short laser pulses in transverse-pumping geometry. 2000 , 17, 534		2
1003	Near-infrared refractive index of thick, laterally oxidized AlGaAs cladding layers. 2000 , 18, 199-202		15
1002	Ultrafast all-optical switching with an asymmetric Fabry-Perot device using low-temperature-grown GaAs: material and device issues. 2000 , 36, 100-111		16
1001	Tailoring light and heavy holes of GaAsP-AlGaAs quantum wells by using interdiffusion for polarization-independent amplifier applications. 2000 , 36, 164-174		8

1000	Donor states in a multi-layered quantum dot. 2000 , 12, 8641-8653		37
999	Carrier-carrier correlations in an optically excited single semiconductor quantum dot. 2000 , 61, 11009-11020	108	
998	Raman study of self-assembled GaAs and AlAs islands embedded in InAs. 2000 , 61, 13785-13790		26
997	Modelling and simulation of Al/sub x/Ga/sub 1-x/As/GaAs HBTs using the finite element method.		
996	Photoacoustic study of the effect of aluminum content on the thermal and thermomechanical properties of Al _y Ga _{1-y} As on GaAs in the range (0 ≤ y ≤ 1). <i>Journal of Applied Physics</i> , 2000 , 87, 7740-7744	2.5	19
995	Mean parameter model for the Pekar-Fröhlich polaron in a multilayered heterostructure. 2000 , 62, 16692-16702	16	
994	Treating some solid state problems with the Dirac equation. 2000 , 33, L509-L514		35
993	Generation and amplification of sub-THz coherent acoustic phonons under the drift of two-dimensional electrons. 2000 , 62, 7459-7469		33
992	General Introduction. 1-47		
991	The refractive index of Al _x Ga _{1-x} As below the band gap: Accurate determination and empirical modeling. <i>Journal of Applied Physics</i> , 2000 , 87, 7825-7837	2.5	197
990	Eshelby's problem for two-dimensional piezoelectric inclusions of arbitrary shape. 2000 , 456, 1051-1068		61
989	Empirical low-field mobility model for III-V compounds applicable in device simulation codes. <i>Journal of Applied Physics</i> , 2000 , 87, 2890-2900	2.5	253
988	Heterostructure and Compound Semiconductor Devices. 2001 , 511-646		
987	Theoretical description of electronic properties of vertical gated quantum dots. 2001 , 64,		41
986	A two-dimensional Eshelby problem for two bonded piezoelectric half-planes. 2001 , 457, 865-883		25
985	Designing two-dimensional electron gases in GaAs/InGaAs/AlGaAs, doped AlGaAs/GaAs, and AlGaAs/InGaAs/GaAs heterostructures for single electron transistor application. <i>Journal of Applied Physics</i> , 2001 , 89, 1759	2.5	10
984	Observation of intersubband real-space transfer in GaAs/AlAs quantum-well structures due to σ mixing. 2001 , 78, 1261-1263		10
983	Deviation of the AlGaAs lattice constant from Vegard's law. 2001 , 34, 1461-1465		43

982	Spatial modulation instability in a Kerr slab waveguide. 2001 , 26, 1879-81	52
981	. 2001 , 19, 1010-1022	11
980	Conversion efficiency for second-harmonic generation in photonic crystals. 2001 , 18, 348	36
979	TRANSFER MATRIX METHOD FOR ELECTRON-IO-PHONON INTERACTION IN ASYMMETRIC DOUBLE-BARRIER STRUCTURES. 2001 , 15, 3539-3549	12
978	Comprehensive modeling of vertical-cavity laser-diodes by the method of lines. 2001 , 37, 928-935	20
977	Gain optimization in optically pumped AlGaAs unipolar quantum-well lasers. 2001 , 37, 1337-1344	7
976	Spatio-temporal dynamics of light amplification and amplified spontaneous emission in high-power tapered semiconductor laser amplifiers. 2001 , 37, 1345-1355	6
975	. 2001 , 37, 1449-1459	35
974	Calculating the photocurrent and transit-time-limited bandwidth of a heterostructure p-i-n photo-detector. 2001 , 37, 1574-1587	23
973	Modeling of heterojunction bipolar transistors at any temperature, pressure, strain and alloy composition. 2001 , 21, 453-474	4
972	Continuity conditions for the wave function of a particle with a position-dependent mass in a laser field. 2001 , 64,	19
971	Acoustic wave propagation in continuous functionally graded plates: an extension of the Legendre polynomial approach. 2001 , 48, 1332-40	86
970	Monte Carlo study of dc and ac vertical electron transport in a single-barrier heterostructure. 2001 , 63,	13
969	Chapter 1 Quantum wells and quantum wires for potential thermoelectric applications. 2001 , 71, 1-121	85
968	X-ray and optical characterization of multilayer semiconductor waveguides. 2001 ,	
967	Analytic methods for field induced tunneling in quantum wells with arbitrary potential profiles. 2001 , 56, 809-822	14
966	Scaling properties of the electronic structure of quasiperiodic GaAs/Al _x Ga _{1-x} As superwires and superdots. 2001 , 305, 38-47	2
965	Structural properties of copper halides. 2001 , 87, 40-47	52

964	Improving performance of resonant tunneling devices in asymmetric structures. 2001 , 10, 535-543	0
963	Inelastic scattering of hot electrons in n-GaAs/AlAs types I and II multiple quantum wells doped with silicon. 2001 , 10, 505-510	1
962	Characteristics of QWIPs at low background. 2001 , 42, 221-235	8
961	A behavioural opto-electro-thermal VCSEL model for simulation of optical links. 2001 , 88, 209-219	8
960	Electron Mobility in One (Two)-Side Modulation-Doped GaAs/Al _x Ga _{1-x} As Asymmetric Quantum Wells. 2001 , 225, 43-61	10
959	Temperature dependence of excitonic transitions in Al _x Ga _{1-x} As/GaAs quantum wells. 2001 , 29, 225-231	7
958	A study for the cartography of the interface roughness of V-shaped AlGaAs/GaAs quantum wires. 2001 , 29, 367-377	6
957	Low temperature electron mobility in a coupled quantum well system. 2001 , 30, 119-127	5
956	Nature of the eigenstates in the miniband of random dimer-barrier superlattices. 2001 , 30, 297-308	12
955	Tight Binding Modeling of Heterojunction Band Offsets as a Function of Pressure and Composition. 2001 , 223, 195-204	12
954	Photoluminescence Study of InAs/AlAs Quantum Dots. 2001 , 224, 119-122	14
953	Electronic Properties of Al _x Ga _{1-x} As _y Sb _{1-y} Alloys Lattice-Matched to InAs. 2001 , 226, 293-304	14
952	High Quality p ⁺ -GaAs Tunnel Junction Diode Grown by Atmospheric Pressure Metalorganic Vapour Phase Epitaxy. 2001 , 183, 273-279	7
951	Photo-emf in Parabolic Graded-Gap Semiconductors. 2001 , 184, 433-436	
950	Epitaxial Growth and Characterisation of Silicon Delta-Doped GaAs, AlAs and Al _x Ga _{1-x} As. 2001 , 36, 1145-1154	
949	Evidence for quantum statistics of the exciton-biexciton system in a GaAs/AlAs type-II superlattice. 2001 , 63,	5
948	Investigation of weak damage in Al _{0.25} Ga _{0.75} As/GaAs by using RBS/C and Raman spectroscopy. 2001 , 286, 332-337	1
947	Pressure effect on the binding energies of donors in GaAs/Al _x Ga _{1-x} As heterojunctions. 2001 , 94-95, 417-420	15

946	Note to electron-phonon interaction in ternary mixed crystals. 2001 , 94-95, 781-785		4
945	Distribution of electrons between valleys and band-gap narrowing at picosecond superluminescence in GaAs. 2001 , 35, 67-71		12
944	Design and analysis of heterojunction bipolar transferred electron devices. 2001 , 48, 1531-1539		1
943	Transition of Infrared Absorption Peaks in Thermally Annealed GaInNAs. 2001 , 40, L750-L752		38
942	ENERGY LEVELS OF A POLARON IN A FINITE PARABOLIC QUANTUM WELL. 2001 , 15, 527-535		7
941	OPTICAL TRANSITIONS IN A PARABOLIC GaAs/Ga _{1-x} Al _x As SUPERLATTICES. 2001 , 08, 321-325		
940	Current instability in power HEMTs. 2001 , 16, 562-566		17
939	Surface acoustic wave attenuation by the localized states of a two-dimensional carrier system in a magnetic field. 2001 , 16, 136-139		1
938	Integral evaluation in the mathematical and numerical modelling of high-electron-mobility transistors. 2001 , 13, 515-524		22
937	Photoreflectance of Zn:Al _x Ga _{1-x} As at the E1 Transition Energy as a Function of Carrier Concentration and Aluminum Composition. 2001 , 64, 386-389		1
936	Influence of leaky waves on free-electron-induced nonlinear reflection properties of highly doped n-GaAs layer at medium IR-wavelengths. 2001 , 3, 493-499		7
935	Hydrogenic impurity in multilayered quantum wires. <i>Journal of Applied Physics</i> , 2001 , 89, 2241-2245	2.5	9
934	Photoluminescence and photo-modulated reflectance spectra of ion-implanted GaAs/AlGaAs coupled quantum wells. <i>Journal of Applied Physics</i> , 2001 , 89, 3138-3142	2.5	1
933	Photoionization spectrum in double-barrier quantum wells: Exact expansion over resonances and natural line shape. 2001 , 64,		2
932	Shallow impurities in V-groove quantum wires. 2001 , 63,		16
931	Uniaxial-stress dependence of Hall effect in an AlGaAs/GaAs modulation-doped heterojunction. 2001 , 79, 4586-4588		6
930	Photoluminescence of a low-density two-dimensional hole gas in a GaAs quantum well: Observation of valence-band Landau levels. 2001 , 63,		20
929	Interface optical phonon-assisted tunneling in double-barrier structures. 2001 , 64,		8

928	Piezoelectric photothermal study of Al _x Ga _{1-x} As epitaxial layer (x=0.22, 0.28, and 0.5) grown on semi-insulating GaAs substrate. <i>Journal of Applied Physics</i> , 2001 , 90, 4385-4391	2.5	14
927	Elastostatic fields in an anisotropic substrate due to a buried quantum dot. <i>Journal of Applied Physics</i> , 2001 , 90, 6190-6196	2.5	47
926	Optical-gain enhancement in two-dimensional active photonic crystals. <i>Journal of Applied Physics</i> , 2001 , 90, 545-551	2.5	84
925	Third order mode optically pumped semiconductor laser. 2002 , 80, 4690-4692		13
924	Donor impurity on-center and off-center in multilayered quantum wires in the presence of magnetic field. <i>Journal of Applied Physics</i> , 2002 , 92, 484-490	2.5	9
923	Off-center donor impurity in multilayered quantum wires. <i>Journal of Applied Physics</i> , 2002 , 91, 2326-2332	2.5	4
922	Largely tunable midinfrared (8–12 μ m) difference frequency generation in isotropic semiconductors. <i>Journal of Applied Physics</i> , 2002 , 91, 2550-2552	2.5	19
921	Elastic and piezoelectric fields around a quantum dot: Fully coupled or semicoupled model?. <i>Journal of Applied Physics</i> , 2002 , 91, 3785-3796	2.5	59
920	Impact of deformation potential scattering on free-carrier induced optical nonlinearities: An experimental study in GaAs. <i>Journal of Applied Physics</i> , 2002 , 91, 3992-3999	2.5	5
919	Micro-Raman studies of vertical-cavity surface-emitting lasers with Al _x O _y /GaAs distributed Bragg reflectors. 2002 , 81, 2544-2546		26
918	Electron transport in the barriers of AlGaAs/GaAs quantum well structures observed by scanning-tunneling-microscope light-emission spectroscopy. 2002 , 80, 3748-3750		10
917	Confinement of acoustical vibrations in a semiconductor planar phonon cavity. 2002 , 89, 227402		183
916	Resonant-cavity-enhanced heterostructure metal-semiconductor-metal photodetector. 2002 , 80, 3222-3224		15
915	Lateral-cavity spectral hole burning in quantum-dot lasers. 2002 , 81, 1546-1548		18
914	Role of interface optical phonons in magnetotunneling in asymmetric double-barrier structures. <i>Journal of Applied Physics</i> , 2002 , 91, 724-731	2.5	4
913	Effect of structural defects consisting of ternary mixed crystals on localized interface optical modes in superlattices. 2002 , 65,		14
912	Effect of interface trapping on the frequency response of a photodetector. 2002 , 20, 1105-1110		5
911	Optical phonon-assisted magnetotunneling peaks in GaAs/Al _x Ga _{1-x} As double-barrier structures. 2002 , 66,		4

910	First-order homogeneous electron gas model of semiconductors at finite temperatures. 2002 , 65,	0
909	Raman study of low-temperature-grown Al _{0.29} Ga _{0.71} As/GaAs photorefractive materials. 2002 , 65,	2
908	Relaxation of photoinjected spins during drift transport in GaAs. 2002 , 81, 2788-2790	49
907	Structure effects on electron-optical phonon interaction in GaAs/Al _x Ga _{1-x} As quantum wells. <i>Journal of Applied Physics</i> , 2002 , 92, 268-273	2.5 5
906	Pressure-induced structural transformation in GaAs: A molecular-dynamics study. 2002 , 65,	24
905	Band structure of a periodic quantum wire array. 2002 , 66,	21
904	Piezoelectric displacement sensing with a single-electron transistor. 2002 , 81, 2258-2260	39
903	Enhanced electron mobility and high order fractional quantum Hall states in AlAs quantum wells. 2002 , 80, 1583-1585	51
902	Al(x)Ga(1-x)As, transport properties. 1-30	
901	Polarons with Spatially Dependent Mass in a Finite Parabolic Quantum Well. 2002 , 19, 974-977	8
900	A novel HMSM photodetector with resonant cavity for short haul communications.	
899	Nanostructure Devices based on Electron Waveguides. 2002 , 19, 269-284	1
898	Laser interferometry as a diagnostic tool for the fabrication of reactive ion etching-edge-emitting lasers. 2002 , 20, 1994	2
897	Lattice Strain Induced by Ion Implantation in AlGaAs/AlGaInAs Quantum Well Samples. 2002 , 19, 599-601	1
896	Shallow impurities in multiple V-groove quantum wires. 2002 , 14, 471-482	0
895	Electron States in Quasi-One-Dimensional Structures; Azimuthal Applied Magnetic Field. 2002 , 65, 459-464	3
894	The Effect of Uniaxial Stress on the Density of States of Shallow Donor Impurities in GaAs Quantum Wells. 2002 , 66, 94-96	1
893	Localized interface optical phonon modes in a semi-infinite superlattice with a cap layer. 2002 , 14, 13761-13775	4

892	Electrochemical formation of thin films of binary III-V compounds. 2002 , 261-318		
891	Photodetectors based on heterostructures for optoelectronic applications. 2002 , 4919, 306		
890	Gate resistance and the Schottky-barrier interface. 2002 , 527-566		
889	Electronic Properties of n-type Al _x Ga _{1-x} As Alloys. 2002 , 744, 1		
888	Elastic Guided Waves in a Layered Plate With a Rectangular Cross Section. 2002 , 124, 319-325		6
887	Effects of exciton-acoustic-phonon scattering on optical line shapes and exciton dephasing in semiconductors and semiconductor quantum wells. 2002 , 66,		15
886	Exciton-acoustic-phonon linewidths in GaAs bulk and quantum wells. 2002 , 65,		9
885	Characterization of AlGaAs/AlAs waveguides for optical parametric interactions. 2002 , 19, 902		4
884	Band offsets in III-nitride heterostructures. 2002 , 35, 591-594		13
883	Strain-mediated phase coexistence in MnAs heteroepitaxial films on GaAs: An x-ray diffraction study. 2002 , 66,		107
882	Longitudinal optical phonon assisted relaxation of excitons due to intersubband transitions in quantum wells. <i>Journal of Applied Physics</i> , 2002 , 91, 5796-5801	2.5	4
881	Confinement and amplification of acoustic waves in cubic heterostructures. 2002 , 65,		
880	Quasi-phase matched tunable mid-infrared (8-12 /spl mu/m) difference frequency generation by total internal reflection in isotropic semiconductors.		
879	Gallium arsenide (GaAs), deformation potentials. 1-7		
878	Al(x)Ga(1-x)As, further band structure parameters. 1-15		
877	Al(x)Ga(1-x)As, lattice properties. 1-6		
876	General Introduction. 1-47		
875	Bidirectional beam propagation method for multilayered dielectrics with quadratic nonlinearity. 2002 , 8, 440-447		14

- 874 Photoreflectance-difference spectroscopy of GaAs (001) under [110] uniaxial stress: Linear and quadratic electro-optic components. **2002**, 66, 11
- 873 Aluminum arsenide (AlAs), effective masses. 1-4
- 872 Al(x)Ga(1-x)As, effective masses, deformation potentials and related parameters. 1-11
- 871 X-valley influence on hot free electron absorption and optical nonlinearities at 10.6 μ m in highly doped n-GaAs. **2002**, 19, 29-37 8
- 870 Quasiparticle Calculations for Point Defects on Semiconductor Surfaces. **2002**, 234, 346-353 8
- 869 Raman study of phonons in Ga_{1-x}Al_xAs. **2002**, 33, 202-206 9
- 868 Spatially varying effective mass effects on energy level populations in semiconductor quantum devices. **2002**, 32, 1-9 4
- 867 Wavelength selective photoexcitation of picosecond acoustic-phonon pulses in a triple GaAs/Al_{0.3}Ga_{0.7}As quantum well structure. **2002**, 316-317, 205-208 9
- 866 Properties of AlGaAs layers grown on Si by the conformal method. **2002**, 91-92, 91-95
- 865 The mobility of charge carriers in a size-quantized coated semiconductor wire. **2002**, 14, 366-374 14
- 864 Polaron effects on the third-order nonlinear optical susceptibility in a quantum disk. **2002**, 15, 217-228 41
- 863 Diffusion process of electrons injected from STM tip into AlGaAs/GaAs quantum wells. **2002**, 190, 275-278 3
- 862 Localised electronic states in semiconductor superlattices. **2002**, 47, 93-196 44
- 861 Localized interface optical-phonon modes in two coupled semi-infinite superlattices. **2002**, 299, 634-643 30
- 860 Renormalization of the Fröhlich constant for electrons in a quantum dot. **2002**, 304, 168-171 16
- 859 Quantum efficiency in GaAs Schottky photodetectors with enhancement due to surface plasmon excitations. **2002**, 46, 29-33 11
- 858 Scaling of pseudomorphic high electron mobility transistors to decanano dimensions. **2002**, 46, 631-638 41
- 857 Control of the interband and intersubband transition energy in quantum wells using localized isoelectronic perturbations. **2002**, 36, 434-438

856	Resonance tunneling and nonlinear current in heterobarriers with complex law of carrier dispersion. 2002 , 36, 539-545	3
855	Interface-related effects on confined excitons in GaAs/Al _x Ga _{1-x} As single quantum wells. 2002 , 190, 191-194	7
854	Negative differential resistance in aperiodic semiconductor superlattices. 2002 , 303, 493-506	12
853	Thermal stresses in elastic multilayer systems. 2002 , 418, 182-188	186
852	Mindlin's problem for an anisotropic piezoelectric half-space with general boundary conditions. 2002 , 458, 181-208	40
851	Simultaneous effects of hydrostatic stress and an electric field on donors in a GaAs-(Ga, Al)As quantum well. 2002 , 14, 987-995	56
850	Aluminum arsenide (AlAs), band structure parameters, deformation potentials. 1-3	
849	Pressure-dependent dynamical properties of Zn-based II-VI semiconductors. 2012 , 407, 3570-3574	8
848	Transverse laser dressing effects on the subband density of states in a 20-nm-wide GaAs/Al _{0.3} Ga _{0.7} As quantum well wire. 2012 , 44, 1446-1453	6
847	Optimal design of heterostructure tunnel diode with nonlinear current-voltage characteristic. 2012 , 44, 1503-1509	3
846	Second harmonic generation in asymmetric double semi-parabolic quantum wells: Effects of electric and magnetic fields, hydrostatic pressure and temperature. 2012 , 44, 1900-1904	41
845	Hydrostatic pressure on optical absorption and refractive index changes of a shallow hydrogenic impurity in a GaAs/GaAlAs quantum wire. 2012 , 52, 234-244	22
844	Applications and Brief Review of Experimental Results. 2012 , 281-327	
843	Investigation of coherent acoustic phonons in terahertz quantum cascade laser structures using femtosecond pump-probe spectroscopy. <i>Journal of Applied Physics</i> , 2012 , 112, 033517	2.5 9
842	First-principles study on stability, energy gaps, optical phonon and related parameters of In _{1-x} Al _x Ga _y As alloys. 2012 , 192, 161-167	4
841	Structural and electronic properties of Ga _{1-x} In _x As _{1-y} N _y quaternary semiconductor alloy on GaAs substrate. 2012 , 519, 55-59	20
840	Temperature and Bi-concentration dependence of the bandgap and spin-orbit splitting in InGaBiAs/InP semiconductors for mid-infrared applications. 2012 , 101, 221108	54
839	Semiconductor Materials and Modelling. 2012 , 33-62	2

- 838 The influence of polar optical phonon confinement on the binding energy of a hydrogenic impurity in quantum wires in the perpendicular electric and magnetic fields. **2012**, 350, 012021
- 837 The effects of hydrostatic pressure on the nonlinear intersubband transitions and refractive index changes of different QW shapes. **2012**, 285, 5223-5228 26
- 836 In situ multifrequency ferromagnetic resonance and x-ray magnetic circular dichroism investigations on Fe/GaAs(110): Enhanced g-factor. **2012**, 100, 092402 13
- 835 Diagnostics of quantum cascade structures by optical methods in the near infrared region. **2012**, 46, 1411-1414 2
- 834 Optical properties of GaAs structures containing a periodic system of layers of AsSb metal nano-inclusions. **2012**, 46, 1291-1295 7
- 833 Imaging of electromagnetic properties via acoustic excitation. **2012**,
- 832 Faster radial strain relaxation in InAs/GaAs core/shell heterowires. *Journal of Applied Physics*, **2012**, 111, 044301 2.5 48
- 831 Optimum temperature control of micro devices under high-speed thermal disturbances. **2012**,
- 830 Interplay between the hot phonon effect and intervalley scattering on the cooling rate of hot carriers in GaAs and InP. **2012**, 20, 82-92 51
- 829 Binding energies of bound polaron in a wurtzite nitride nanowire: Contributions of IO and QC phonon modes. **2012**, 249, 544-554 3
- 828 The electronic properties of a core/shell/well/shell spherical quantum dot with and without a hydrogenic impurity. *Journal of Applied Physics*, **2012**, 111, 083702 2.5 46
- 827 Effects of hydrostatic pressure and external electric field on the impurity binding energy in strained GaN/Al_xGa_{1-x}N spherical quantum dots. **2012**, 8, 224-228 1
- 826 The effects of hydrostatic pressure and intense laser field on the linear and nonlinear optical properties of a square quantum well. **2012**, 285, 373-377 37
- 825 Oscillator strengths of the intersubband electronic transitions in the hydrogenic nano-antidots. **2012**, 51, 62-72 24
- 824 On the two dimensional effective electron mass in quantum wells, inversion layers and NIPI superlattices of Kane type semiconductors in the presence of strong light waves: Simplified theory and relative comparison. **2012**, 51, 203-222 15
- 823 Intersubband optical refractive index changes in an asymmetric quantum dot underlying an external static magnetic field. **2012**, 51, 580-586 12
- 822 Gain analysis in photonic crystal lasers using modified complex plane-wave expansion method. **2012**, 73, 37-43 1
- 821 Determination of the chemical composition of GaNAs using STEM HAADF imaging and STEM strain state analysis. **2012**, 117, 15-23 67

820	Hydrogen Detection Using a Functionalized Photonic Crystal Vertical Cavity Laser. 2012 , 48, 160-168		19
819	. 2012 , 48, 465-471		25
818	Changes in the spectra of picosecond stimulated emission from GaAs accompanied by signs of electron-phonon interaction. 2012 , 46, 921-928		3
817	Validation of energy prediction method for a concentrator photovoltaic module in Toyohashi Japan. 2013 , 21, 1598-1610		47
816	Catalyst composition and impurity-dependent kinetics of nanowire heteroepitaxy. 2013 , 7, 7689-97		10
815	Linear thermal expansion coefficient determination using in situ curvature and temperature dependent X-ray diffraction measurements applied to metalorganic vapor phase epitaxy-grown AlGaAs. <i>Journal of Applied Physics</i> , 2013 , 114, 033501	2.5	3
814	Direct measurement of band edge discontinuity in individual core-shell nanowires by photocurrent spectroscopy. 2013 , 13, 4152-7		10
813	A coupled-mode theory analysis of intermixing in semiconductor distributed Bragg reflectors. 2013 , 45, 937-946		2
812	Semiconductor Materials and Modelling. 2013 , 27-54		
811	Linear and nonlinear optical absorption coefficients and refractive index changes in modulation-doped quantum wells: Effects of the magnetic field and hydrostatic pressure. 2013 , 428, 30-35		24
810	Simultaneous effects of hydrostatic pressure and temperature on the nonlinear optical properties in a parabolic quantum well under the intense laser field. 2013 , 309, 158-162		32
809	Induced Anomalous Dispersion in Semiconductor Lasers. 2013 , 19, 1502508-1502508		1
808	Measurement of indium concentration profiles and segregation efficiencies from high-angle annular dark field-scanning transmission electron microscopy images. 2013 , 131, 1-9		16
807	Effect of parabolic potential well profile on multisubband electron mobility in a coupled quantum well in presence of an external electric field. 2013 , 61, 50-58		3
806	Optical absorption of an asymmetric quantum dot in the presence of an uniform magnetic field. 2013 , 60, 40-46		8
805	Computation of intersubband transition energy in normal and inverted core-shell quantum dots using finite difference technique. 2013 , 60, 414-425		18
804	The second-harmonic generation of anisotropic quantum disks in the presence of a tilted magnetic field. 2013 , 62, 149-155		
803	Pressure effect on spin-orbit interaction in a spherical quantum antidot. 2013 , 87, 229-234		4

802	Linear and nonlinear optical properties of multi-layered spherical nano-systems with donor impurity in the center. 2013 , 12, 36-42		25
801	Elastic tunneling identification through crossings, anti-crossings and splitting of states in the complex electronic current of systems based on mesoscopic molecules. 2013 , 86, 1		1
800	Hydrostatic pressure and temperature dependence of dielectric mismatch effect on the impurity binding energy in a spherical quantum dot. 2013 , 58, 218-227		21
799	Evaluation of chemical cleaning for Ga _{1-x} Al _x As photocathode by spectral response. 2013 , 309, 323-327		3
798	Linear and nonlinear optical properties of GaAs/Al _x Ga _{1-x} As/GaAs/Al _y Ga _{1-y} As multi-shell spherical quantum dot. <i>Journal of Applied Physics</i> , 2013 , 114, 183704	2.5	24
797	Nonlinear intersubband absorption and refractive index changes in square and graded quantum well modulated by temperature and Hydrostatic pressure. 2013 , 134, 42-48		33
796	Degradation signatures of high power laser diodes. 2013 ,		1
795	Comparing the relativistic and non-relativistic transmission coefficients of the electron transport through a quantum heterostructure. 2013 , 377, 3242-3245		
794	Effects of electric field and shape on the ground state energy of an exciton bound to an ionized donor impurity in ellipsoidal quantum dots. <i>Journal of Applied Physics</i> , 2013 , 114, 194301	2.5	9
793	Hydrostatic pressure and temperature effects on nonlinear optical rectification in a lens shape InAs/GaAs quantum dot. 2013 , 135, 271-275		37
792	New wavefunctions for the excited states of an axial impurity in a quantum wire. 2013 , 55, 198-210		4
791	Terahertz radiation from the coherent longitudinal optical phonon-plasmon coupled mode in an i-GaAs/n-GaAs epitaxial structure. 2013 , 417, 012051		
790	Periodic oscillations in dimer quasiperiodic fibonacci Al _x Ga _{1-x} As/GaAs superlattices. 2013 ,		
789	One-phonon resonant electron Raman scattering in a cylindrical GaAs/AlAs quantum dot. 2013 , 44, 752-757		2
788	Intersubband plasmon-phonon coupling in GaAsP/AlGaAs near surface quantum well. 2013 , 102, 181120		1
787	Spatial-Mode Discrimination in Guided and Antiguided Arrays of Long-Wavelength VCSELs. 2013 , 19, 1-10		5
786	Study of transmission properties in GaAs/Al _x Ga _{1-x} As superlattices generated by a specific sequences. 2013 , 56, 16-26		3
785	Refractive index changes of multi-layered spherical nanostructures with donor impurity. 2013 , 420, 81-85		5

784	Achievement of tailored laser frequencies by fine-tuning the structural parameters of Fibonacci in Al _x Ga _{1-x} As/GaAs superlattices. 2013 , 62, 233-241		1
783	Lattice dynamics and thermal properties of CaxMg1-xS ternary alloys. 2013 , 69, 148-152		3
782	Explanations of inconsistencies in capacitance-voltage profiles of normal and inverted heterostructures. 2013 , 16, 1090-1094		1
781	Quantitative chemical evaluation of dilute GaNAs using ADF STEM: avoiding surface strain induced artifacts. 2013 , 129, 1-9		28
780	Mixed disorder in GaAs/Al _x Ga _{1-x} As superlattices and its effect on the range of wavelength infrared lasers. 2013 , 124, 3812-3815		3
779	Tuning the light emission from GaAs nanowires over 290 meV with uniaxial strain. 2013 , 13, 917-24		119
778	Fast determination of a polaron mechanism in beryllium-VI polymorphs using LDA-1/2 approach. 2013 , 135, 248-253		4
777	Effect of pressure on spin-orbit interaction in a quantum wire with V-shaped cross section. 2013 , 19, 63-68		22
776	Surface phonon-polaritons in rectangular quantum wires of polar ternary mixed crystals. 2013 , 50, 51-56		3
775	Elastic modulus, optical phonon modes and polaron properties in Al _{1-x} B _x N alloys. 2013 , 13, 493-499		10
774	Polaron states in a double quantum ring structure in the presence of electric and magnetic fields. 2013 , 57, 85-94		6
773	Optical gain spectra of unstrained graded GaAs/Al _x Ga _{1-x} As quantum well laser. 2013 , 377, 582-586		11
772	Electronic Properties of Heterostructures. 2013 , 79-129		
771	Electronic band structure and derived properties of AlAs _x Sb _{1-x} alloys. 2013 , 59, 144-154		13
770	Photoemission characteristics of (Cs, O) activation exponential-doping Ga _{0.37} Al _{0.63} As photocathodes. <i>Journal of Applied Physics</i> , 2013 , 113, 213105	2.5	23
769	Enhancement of multisubband electron mobility in parabolic Al _x Ga _{1-x} As-GaAs double quantum well structures. <i>Journal of Applied Physics</i> , 2013 , 113, 083704	2.5	21
768	Red Emitting VCSEL. 2013 , 379-401		
767	Synchronized photonic modulators driven by surface acoustic waves. 2013 , 21, 21669-76		19

766	One-dimensional photonic crystals with a sawtooth refractive index: another exactly solvable potential. 2013 , 15, 103009		11
765	Investigations of carrier scattering into L-valley in $\lambda = 3.5 \mu\text{m}$ InGaAs/AlAs(Sb) quantum cascade lasers using high hydrostatic pressure. 2013 , 250, 693-697		6
764	Composition-dependent elastic modulus, vibration frequency and polaron properties of ZnSexTe1-x system. 2013 , 35, 2303-2308		14
763	VCSEL Fundamentals. 2013 , 19-75		17
762	Calculations of terahertz quantum cascade lasers with ternary compound semiconductor wells. 2013 ,		
761	Picosecond opto-acoustic interferometry and polarimetry in high-index GaAs. 2013 , 21, 16473-85		12
760	Improvements in thermionic cooling through engineering of the heterostructure interface using Monte Carlo simulations. <i>Journal of Applied Physics</i> , 2013 , 114, 043717	2.5	3
759	Performance enhancement of a GaAs detector with a vertical field and an embedded thin low-temperature grown layer. 2013 , 13, 2475-83		6
758	Precise Determination of the Direct/Indirect Band Gap Energy Crossover Composition in AlxGa1-xAs. 2013 , 6, 071201		7
757	A study of electron transport through a multiple quantum well structure in the presence of an electric field, using the relativistic transfer matrix. 2013 , T157, 014005		
756	Effect of Bismuth Alloying on the Transport Properties of the Dilute Bismide Alloy, GaAs1-xBix. 2013 , 181-200		3
755	Vacuum Rabi splitting in a semiconductor circuit QED system. 2013 , 110, 066802		84
754	Study of gain characteristics of GaAs/GaAlAs self assembled quantum dots. 2013 ,		
753	Temperature dependence of the average electron-hole pair creation energy in Al0.8Ga0.2As. 2013 , 102, 181119		17
752	Anisotropic homogeneous linewidth of the heavy-hole exciton in (110)-oriented GaAs quantum wells. 2013 , 88,		21
751	Ultrahigh Q-frequency product for optomechanical disk resonators with a mechanical shield. 2013 , 103, 241112		32
750	One-phonon resonant electron Raman scattering in multilayer coaxial cylindrical AlxGa1-xAs/GaAs quantum cables. 2013 , 34, 042001		1
749	The pressure dependences of elastic and lattice dynamic properties of AlAs from ab initio calculations. 2013 , 22, 026201		3

748	Resolving sub-phonon wavelength super lattices using coherent acoustic phonon spectroscopy. 2013,		
747	Commensurability Oscillations in the Radio-Frequency Conductivity of Unidirectional Lateral Superlattices: Measurement of Anisotropic Conductivity by Coplanar Waveguide. 2013, 82, 054710		8
746	Effects of Temperature and Hydrostatic Pressure on Binding Energy of an Exciton in a Spherical Quantum Dot. 2014, 12, 358-362		4
745	Structural asymmetry induced enhancement of electron mobility in coupled double quantum well structures. 2014, 53, 095201		0
744	Elasticity and Phonons. 2014, 1-34		
743	Spectral characteristics of multimode semiconductor lasers with a high-order surface diffraction grating. 2014, 44, 907-911		6
742	Interface phonon-polaritons in quantum well wire systems of polar ternary mixed crystals. 2014, 74, 206-216		2
741	Spin-Orbit Interaction in a Spherical Quantum Dot. 2014, 125, 1197-1205		3
740	Double-diamond high-contrast-gratings vertical external cavity surface emitting laser. 2014, 47, 065104		24
739	Study of the Effect of Luminescence Down-Shifting on GaAs Solar Cells With Several Optical Windows Layers. 2014, 136,		6
738	Effect of geometry on the screened acceptor binding energy in a quantum wire. 2014,		
737	Ultrafast pump-probe spectroscopy in gallium arsenide at 25 T. 2014, 39, 5772-5		4
736	III-V semiconductor waveguides for photonic functionality at 780 nm. 2014,		
735	Strain and origin of inhomogeneous broadening probed by optically detected nuclear magnetic resonance in a (110) GaAs quantum well. 2014, 89,		6
734	Ultra-thin GaAs single-junction solar cells integrated with a reflective back scattering layer. <i>Journal of Applied Physics,</i> 2014, 115, 203105	2.5	41
733	Thermal conduction in lattice-matched superlattices of InGaAs/InAlAs. 2014, 105, 051909		35
732	An effective approach for the minimization of errors in capacitance-voltage carrier profiling of quantum structures. <i>Journal of Applied Physics,</i> 2014, 115, 134308	2.5	1
731	Effects of strain and quantum confinement in optically pumped nuclear magnetic resonance in GaAs: Interpretation guided by spin-dependent band structure calculations. 2014, 90,		13

730	Ultra-Thin Unidirectional Carpet Cloak and Wavefront Reconstruction With Graded Metasurfaces. 2014 , 13, 1775-1778		82
729	Electric field induced oscillating electron mobility in asymmetric wide GaAs/Al _x Ga _{1-x} As quantum well structure. <i>Journal of Applied Physics</i> , 2014 , 116, 043703	2.5	7
728	Numerical Analysis of Mode Discrimination by Intracavity Patterning in Long-Wavelength Wafer-Fused Vertical-Cavity Surface-Emitting Lasers. 2014 , 50, 1-9		8
727	Applied electric field and hydrostatic pressure effects on quasistationary states in single and coupled GaAs-(Ga,Al)As quantum wells. 2014 , 480, 012027		3
726	Probing inhomogeneous composition in core/shell nanowires by Raman spectroscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 184303	2.5	3
725	Coaxial tunnel junctions: a novel approach to reduce the current crowding effect in electrically-pumped VECSELs. 2014 ,		
724	Shallow impurity states in Al _x Ga _{1-x} As cylindrical quantum wire. 2014 , 35, 082002		
723	Multisubband electron mobility in a parabolic quantum well structure under the influence of an applied electric field. 2014 , 35, 012001		3
722	Fröhlich resonance in the AsSb/AlGaAs system. 2014 , 56, 1952-1956		8
721	Simulating the spectral response of quantum dot-in-well infrared photodetectors from eight band k.p method. <i>Journal of Applied Physics</i> , 2014 , 116, 203701	2.5	
720	Nonlinear optical rectification in asymmetric quantum dots with an external static magnetic field. 2014 , 56, 130-133		12
719	Quasistationary states in single and double GaAs/(Ga,Al)As quantum wells: Applied electric field and hydrostatic pressure effects. 2014 , 442, 74-80		5
718	Linear and nonlinear optical properties of multilayered spherical quantum dots: Effects of geometrical size, hydrogenic impurity, hydrostatic pressure and temperature. 2014 , 145, 55-60		56
717	The combined effect of pressure and temperature on the impurity binding energy in a cubic quantum dot using the FEM simulation. 2014 , 69, 38-52		36
716	Terahertz emission from doped GaAs and GaAs/AlGaAs: A comparative Monte Carlo study. 2014 , 321, 90-95		3
715	Electron-phonon interaction effect on the energy levels and diamagnetic susceptibility of quantum wires: Parallelogram and triangle cross section. <i>Journal of Applied Physics</i> , 2014 , 115, 124314	2.5	31
714	Sharp Switching in Optical Couplers With Variable Coupling Coefficient. 2014 , 32, 1565-1569		1
713	Enhancement of electron mobility in asymmetric coupled quantum well structures. <i>Journal of Applied Physics</i> , 2014 , 115, 073701	2.5	10

- 712 Intersubband optical absorption coefficients and refractive index changes in a graded quantum well under intense laser field: Effects of hydrostatic pressure, temperature and electric field. **2014**, 434, 26-31 32
- 711 Multisubband electron mobility in asymmetric GaAs/AlGaAs quantum well structures. **2014**, 66, 39-47 6
- 710 Nonlinear optical rectification in a two-dimensional system. **2014**, 60, 1-3 2
- 709 Generalized optical gain analysis in nonparabolic semiconductor laser. **2014**, 27, 50-61
- 708 Investigation of GaAs/AlGaAs quantum cascade structures by optical methods based on hot luminescence in the near-infrared range. **2014**, 48, 1463-1466
- 707 Electric field and shape effect on the linear and nonlinear optical properties of ellipsoidal finite-potential quantum dots. **2014**, 75, 505-513 4
- 706 Multi-subband electron mobility in AlGaAs parabolic quantum wells. **2014**,
- 705 Effect of doping profile on multisubband electron mobility in AlGaAs parabolic quantum well structures. **2014**, 64, 33-38 11
- 704 Novel high-efficiency crystalline-silicon-based compound heterojunction solar cells: HCT (heterojunction with compound thin-layer). **2014**, 16, 15400-10 26
- 703 Evaluation of the junction electric field and the ideality factor of GaAs p-n junction solar cells by using photoreflectance spectroscopy. **2014**, 64, 1031-1035 19
- 702 Manipulating optical reflections using engineered nanoscale metasurfaces. **2014**, 89, 35
- 701 Effect of interdiffusion on electronic states in one-layer quantum ring superlattice. **2014**, 64, 51-56 8
- 700 A detailed investigation of electronic and intersubband optical properties of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}/\text{Al}_y\text{Ga}_{1-y}\text{As}/\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ multi-shell quantum dots. **2014**, 47, 295302 17
- 699 Unintentional high-density p-type modulation doping of a GaAs/AlAs core-multishell nanowire. **2014**, 14, 2807-14 37
- 698 Sensitivity of entanglement decay of quantum-dot spin qubits to the external magnetic field. **2014**, 89, 15
- 697 Effect of the aluminium concentration on the resonant tunnelling time and the laser wavelength of random trimer barrier $\text{Al}_x\text{Ga}_{1-x}\text{As}$ superlattices. **2014**, 449, 150-154
- 696 Impurity-related photoionization cross section in a pyramid-shaped quantum dot: Intense laser field and hydrostatic pressure effects. **2014**, 63, 105-113 16
- 695 Anisotropic intrasubband hole scattering by polar optical phonon modes in thin GaAs/ $\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells. **2014**, 72, 156-163 0

694	Superlattice band structure: New and simple energy quantification condition. 2014 , 450, 67-70	5
693	Strain in crystalline core-shell nanowires. 2014 , 67, 30403	22
692	Photonic Mach-Zehnder modulators driven by surface acoustic waves in AlGaAs technology. 2014 ,	1
691	Comprehensive study of AlGaAs/GaAs heterostructures grown by MBE: Structural and compositional analysis. 2014 ,	
690	Fermi-level pinning through defects at GaAs/oxide interfaces: A density functional study. 2015 , 92,	26
689	Generation of Rabi-frequency radiation using exciton-polaritons. 2015 , 92,	12
688	Elastic, Mechanical, and Lattice Dynamic Properties. 2015 , 111-171	
687	Nonmonotonous electron mobility due to structurally induced resonant coupling of subband states in an asymmetric double quantum well. 2015 , 5, 117232	2
686	Acoustoelastic effect of textured (Ba,Sr)TiO ₃ thin films under an initial mechanical stress. <i>Journal of Applied Physics</i> , 2015 , 118, 225305	2.5 6
685	Epitaxial growth of low threading dislocation density InSb on GaAs using self-assembled periodic interfacial misfit dislocations. 2015 , 158, 258-261	9
684	Optical second-harmonic generation in a two-dimensional system. 2015 , 29, 1550042	
683	Effect of Γ X band mixing on the donor binding energy in a Quantum Wire. 2015 , 73, 012100	
682	Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. 2015 , 30, 114012	5
681	Coupling effect of quantum wells on band structure. 2015 , 36, 102005	1
680	Photoluminescence observation of electron-hole droplets in a GaAs/AlAs type-II superlattice. 2015 , 619, 012005	6
679	. 2015 ,	50
678	Non-equilibrium Green's function calculation of AlGaAs-well-based and GaSb-based terahertz quantum cascade laser structures. 2015 , 106, 111111	6
677	Plasmon resonance in new AsSbAlGaAs metal-semiconductor metamaterials. 2015 , 49, 1587-1591	3

676	Reconstruction at the interface of one cycle of trimethylaluminum and water on GaAs(111)A-2 \times 8 from atomic layer deposition. 2015 , 8, 126602	
675	Impact of Anionic Br δ Substitution on Open Circuit Voltage in Lead Free Perovskite (CsSnI $_{3-x}$ Br $_x$) Solar Cells. 2015 , 119, 1763-1767	263
674	Subsurface imaging of coupled carrier transport in GaAs/AlGaAs core-shell nanowires. 2015 , 15, 75-9	7
673	Toward reversing Joule heating with a phonon-absorbing heterobarrier. 2015 , 91,	4
672	Design and characterization of high optical quality InGaAs/GaAs/AlGaAs-based polariton microcavities. 2015 , 106, 021109	7
671	Nonlinear optical absorption via two-photon process in GaAs/Ga $_{1-x}$ Al $_x$ As quantum well. 2015 , 82, 36-41	23
670	Structural, optical, and current investigations of superlattices with a complex AlGaAs-based unit cell. 2015 , 49, 118-123	1
669	Graded metascreens to enable a new degree of nanoscale light management. 2015 , 373,	24
668	Electrically Pumped Vertical-External-Cavity Surface-Emitting Lasers With Patterned Tunnel Junction for Single Transversal-Mode Emission. 2015 , 21, 485-492	0
667	Improved optomechanical disk resonator sitting on a pedestal mechanical shield. 2015 , 17, 023016	17
666	Enhancement of multisubband electron mobility in asymmetrically doped coupled double quantum well structure. 2015 , 476, 91-95	7
665	Nonlinear phonon-assisted cyclotron resonance via two-photon process in asymmetrical Gaussian potential quantum wells. 2015 , 86, 111-120	12
664	Energy-tunable sources of entangled photons: a viable concept for solid-state-based quantum relays. 2015 , 114, 150502	53
663	Polaron effects on optical properties of a modified Gaussian quantum dot. 2015 , 47, 2727-2745	11
662	Electron-phonon interaction in three-barrier nanosystems as active elements of quantum cascade detectors. 2015 , 49, 529-539	2
661	Investigation of internal electric fields in GaAs solar cell under highly-concentrated light. 2015 , 66, 667-671	8
660	Effect of interdiffusion on nonlinear intraband light absorption in Gaussian-shaped double quantum rings. 2015 , 70, 210-216	4
659	Nonlinear phonon-assisted cyclotron resonance via two-photon process in parabolic quantum well. 2015 , 83, 755-765	9

658	Effect of geometry on the pressure induced donor binding energy in semiconductor nanostructures. 2015 , 04, 1550018		
657	Assessment of Polarity in GaN Self-Assembled Nanowires by Electrical Force Microscopy. 2015 , 15, 6770-6		38
656	Photoluminescence study of Be-acceptors in GaInNAs epilayers. <i>Journal of Applied Physics</i> , 2015 , 117, 045705	2.5	2
655	Subcell Debye behavior analysis of order-disorder effects in triple-junction InGaP-based photovoltaic solar cells. 2015 , 168, 309-314		2
654	Investigation of the electrical and optical properties of InAs/InGaAs dot in a well solar cell. 2015 , 15, 1318-1323		13
653	Mass-transport driven growth dynamics of AlGaAs shells deposited around dense GaAs nanowires by metalorganic vapor phase epitaxy. 2015 , 17, 5998-6005		8
652	Growth and kinetic Monte Carlo simulation of InAs quantum wires on vicinal substrates. 2015 , 412, 87-94		5
651	Effect of phonon confinement on one- and two-polar optical phonon capture processes in quantum dots. 2015 , 66, 268-274		2
650	Effects of temperature on binding energy and the nonlinear optical properties of a hydrogenic donor in a GaAs/Ga _{0.8} Al _{0.2} As pillbox immersed in a Ga _{0.6} Al _{0.4} As material. 2015 , 457, 126-131		1
649	Nonlinear optical absorption via two-photon process in asymmetrical Gaussian potential quantum wells. 2015 , 77, 267-275		14
648	Oscillating electron mobility in GaAs/Al _x Ga _{1-x} As double quantum well structure under applied electric field. 2015 , 77, 162-170		5
647	Effect of Si-doped layer position on optical absorption in GaAs quantum well under hydrostatic pressure. 2015 , 77, 196-208		24
646	Quantum efficiency study of the sensitive to blue-green light transmission-mode GaAlAs photocathode. 2015 , 335, 42-47		8
645	Phonon confinement effect on the polaron states in a double quantum ring structure in the presence of electric and magnetic fields. 2015 , 456, 365-370		2
644	A study on structural and electronic properties of GaAs _{1-x} N _x and GaAs _{1-x} Bi _x alloys. 2016 , 4, 6		
643	Ballistic Transport in 1D GaAs/AlGaAs Heterostructures. 2016 ,		
642	Enhancement of multisubband electron mobility in hybrid double quantum well structure. 2016 ,		
641	Calculations of Energy-Loss Function for 26 Materials. 2016 , 29, 663-670		33

640	Design Considerations for Single-Mode Vertical-Cavity Surface-Emitting Lasers With Impurity-Induced Intermixing. 2016 , 52, 1-6	1
639	Electrons, holes, and excitons in GaAs polytype quantum dots. <i>Journal of Applied Physics</i> , 2016 , 119, 125705	6
638	Coherent Excitation of Optical Phonons in GaAs by Broadband Terahertz Pulses. 2016 , 6, 38264	13
637	Effects of hydrostatic pressure on the donor impurity in a cylindrical quantum dot with Morse confining potential. 2016 , 171, 916-924	5
636	Chapter 6 Metasurfaces for Extreme Light Manipulation and Wave Control. 2016 , 191-242	1
635	Observation of a complex Franz-Keldysh oscillation in InAs/GaAs quantum dots. 2016 , 69, 1581-1586	3
634	Optimization of thermoelectric properties for rough nano-ridge GaAs/AlAs superlattice structure. 2016 , 6, 115201	7
633	Design and simulation of high efficiency $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{Ga}_{0.47}\text{In}_{0.53}\text{As}$ bandgraded 2-J tandem solar cell. 2016 ,	
632	An error-function compositional grading scheme in vertical-cavity surface-emitting lasers. 2016 ,	
631	Optical properties of intermixed vertical cavity surface emitting lasers: a theoretical model. 2016 , 48, 1	1
630	Polarization-entangled mid-infrared photon generation in p-doped semiconductor quantum wells. 2016 , 31, 115011	
629	Bowling effect in elastic constants of dilute Ga(As,N) alloys. 2016 , 108, 183106	2
628	Hydrostatic pressure and temperature effects on the binding energy and optical absorption of a multilayered quantum dot with a parabolic confinement. 2016 , 25, 127302	10
627	Pressure induced increase of the exciton phonon interaction in ZnO/(ZnMg)O quantum wells. 2016 , 6, 035106	3
626	Confined optical-phonon-assisted cyclotron resonance in quantum wells via two-photon absorption process. 2016 , 94, 51-59	20
625	Adaptive Integrated Optical Bragg Grating in Semiconductor Waveguide Suitable for Optical Signal Processing. 2016 , 35, 114-127	3
624	Electric field and shape effect on the linear and nonlinear optical properties of multi-shell ellipsoidal quantum dots. 2016 , 94, 204-214	14
623	Spin-orbit interaction in a multilayered spherical quantum dot. 2016 , 90, 1115-1126	4

622	Electromagnetically induced transparency in a spherical quantum dot with hydrogenic impurity in a four level ladder configuration. 2016 , 127, 6351-6357	9
621	Efficiency limit of InAs/GaAs quantum dot solar cells attributed to quantum dot size effects. 2016 , 155, 70-78	18
620	Structural parameters and their effects on the electronic transport properties in aperiodic superlattice profile. 2016 , 96, 8-15	
619	Optical phonons in methylammonium lead halide perovskites and implications for charge transport. 2016 , 3, 613-620	228
618	Al 0.2 Ga 0.8 As X-ray photodiodes for X-ray spectroscopy. 2016 , 840, 168-173	4
617	Group velocity of light in a three level ladder-type spherical quantum dot with hydrogenic impurity. 2016 , 100, 500-507	2
616	Impact of strain on periodic gain structures in vertical external cavity surface-emitting lasers. 2016 , 122, 1	3
615	Modeling and analysis of smoothly diffused vertical cavity surface emitting lasers. 2016 , 9, 56-61	2
614	Exploring diamagnetic susceptibility of impurity doped quantum dots in presence of Gaussian white noise. 2016 , 98, 190-197	6
613	Raman Spectroscopy. 2016 , 77-142	1
612	Investigation on multi-frequency oscillations in InGaAs planar Gunn diode with multiple anode-cathode spacings. 2016 , 247, 1-5	1
611	Carrier-tunneling-induced photovoltaic effect of InAs/GaAs quantum-dot solar cells. 2016 , 69, 566-572	3
610	Microscopic nature of crystal phase quantum dots in ultrathin GaAs nanowires by nanoscale luminescence characterization. 2016 , 18, 063009	10
609	Improved two dimensional electron mobility in asymmetric barrier delta-doped AlGaAs/GaAs inverted MODFET structures. 2016 ,	
608	Thermal conductivity of disordered two-dimensional binary alloys. 2016 , 8, 17815-17819	5
607	Linear and nonlinear magneto-optical absorption in parabolic quantum well. 2016 , 127, 10519-10526	10
606	Dependence on the incident light power of the internal electric fields in a GaAs p-i-n solar cell according to bright photoreflectance spectroscopy. 2016 , 69, 80-84	3
605	Cascading processes in the nonlinear diffraction of light by standing acoustic waves. 2016 , 93,	

604	Cyclotron decay time of a two-dimensional electron gas from 0.4 to 100 K. 2016 , 93,	5
603	Piezoelectric Electromechanical Coupling in Nanomechanical Resonators with a Two-Dimensional Electron Gas. 2016 , 117, 017702	15
602	Image Charge and Electric Field Effects on Hydrogen-like Impurity-bound Polaron Energies and Oscillator Strengths in a Quantum Dot. 2016 , 45, 5847-5852	8
601	Linear and nonlinear magneto-optical absorption in a quantum well modulated by intense laser field. 2016 , 100, 1112-1119	8
600	New Generation of Vertical-Cavity Surface-Emitting Lasers for Optical Interconnects. 2016 , 309-325	
599	Molecular dynamics study on the thermal conductivity of multiple layers in semiconductor disk laser. 2016 ,	
598	High-Temperature In situ Deformation of GaAs Micro-pillars: Lithography Versus FIB Machining. 2016 , 68, 2761-2767	13
597	Electron transport in Al Ga _{1-x} As EMIGFETs: Conductivity enhancement induced by magnetic field effects. 2016 , 100, 867-875	4
596	Partial Oxidized Arsenene: Emerging Tunable Direct Bandgap Semiconductor. 2016 , 6, 24981	30
595	Dynamical Formation Process of Electron-hole Droplets in a GaAs/AlAs Type-II Superlattice. 2016 , 85, 034701	5
594	Transient thermal imaging of a vertical cavity surface-emitting laser using thermoreflectance microscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 045105	2.5 4
593	Bragg resonance in a system of AsSb plasmonic nano-inclusions in AlGaAs. 2016 , 50, 1595-1599	1
592	Impact of a Spacer Layer on the Analog Performance of Asymmetric InP/InGaAs nMOSFETs. 2016 , 63, 2313-2320	15
591	Graphene-GaAs-graphene stacked layers for the improvement of the transmission at the wavelength of 1.55 μ m. 2016 , 57, 120-124	10
590	Dispersion blue-shift in an aperiodic Bragg reflection waveguide. 2016 , 365, 225-230	5
589	Direct Evidence of the Leaky Emission in Oxide-Confined Vertical Cavity Lasers. 2016 , 52, 1-7	12
588	Nonlinear optical absorption via two-photon process in asymmetrical semi-parabolic quantum wells. 2016 , 89, 288-295	11
587	Surface and interface phonon-polaritons in freestanding quantum well wire systems of polar ternary mixed crystals. 2016 , 77, 114-121	2

586	Effects of crossed electric and magnetic fields on the interband optical absorption spectra of variably spaced semiconductor superlattices. 2016 , 488, 72-82	2
585	Electromagnetically induced transparency in a spherical quantum dot with hydrogenic impurity in the external magnetic field. 2016 , 92, 10-23	19
584	Diamagnetic susceptibility: An indicator of pressure induced donor localization in a double quantum well. 2016 , 92, 232-241	8
583	Energy-tunable single-photon light-emitting diode by strain fields. 2016 , 122, 1	2
582	Direct visualization of the in-plane leakage of high-order transverse modes in vertical-cavity surface-emitting lasers mediated by oxide-aperture engineering. 2016 ,	1
581	Mid-infrared entangled photon generation in optimised asymmetric semiconductor quantum wells. 2016 , 90, 107-116	1
580	Ab initio predictions of structure preferences and band gap character in ordered AlAs _{1-x} Bix alloys. 2016 , 16, 288-293	6
579	The DRs in Low Dimensional HD Systems in the Presence of Magnetic Field. 2016 , 3-113	
578	Structural asymmetry induced size quantized nonmonotonous electron mobility in GaAs/Al _x Ga _{1-x} As double quantum well structure. 2016 , 89, 75-82	4
577	Influence of the image charge effect on the hydrogen-like impurity-bound polaron in a spherical quantum dot in the presence of an electric field. 2016 , 75, 174-180	9
576	Simultaneous effects of hydrostatic pressure, temperature and electric field on optical absorption in InAs/GaAs lens shape quantum dot. 2016 , 655, 172-177	26
575	Enhancement of Multisubband Electron Mobility in Barrier Delta-Doped Asymmetric GaAs/AlGaAs Double Quantum Well Structure. 2016 , 33, 17-22	2
574	Effects of surface reconstruction on the epitaxial growth of III-Sb on GaAs using interfacial misfit array. 2017 , 399, 220-228	12
573	Effect of phonons on optical properties of RbCl quantum pseudodot qubits. 2017 , 49, 1	18
572	Terahertz emission characteristics of GaMnAs dilute magnetic semiconductor under 650 mT external magnetic field. 2017 , 17, 522-526	0
571	Improved two-dimensional electron mobility in asymmetric barrier delta-doped GaAs/AlGaAs modulation-doped field-effect transistor structures. 2017 , 56, 034001	3
570	Influence of image charge effect on impurity-related optical absorption coefficients and refractive index changes in a spherical quantum dot. 2017 , 103, 205-212	13
569	The effects of polaronic mass and conduction band non-parabolicity on a donor binding energy under the simultaneous effect of pressure and temperature basing on the numerical FEM in a spherical quantum dot. 2017 , 104, 93-103	17

568	Classical information transfer between distant quantum dots using individual electrons in fast moving quantum dots. 2017 , 254, 1600673	2
567	Resonant cavity light-emitting diodes based on dielectric passive cavity structures. 2017 ,	1
566	Robustness versus thermal effects of single-mode operation of vertical-cavity surface-emitting lasers with engineered leakage of high-order transverse optical modes. 2017 ,	1
565	Sensitive monitoring of photocarrier densities in the active layer of a photovoltaic device with time-resolved terahertz reflection spectroscopy. 2017 , 110, 071108	8
564	Intersubband absorption in m-plane ZnO/ZnMgO MQWs. 2017 ,	2
563	Effects of electron-phonon interaction and impurity on optical properties of hexagonal-shaped quantum wires. 2017 , 88, 1	10
562	Enhancement of multisubband electron mobility in square-parabolic asymmetric double quantum well structure. 2017 , 105, 11-21	8
561	Many-valley electron transport in AlGaAs VCSELs. 2017 , 32, 055007	9
560	Linear and nonlinear optical properties of an off-center donor in GaAs/AlGaAs and AlGaAs/GaAs core-shell ellipsoidal quantum dots. 2017 , 109, 382-393	8
559	Application of nanophotonics to the next generation of surface-emitting lasers. 2017 , 6, 813-829	7
558	Revealing Large-Scale Homogeneity and Trace Impurity Sensitivity of GaAs Nanoscale Membranes. 2017 , 17, 2979-2984	11
557	Optical absorption in a disk-shaped quantum dot in the presence of an impurity. 2017 , 507, 142-146	9
556	Nanoscale effects on the thermal and mechanical properties of AlGaAs/GaAs quantum well laser diodes: influence on the catastrophic optical damage. 2017 , 50, 235101	7
555	Energy-loss rate of hot electrons due to confined acoustic phonon modes in a semiconductor quantum wire under transverse electric field. 2017 , 519, 102-107	4
554	Numerical simulation of Lamb waves propagation in a functionally graded piezoelectric plate composed of GaAs-AlAs materials using Legendre polynomial approach. 2017 , 142, 401-411	25
553	GaAs(100) Surface Passivation with Sulfide and Fluoride Ions. 2017 , 2, 2915-2920	
552	First-principles calculations of the structural and optoelectronic properties of BSb _{1-x} As _x ternary alloys in zinc blende structure. 2017 , 198, 214-228	8
551	Mechanical and thermodynamic properties of AlX (X = N, P, As) compounds. 2017 , 31, 1750167	13

550	Size effect caused significant reduction of thermal conductivity of GaAs/AlAs distributed Bragg reflector used in semiconductor disk laser. 2017 , 96, 259-264		2
549	Optical gain of a triple coaxial cylindrical quantum well wires laser under the geometrical effects and magnetic fields. 2017 , 139, 309-314		6
548	Structural and thermomechanical properties of the zinc-blende AlX (X = P, As, Sb) compounds. 2017 , 31, 1750141		0
547	Resonant optical properties of AlGaAs/GaAs multiple-quantum-well based Bragg structure at the second quantum state. <i>Journal of Applied Physics</i> , 2017 , 121, 103101	2.5	11
546	Supernormal hardness increase of dilute Ga(As, N) thin films. <i>Journal of Applied Physics</i> , 2017 , 121, 095105		1
545	The effects of a geometrical size, external electric fields and impurity on the optical gain of a quantum dot laser with a semi-parabolic spherical well potential. 2017 , 508, 7-11		4
544	Metastable phases, phase transformation and properties of AlAs based on first-principle study. 2017 , 128, 337-342		17
543	Multinary wurtzite-type oxide semiconductors: present status and perspectives. 2017 , 32, 013007		9
542	Phase control of transmission in one-dimensional photonic crystal with defect layer doped by quantum dots. 2017 , 49, 1		2
541	Evidence for various higher-subband resonances and interferences in a GaAs/AlAs asymmetric quadruple-quantum-well superlattice analyzed from its photoluminescence properties. 2017 , 95,		0
540	Cryogenic mechanical loss of a single-crystalline GaP coating layer for precision measurement applications. 2017 , 95,		5
539	Electron Mobility in Al _x Ga _{1-x} As Based Square-Parabolic Double Quantum Well HEMT Structure □ Effect of Asymmetric Doping Profile. 2017 , 254, 1700221		7
538	Polaronic Charge Carrier-Lattice Interactions in Lead Halide Perovskites. 2017 , 10, 3705-3711		12
537	Impact of the growth temperature on the performance of 1.70-eV Al _{0.22} Ga _{0.78} As solar cells grown by MBE. 2017 , 475, 322-327		1
536	Lattice Vibration and Polaron Properties of InSb Under Pressure. 2017 , 52, 1700018		3
535	Modeling the electronic properties of GaAs polytype nanostructures: Impact of strain on the conduction band character. 2017 , 95,		8
534	Modeling of Quantum Well Infrared Photo Detector for Long Wavelength Infrared Detection. 2017 , 63, 719-727		1
533	Understanding band alignments in semiconductor heterostructures: Composition dependence and type-I/type-II transition of natural band offsets in nonpolar zinc-blende Al _x Ga _{1-x} N/Al _y Ga _{1-y} N composites. 2017 , 95,		14

532	Elasticity study of textured barium strontium titanate thin films by X-ray diffraction and laser acoustic waves. 2017 , 56, 055501		2
531	Full momentum- and energy-resolved spectral function of a 2D electronic system. 2017 , 358, 901-906		13
530	Metal-Exchange Catalysis in the Growth of Sesquioxides: Towards Heterostructures of Transparent Oxide Semiconductors. 2017 , 119, 196001		42
529	High-performance Photon-enhanced thermionic emission solar energy converters with Al _x Ga _{1-x} As/GaAs cathode under multilevel built-in electric field. 2017 , 402, 85-90		26
528	Thermomechanical degradation of single and multiple quantum well AlGaAs/GaAs laser diodes. 2017 , 76-77, 588-591		3
527	Optical rectification in quantum wells within different confinement and nonlinearity regimes. 2017 , 111, 556-567		16
526	Effect of carrier confinement on effective mass of excitons and estimation of ultralow disorder in AlGaAs/GaAs quantum wells by magneto-photoluminescence. 2017 , 7, 4905		16
525	Semi-analytical calculation of resonant modes in axially asymmetric microtube resonators. 2017 , 386, 72-76		4
524	Temperature behavior of Franz-Keldysh oscillation and evaluation of interface electric fields attributed to strain effect of InAs/GaAs quantum dot. 2017 , 17, 31-36		2
523	A comprehensive evaluation of factors that influence the spin polarization of electrons emitted from bulk GaAs photocathodes. <i>Journal of Applied Physics</i> , 2017 , 122, 035703	2.5	15
522	Symmetry Breaking-induced Band-splitting in GaAs Thin Film by First-principles Calculations. 2017 , 60, 445-449		2
521	Alloy scattering relaxation time simulation. 2017 ,		0
520	Graded band gap InGaAs diodes for terahertz applications. 2017 ,		0
519	Fiber optic mechanical deformation sensors employing perpendicular photonic crystals. 2017 , 25, 23388-23398		5
518	High frequency optomechanical disk resonators in III-V ternary semiconductors. 2017 , 25, 24639-24649		15
517	Room temperature strong coupling in a semiconductor microcavity with embedded AlGaAs quantum wells designed for polariton lasing. 2017 , 25, 24816-24826		5
516	Improved third-order nonlinear effect in graphene based on bound states in the continuum. 2017 , 5, 629		25
515	Temperature dependence of photoemission characteristics from AlGaAs/GaAs photocathodes. 2017 , 56, 6015-6021		2

514	Optical limiting performance of a GaAs/AlAs heterostructure microcavity in the near-infrared. 2017 , 56, 5811-5816		5
513	Analysis and investigation of temperature and hydrostatic pressure effects on optical characteristics of multiple quantum well slow light devices. 2017 , 56, 7331-7340		1
512	. 2017 ,		
511	Enhancement of multisubband electron transport mobility in square Γ -parabolic double quantum well. 2017 ,		
510	Investigation of elastic moduli and constants of zinc-blende $\text{Al}_y\text{Ga}_{1-y}\text{As}$ alloy by statistical moment method. 2018 , 91, 1		3
509	Valleytronics in thermoelectric materials. 2018 , 3,		67
508	Simultaneous measurement of thermal conductivity and diffusivity of an undoped $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}$ thin film epitaxially grown on a heavily Zn doped GaAs using spectrally-resolved modulated photothermal infrared radiometry. 2018 , 662, 69-74		13
507	Linear and nonlinear magneto-optical absorption in a triangular quantum well. 2018 , 32, 1850162		6
506	The piezoelectric gating effect in a thin bent membrane with a two-dimensional electron gas. 2018 , 30, 184003		1
505	A quantum rings based on multiple quantum wells for 1.2-8 THz detection. 2018 , 101, 162-166		8
504	Magneto-optical properties of semi-parabolic plus semi-inverse squared quantum wells. 2018 , 539, 117-122		26
503	Resonant Optical Reflection from AsSb/AlGaAs Metamaterials and Structures. 2018 , 52, 468-472		
502	Electromagnetically induced transparency in a multilayered spherical quantum dot with hydrogenic impurity. 2018 , 78, 191-200		9
501	Bayesian Spectroscopy of Admixed Photoluminescence Spectra with Exciton, Biexciton and Electron Hole Droplet States in a GaAs/AlAs Type-II Superlattice. 2018 , 197, 18-22		6
500	Optical functions and critical points of dilute bismide alloys studied by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2018 , 123, 045701	2.5	9
499	Extreme Events through Prevailing Backscattering and Their Suppression by a Focusing Nonlinearity. 2018 , 8,		2
498	A comprehensive study of g-factors, elastic, structural and electronic properties of III-V semiconductors using hybrid-density functional theory. <i>Journal of Applied Physics</i> , 2018 , 123, 065702	2.5	13
497	Perturbation method for calculating impurity binding energy in an inhomogeneous cylindrical quantum dot with dielectric mismatch. 2018 , 90, 1		3

496	Theoretical investigation of the structural stabilities, optoelectronic properties and thermodynamic characteristics of GaP _x Sb _{1-x} ternary alloys. 2018 , 92, 705-714	5
495	Optical phonon modes and polaron related parameters in Ga _x In _{1-x} P. 2018 , 531, 144-148	3
494	Stark shift and photoionization cross section of on-center and off-center donor impurity in a core/shell ellipsoidal quantum dot. 2018 , 98, 111-117	7
493	An investigation on the effect of impurity position on the binding energy of quantum box under electric field with pressure and temperature. 2018 , 32, 1850154	3
492	Direct observation of a π energy spectrum transition in narrow AlAs quantum wells. 2018 , 97,	10
491	Anisotropic-Strain-Induced Band Gap Engineering in Nanowire-Based Quantum Dots. 2018 , 18, 2393-2401	9
490	Tuning of the Critical Temperature in Magnetic 2D Coordination Polymers by Mixed Crystal Formation. 2018 , 18, 3117-3123	26
489	Non-extensive entropy of modified Gaussian quantum dot under polaron effects. 2018 , 92, 941-945	6
488	Effects of Temperature, Pressure, and Size on Different Transitions of Optical Properties of Spherical Quantum Dot. 2018 , 42, 1669-1675	1
487	Influence of the position of a donor impurity on the second-order nonlinear optical susceptibility in a cylindrical quantum dot. 2018 , 113, 550-557	12
486	Polaron and dielectric mismatch effects on impurity-related optical absorption and refractive index changes in a spherical quantum dot. 2018 , 113, 442-458	4
485	Semiconductor Materials and Modeling. 2018 , 29-57	0
484	Diffusion Blurring of GaAs Quantum Wells Grown at Low Temperature. 2018 , 52, 1704-1707	2
483	Elastic Properties of Suspended Conducting GaAs/AlGaAs Nanostructures by Means of Atomic Force Microscopy. 2018 , 54, 496-501	
482	Wave packet broadening through different semiconducting mediums: A meshless multi-quadric radial base function study. 2018 , 32, 1850361	1
481	Monte Carlo Modeling of the Diodes with Lateral Resonant Tunneling Border. 2018 ,	0
480	Graded Band Diode for Noise Generation in Terahertz Range. 2018 ,	
479	High quantum efficiency transmission-mode GaAlAs photocathode with a nanoscale surface structure. 2018 , 8, 3155	4

- 478 Theoretical investigations of phases of ALAs by first-principles. **2018**, 56, 2119-2128 2
- 477 A detailed investigation of electronic and optical properties of single exciton in GaAs/Al_xGa_{1-x}As/GaAs/Al_yGa_{1-y}As multi-shell quantum dot. **2018**, 98, 3109-3125 3
- 476 Pressure and composition dependence of thermodynamic properties of zinc-blende Al_yGa_{1-y}As alloy. **2018**, 133, 1
- 475 A meshless method of line radial base function study of Gaussian wave packet broadening in few semiconducting mediums: electron-electron interaction effects. **2018**, 50, 1 1
- 474 Nonlinear electron transport in asymmetric double quantum well structures. **2018**,
- 473 Radiative and non-radiative recombination of thermally activated magneto-excitons probed via quasi-simultaneous photoluminescence and surface-photovoltage spectroscopy. *Journal of Applied Physics*, **2018**, 124, 055704 2.5 4
- 472 Phonon-assisted cyclotron resonance in special symmetric quantum wells. **2018**, 124, 1 9
- 471 Electron trapping in the photo-induced conductivity decay in GaAs/SnO₂ heterostructure. **2018**, 124, 1 3
- 470 Resonant intersubband polariton-LO phonon scattering in an optically pumped polaritonic device. **2018**, 112, 191106 10
- 469 Selective dependence of the electron-phonon interaction on the nature of the optical transition in AlGaAs quantum wells. **2018**, 202, 322-326 3
- 468 Nonlinear electron transport mobility in asymmetric wide quantum well structure. **2018**, 92, 1091-1097
- 467 Simultaneous measurement of infrared absorption coefficient of Carbon doped Al_{0.33}Ga_{0.67}As thin film and thermal boundary resistance between thin film and heavily Zn doped GaAs substrate using spectrally-resolved modulated photothermal infrared radiometry. **2018**, 667, 73-78 6
- 466 Single junction solar cell employing strain compensated GaAs_{0.965}Bi_{0.035}/GaAs_{0.75}P_{0.25} multiple quantum wells grown by metal organic vapor phase epitaxy. **2018**, 112, 251105 4
- 465 Prediction of optical band gap of $\Gamma(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ using material informatics. **2018**, 11, 1-5 12
- 464 Spin relaxation mediated by spin-orbit and acoustic phonon interactions in a single-electron two-dimensional quantum dot. **2018**, 122, 548-556 1
- 463 AlGaAs-based vertical-external-cavity surface-emitting laser exceeding 4 W of direct emission power in the 740-790 nm spectral range. **2018**, 43, 1578-1581 8
- 462 Multisubband Plasmons in Doped ZnO Quantum Wells. **2018**, 10, 14
- 461 Structural, Mechanical, Anisotropic, and Thermal Properties of ALAs in C12 and P6 Phases under Pressure. **2018**, 11, 12

460	A Topological View on Optical and Phononic Fabry-Pérot Microcavities through the Su-Schrieffer-Heeger Model. 2018 , 8, 527	6
459	Analysis of in-plane thermal phonon transport in III-V compound semiconductor superlattices. 2018 , 22, 239-253	3
458	Broadband ultrafast terahertz spectroscopy in the 25 T Split Florida-Helix. 2018 , 89, 073901	2
457	LO-phonon-assisted cyclotron resonance in a special asymmetric hyperbolic-type quantum well. 2018 , 120, 738-746	20
456	Effect of parabolic potential on improvement of electron mobility in hybrid double quantum well structure. 2018 ,	0
455	Magneto-optical absorption in quantum dot via two-photon absorption process. 2018 , 173, 263-270	3
454	Effect of non-square structure potential on the multisubband electron mobility in double quantum well structure. 2018 , 545, 62-68	7
453	Intersubband optical properties of three electrons confined in multishell quantum dots: comparison of two semiconducting compounds. 2018 , 17, 1135-1142	11
452	Microhardness, phase transition, acoustic wave velocities and melting temperature of Al _x Ga _{1-x} Sb. 2018 , 32, 1850210	2
451	Temperature dependence of phonons and related crystal properties in InAs, InP and InSb zinc-blende binary compounds. 2018 , 16, e00308	7
450	GaN-based vertical-cavity surface-emitting lasers with AlInN/GaN distributed Bragg reflectors. 2019 , 82, 012502	20
449	Determining the Optimal Phase-Change Material via High-Throughput Calculations. 2019 , 4, 2679-2687	2
448	Resonant optical studies of GaAs/AlGaAs Multiple Quantum Well based Bragg Structures at excited states. 2019 , 4, 651-659	0
447	Spatial distribution of thermoelectric voltages in a Hall-bar shaped two-dimensional electron system under a magnetic field. 2019 , 3, 055005	3
446	Simulation Study of an Apertured Planar Microcavity for Efficient Single-Photon Sources. 2019 , 75, 63-67	
445	Bridging scales in multiphysics VCSEL modeling. 2019 , 51, 1	1
444	Comprehensive Analysis of Electric Properties of Oxide-Confined Vertical-Cavity Surface-Emitting Lasers. 2019 , 25, 1-9	4
443	Structural, electronic and thermal properties of Al _x Ga _{1-x} As ternary alloys: Insights from DFT study. 2019 , 92, 140-146	3

442	First principle study of the structural, electronic, optical and thermodynamic properties of the cubic Al _{1-x} B _x As ternary alloys. 2019 , 6, 105902		3
441	Blueshift of Optical Signal in PhC Based Butterworth Filter Due to Joule Heat Dissipation. 2019 , 352-360		
440	Influence of Pressure on Polaron Energy in a Wurtzite GaN/Al _x Ga _{1-x} N Quantum Well. 2019 , 288, 17-26		
439	GaAs quantum well in the non-parabolic case: the effect of hydrostatic pressure on the intersubband absorption coefficient and the refractive index. 2019 , 86, 20101		6
438	Ultrafast dynamics of pure many-body effect and its competition with bandgap widening via electron-phonon coupling in PbTe thin films. 2019 , 34, 105011		4
437	Temperature effect on the diamagnetic susceptibility of a shallow magneto-donor in GaAs/AlAs Quantum Box. 2019 , 1292, 012002		
436	Design of high-performance double quantum well vertical cavity transistor lasers with GRIN base region. 2019 , 125, 1		1
435	Terahertz intersubband transitions in GaAsBi/AlGaAs single quantum well heterostructure. 2019 , 136, 106299		3
434	The hydrostatic pressure and magnetic field effect on the diamagnetic susceptibility of a shallow donor in GaAs/AlAs Quantum Box. 2019 , 1292, 012001		1
433	Thermal analysis and heat dissipation improvement for quantum cascade lasers through experiments, simulations, and structure function. 2019 , 58, 091008		6
432	Investigating the Role of Band Offset on the Property and Operation of the Potential Well Barrier Diodes. 2019 , 256, 1800284		1
431	Real-Time Electron and Hole Transport Dynamics in Halide Perovskite Nanowires. 2019 , 19, 8701-8707		7
430	Diodes with Lateral n ⁺ -n ⁻ -Border. 2019 ,		0
429	Monte Carlo modeling of thin GaAs photocathodes. <i>Journal of Applied Physics</i> , 2019 , 126, 075706	2.5	2
428	Surface-Acoustic-Wave Induced Ferromagnetic Resonance in Fe Thin Films and Magnetic Field Sensing. 2019 , 12,		17
427	Impact of piezoelectric fields on coherent zone-folded phonons in GaAs/AlAs superlattices. 2019 , 100,		1
426	Phonon-assisted cyclotron resonance in Pöschl-Teller quantum well. <i>Journal of Applied Physics</i> , 2019 , 126, 124301	2.5	12
425	Optical absorption coefficients in asymmetric quantum well. 2019 , 383, 125983		7

424	Oscillation of Electron Mobility in V-Shaped Double Quantum Well Structure Under Applied Electric Field. 2019 , 256, 1800337		3
423	VENUS: A Vertical-Cavity Surface-Emitting Laser Electro-Opto-Thermal NUmberical Simulator. 2019 , 25, 1-12		13
422	One- and two-photon-induced cyclotron-phonon resonance in modified-Pöschl-Teller quantum well. 2019 , 125, 1		11
421	Double two-photon absorption in an asymmetric stepped quantum well in the terahertz range. 2019 , 130, 560-568		5
420	Merging of defect modes in a superlattice of one-dimensional metamaterials photonic crystals. 2019 , 9, 055318		4
419	Broadband Photo-Excited Coherent Acoustic Frequency Combs and Mini-Brillouin-Zone Modes in a MQW-SESAM Structure. 2019 , 9, 289		5
418	Computational Intelligence, Communications, and Business Analytics. 2019 ,		
417	Structural parameters, energy gaps and density of states of AlAs _{1-x} Bix semiconducting ternary alloys. 2019 , 6, 085915		4
416	Electron transport in Al _x Ga _{1-x} As based double quantum well modulation doped field effect transistor structure: effect of non-square potential profile. 2019 , 29, 084003		2
415	Simultaneous magneto-electro-optical measurements in modulation-doped quantum well: An investigation on magneto-photoluminescence intensity oscillations. <i>Journal of Applied Physics</i> , 2019 , 125, 205701	2.5	1
414	Mid-infrared supercontinuum generation and its application on all-optical quantization with different input pulses. 2019 , 28, 054206		2
413	Detection of optically injected spin polarized electrons in the L-valley of AlGaAs through polarization resolved photoluminescence excitation spectroscopy. 2019 , 213, 204-209		3
412	Metallic AsSb nanoinclusions strongly enriched by Sb in AlGaAsSb metamaterial. <i>Journal of Applied Physics</i> , 2019 , 125, 145106	2.5	4
411	Two-photon induced magneto-optical absorption in finite semi-parabolic quantum wells. 2019 , 130, 446-453		
410	Femtosecond Pump Probe Spectroscopy Implementation for Semiconductors. 2019 , 288, 148-152		0
409	Magneto-optical effect in GaAs/GaAlAs semi-parabolic quantum well. 2019 , 682, 10-17		26
408	One- and two-photon-induced magneto-optical properties of hyperbolic-type quantum wells. 2019 , 185, 1261-1269		3
407	Design and performance simulation of microcavity enhanced bilayer graphene infrared photodetector. 2019 , 447, 24-29		3

406	Achieving balance of valley occupancy in narrow AlAs quantum wells. <i>Journal of Applied Physics</i> , 2019 , 125, 154501	2.5	4
405	Large-scale spin-polarized DFT calculation of electronic properties of GaAs with defects. 2019 , 6, 055914		4
404	Effect of magnetic field on absorption coefficients, refractive index changes and group index of spherical quantum dot with hydrogenic impurity. 2019 , 91, 62-69		19
403	Effects of ternary mixed crystals on interface/surface optical phonon in spherical core-shell quantum dots. 2019 , 33, 1950068		1
402	Hydrostatic Pressure and Temperature Effect on the Electron-Related Optical Responses in Symmetric and Asymmetric n-Type Double Delta-Doped GaAs Quantum Well Under Terahertz Laser Field. 2019 , 48, 3537-3546		5
401	Effect of the impurity on the Aharonov-Bohm oscillations and the intraband absorption in GaAs/AlAs quantum ring under intense THz laser field. 2019 , 111, 91-97		8
400	AlInP photodiode x-ray detectors. 2019 , 52, 225101		3
399	Tunable Direct Band Gap of ECuGaO and ELiGaO Solid Solutions in the Full Visible Range. 2019 , 58, 4262-4267		6
398	Half-metallic fully compensated ferrimagnetism and multifunctional spin transport properties of Mn ₃ Al. 2019 , 31, 305501		4
397	Slow and fast light propagation and controllable switch at $\lambda = 1.55 \mu\text{m}$ in a photonic crystal with a defect layer doped by an InAs/GaAs quintuple-coupled quantum dot molecule nanostructure. 2019 , 29, 056202		4
396	The effects of intraband and interband carrier-carrier scattering on hot-carrier solar cells: A theoretical study of spectral hole burning, electron-hole energy transfer, Auger recombination, and impact ionization generation. 2019 , 27, 433-452		9
395	Viscoelastic response of quantum Hall fluids in a tilted field. 2019 , 99,		8
394	Study of the Role of Window Layer Al _{0.8} Ga _{0.2} As on GaAs-based Solar Cells Performance. 2019 , 12, 1-9		1
393	Mode-conversion effects of phonons on Anderson localization. 2019 , 100,		2
392	Design and Optimization of AlGaAs/InP Multi-junction Solar Cell. 2019 ,		
391	(V, Ti) co-doping effect on electronic and magnetic properties of zb-AlAs. 2019 , 33, 1950326		6
390	Strain-induced control of a pillar cavity-GaAs single quantum dot photon source. 2019 , 9, 18564		1
389	Anticrossing of optical modes in coupled microcavities. 2019 , 1400, 066032		

388	High-performance GaAs nanowire cathode for photon-enhanced thermionic emission solar converters. 2019 , 54, 5605-5614	36
387	Optical filtering devices in SiO ₂ /AlGaAs superlattice structures. 2019 , 125, 220-232	2
386	Effect of Conduction Band Non-Parabolicity on the Nonlinear Optical Properties in GaAs/ Double Semi-V-shaped Quantum Wells. 2018 , 12,	10
385	Photoluminescence from InAs Quantum Dots Buried Under Low-Temperature-Grown GaAs. 2019 , 256, 1800479	1
384	Optical Properties of Energy-Dependent Effective Mass GaAs/GaxIn _{1-x} As and GaAs/AlxGa _{1-x} As Quantum Well Systems: A Shooting Method Study. 2019 , 48, 942-950	5
383	Enhancement of electron mobility in GaAs/AlxGa _{1-x} As square-parabolic double quantum well HEMT structure. 2019 , 25, 1901-1907	1
382	Effect of external electric field on multisubband electron mobility in n-V-shaped double quantum well HEMT structure. 2020 , 95, 034002	
381	AlGaAs two by two pixel detector for electron spectroscopy in space environments. 2020 , 951, 163039	2
380	Modeling and optimization of n-c-AlGaAs/p-c-GaAs solar cells. 2020 , 202, 163609	
379	Correlation between open-circuit voltages and preferential glide planes of misfit dislocations of metamorphic InGaAs single junction solar cells grown on GaAs. 2020 , 533, 125432	4
378	Slow light pulse propagation through spherical quantum dot with on-center hydrogen impurity in magnetic field. 2020 , 118, 113883	1
377	Collective effects and optical characteristics of CdSexTe _{1-x} . 2020 , 203, 163952	1
376	The effects of close packing and electric fields on the optical properties of three-dimensionally stacked quantum dots. 2020 , 19, 160-169	1
375	Optical properties and chemical bonding of 3C-SiC under high-pressure. 2020 , 202, 163613	4
374	Effect of electric field non-uniformity on the differences between I-V characteristics of QWIP devices fabricated on the same wafer. 2020 , 301, 111725	0
373	Electronic transport in n-type modulation-doped AlGaAs/GaAsBi quantum well structures: influence of Bi and thermal annealing on electron effective mass and electron mobility. 2020 , 35, 025009	2
372	Electric field induced non-linear multisubband electron mobility in V-shaped asymmetric double quantum well structure. 2020 , 100, 512-527	5
371	Linear and third order nonlinear optical properties of GaAs quantum dot in terahertz region. 2020 , 118, 113913	9

- 370 Optical properties of a two-dimensional GaAs quantum dot under strain and magnetic field. **2020**, 135, 1 2
- 369 Magnetic Field Dependence of Excitonic and Optical Properties of InP/ZnS Core/Shell Nanostructure. **2020**, 49, 7386-7393
- 368 Heterostructure design to achieve high quality, high density GaAs 2D electron system with g-factor tending to zero. **2020**, 117, 022102
- 367 Measurement of thermal transport properties of selected superlattice and thin films using frequency-domain photothermal infrared radiometry. **2020**, 166, 108226 7
- 366 Nonlinear pressure effect on the electronic states induced by a defect layer in a Multi-Quantum wells structure. **2020**, 31, S109-S113 3
- 365 Ab-initio study on the phase transition, elastic, optoelectronic, and thermodynamic properties of GaAs_{1-x}Sbx. **2020**, 219, 165253 3
- 364 Ab-initio study of ordered III \bar{V} antimony-based semiconductor alloys (\mathbf{GaP}_{1-x} \mathbf{Sb}_x and \mathbf{AlP}_{1-x} \mathbf{Sb}_x). **2020**, 94, 1 2
- 363 Impact of the synthetic approach on the magnetic properties and homogeneity of mixed crystals of tunable layered ferromagnetic coordination polymers. **2020**, 49, 16707-16714 7
- 362 Analysis of Phonon Modes and Electron-Phonon Interaction in Quantum-Cascade Laser Heterostructures. **2020**, 54, 936-940
- 361 A nonparabolic conduction band study of circular quantum dot optical properties: modeling of surface roughness by using Koch snowflakes. **2020**, 22, 1 1
- 360 An extended moments model of quantum efficiency for metals and semiconductors. *Journal of Applied Physics*, **2020**, 128, 015301 2.5 3
- 359 Light storage and retrieval in spherical semiconductor quantum dots with on-center hydrogen impurity in magnetic field. **2020**, 147, 106691 2
- 358 Phononic bandgap and phonon anomalies in HfN and HfN/ScN metal/semiconductor superlattices measured with inelastic x-ray scattering. **2020**, 117, 111901 1
- 357 The Influence of Hydrostatic Pressure on the Binding Energy of Hydrogenic Impurity State in a Wurtzite AlyGa_{1-y}N/AlxGa_{1-x}N Parabolic Quantum Well. **2020**, 310, 14-21
- 356 Energy spectra of position-dependent masses in double heterostructures. **2020**, 95, 075207 0
- 355 Recent Progress on Extended Wavelength and Split-Off Band Heterostructure Infrared Detectors. **2020**, 11, 3
- 354 The structural effects on performance of a lateral AlGaAs/GaAs quantum well solar cell. **2020**, 41, 100799
- 353 Photoexcited elastic waves in free-standing GaAs films. **2020**, 101, 3

352	Polaron transport in hybrid CHNHPbI perovskite thin films. 2020 , 12, 14112-14119	4
351	Tunable electronic and optical properties of two-dimensional ZnSe/AlAs van der Waals heterostructure. 2020 , 126, 1	5
350	Investigation on Rashba spin-orbit interactions in two dimension quantum array for thermal imaging applications. 2020 , 22, 085001	0
349	Photoelectric process in GaAs quantum dot. 2020 , 28, 350-352	
348	Improved Light Output of AlGaInP-Based Micro-Light Emitting Diode Using Distributed Bragg Reflector. 2020 , 32, 438-441	8
347	Investigation of coherency stress-induced phase separation in AlN/Al _x Ga _{1-x} N superlattices grown on sapphire substrates. 2020 , 22, 3198-3205	2
346	A detailed comparison of measured and simulated optical properties of a short-period GaAs/Al _x Ga _{1-x} As distributed Bragg reflector. 2020 , 35, 055003	1
345	Theoretical investigation of the transient regime of electromagnetically induced transparency in spherical quantum dot with on-center hydrogen impurity. 2020 , 52, 1	1
344	Phonon and Polaron properties in InSb spherical quantum dots. 2020 , 65, 146-152	3
343	Electron-Interface phonon scattering in quantum wells due to absorption and emission of interface phonons. 2020 , 120, 114043	10
342	Influence of confined optical phonons on the magneto-optical properties in parabolic quantum wells. 2020 , 145, 109501	10
341	Combined effects of temperature, hydrostatic pressure, and aluminum concentration on the magneto-optical properties of GaAs/Al _x Ga _{1-x} As quantum wells when phonons are confined. 2020 , 145, 106626	2
340	Intersubband and intrasubband electron scattering by acoustic-phonons in quantum wells. 2020 , 206, 164348	10
339	Real-Space Characterization of Cavity-Coupled Waveguide Systems in Hypersonic Phononic Crystals. 2020 , 13,	7
338	Using SiO ₂ -Based Distributed Bragg Reflector to Improve the Performance of AlGaInP-Based Red Micro-Light Emitting Diode. 2020 , 9, 036002	4
337	Binding energies and optical absorption of donor impurities in spherical quantum dot under applied magnetic field. 2020 , 119, 114011	22
336	First-principles study of rocksalt Mg _x Zn _{1-x} O: band structure and optical spectra. 2020 , 100, 1620-1635	2
335	Structural Features and Photoelectric Properties of Si-Doped GaAs under Gamma Irradiation. 2020 , 10,	1

334	Temperature Dependence of Raman and Photoluminescence Spectra of Ternary Alloyed CdSe _{0.3} Te _{0.7} Quantum Dots. 2020 , 49, 2568-2577	1
333	Broadband Dynamic Polarization Conversion in Optomechanical Metasurfaces. 2020 , 7,	2
332	Optical vibration modes in multi-layer quantum dots of polar ternary mixed crystals. 2020 , 121, 114124	1
331	Simple theoretical analyses of the Burstein-Moss shift (BMS) revisited for n-GaAs semiconductor with and without band-tailing conditions. 2021 , 95, 443-448	1
330	Pressure induced transition of direct to indirect excitons in double quantum well: Effect of EX crossover. 2021 , 126, 114482	
329	Comprehensive analysis of the composition determination in epitaxial Al Ga As films: A multitechnique approach. 2021 , 123, 105469	1
328	The effects of hydrostatic pressure and temperature on photoionization cross section of impurities in semiconductors under magnetic and intense terahertz laser fields. 2021 , 111, 110688	0
327	The effect of strain and spatial Bi distribution on the band alignment of GaAsBi single quantum well structure. 2021 , 602, 412487	0
326	Limiting mechanisms for photon recycling in thin-film GaAs solar cells. 2021 , 29, 379-390	7
325	A comparative study of the structural and optical properties of Si-doped GaAs under different ion irradiation. 2021 , 111, 110611	6
324	Magneto-optical transport properties of parabolic potential GaAs/Ga _{1-x} Al _x As wells under the influence of Al concentration and hydrostatic pressure. 2021 , 127, 114491	4
323	Temperature, hydrostatic pression and composition x effects on intersubband energy levels in ZnSe/ZnS _x Se _{1-x} core-shell quantum dot. 2021 , 225, 165860	3
322	Intra-band Raman scattering and gain in a double quantum well wire with asymmetrical barriers. 2021 , 600, 412640	
321	Electronic, optical, and thermoelectric properties of perovskite variants A ₂ BX ₆ : Insight and design via first-principles calculations. 2021 , 45, 4495-4507	11
320	Zeeman splitting, Zeeman transitions and optical absorption of an electron confined in spherical quantum dots under the magnetic field. 2021 , 101, 117-128	6
319	Governing Equations. 29-56	
318	Imaging of surface acoustic waves on GaAs using 2D confocal Raman microscopy and atomic force microscopy. 2021 , 118, 031602	1
317	Defects and dopants in zinc-blende aluminum arsenide: a first-principles study. 2021 , 23, 013018	

316	Bright Single Photon Emission from Quantum Dots Embedded in a Broadband Planar Optical Antenna. 2021 , 9, 2001490	4
315	Refractive indices of MBE-grown Al _x Ga _(1-x) As ternary alloys in the transparent wavelength region. 2021 , 11, 025327	14
314	Binding energy and photoionization cross section of hydrogenic impurities in elliptic cylindrical core/shell quantum dots under a non-axial electric field. 2021 , 150, 106818	4
313	Optical bistability in reflection of the laser pulse in a 1D photonic crystal doped with four-level InGaN/GaN quantum dots. 2021 , 31, 036202	5
312	Cavity optomechanics with photonic bound states in the continuum. 2021 , 3,	7
311	Nonlinear magneto-optical absorption in a finite semi-parabolic quantum well. 2021 , 53, 1	5
310	Prediction of inverse spin Hall devices based on the direct injection of carriers in L-valley of GaAs. 2021 , 54, 205101	1
309	Communication Strategy to Reduce the Content of Residual Oxide Layer on SiC Surface in ECMP. 2021 , 10, 044006	0
308	RECYCLING TECHNOLOGY OF ACTIVE MATERIALS OF THE ZINC-MANGANESE CURRENT SOURCES. 2021 , 87, 128-136	1
307	Semiconductor Lasers. 2021 , 81-122	
306	Possibility of intracavity terahertz difference frequency generation in a two-frequency GaAsP/AlGaAs/GaAs quantum well laser. 2021 , 60, 4404-4409	
305	Anisotropy mechanical behavior of crystals based on gallium arsenide cleavage processing. 2021 ,	0
304	Cyclotron interface phonon resonance line-width in asymmetric semiparabolic quantum wells. 2021 , 152, 109967	4
303	Electron mobility in asymmetric coupled Al _x Ga _(1-x) As parabolic quantum well structure Impact of external electric field. 2021 , 608, 412798	3
302	A first-principles study of the vibrational and thermodynamic properties of Ga _{Bix} As _(1-x) alloys. 1	
301	Near infrared integrated photonic switches for portable quantum sensors. 2021 , 1919, 012007	1
300	Influence of piezoelectric phonons on the magneto optical transition linewidth in GaN and GaAs. 2021 , 129, 114601	5
299	Tuning the Mode Splitting of a Semiconductor Microcavity with Uniaxial Stress. 2021 , 15,	2

298	Dark curve analysis of thin-film GaAs solar cells, with a focus on photon recycling approaches. 2021 ,	
297	Investigation on structural, electronic, thermal and thermoelectric properties of $\text{Al}_{0.75}\text{B}_{0.25}\text{As}$ under pressure based on density functional theory. 2021 , 95, 1	
296	Experimental Validation of Formula for Calculation Thermal Diffusivity in Superlattices Performed Using a Combination of Two Frequency-Domain Methods: Photothermal Infrared Radiometry and Thermoreflectance. 2021 , 11, 6125	3
295	Coherent phonon detection gated by transient spin-polarized electrons. 2021 , 103,	
294	A review on thermalization mechanisms and prospect absorber materials for the hot carrier solar cells. 2021 , 225, 111073	9
293	Influence of hydrostatic pressure, temperature, and terahertz laser field on the electron-related optical responses in an asymmetric double quantum well. 2021 , 94, 1	0
292	Universal alignment of surface and bulk oxygen levels in semiconductors. 2021 , 119, 021601	0
291	Disorder effect upon energy band gaps and carrier effective masses of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$. 2021 , 136, 1	0
290	Determination of the acoustic phonon-hot carriers interaction in n- and p-type modulation-doped GaInNAs/GaAs quantum wells. 2021 , 612, 412946	1
289	Theory of Graded-Bandgap Thin-Film Solar Cells. 2021 , 2, 1-140	1
288	Accurate modeling and characterization of photothermal forces in optomechanics. 2021 , 6, 086101	1
287	UV-Vis-NIR broadband response of GaAs-based photocathode with multilayer graded-band cascade structure. 2021 , 156, 106957	0
286	Anisotropy of optical phonons in biaxially stressed zinc-blende- and diamond-type semiconductors and alloys. 2021 , 614, 413008	1
285	Design and simulation of double-heterojunction solar cells based on Si and GaAs wafers. 2021 , 5, 085008	6
284	Effect of size modulation and donor position on intersubbands refractive index changes of a donor within a spherical core/shell/shell semiconductor quantum dot. 2021 , 42, 694-701	2
283	A quantitative analysis of electronic transport in n- and p-type modulation-doped GaAsBi/AlGaAs quantum well structures.	0
282	Polaronic mass and non-parabolicity effects on the photoionization cross section of an impurity in a double quantum dot. 2021 , 159, 107049	3
281	Enhanced absorption process in the thin active region of GaAs based p-i-n structure*. 2021 , 30, 097803	0

280	Opto-thermally controlled beam steering in nonlinear all-dielectric metastructures. 2021 , 29, 37128-37139	4
279	Innovative Infrared-pulsed laser assisted RF sputtered $\text{InGa}_{20}\text{O}_3$ thin film at low temperature process. 2021 , 879, 160435	1
278	Comparison of the contribution of different types of interface-optical phonon modes to electron-phonon scattering in a quasi-two-dimensional system. 2021 , 621, 413317	2
277	Novel photoelectrochemically combined mechanical polishing technology for scratch-free 4H-SiC surface by using $\text{CeO}_2\text{-TiO}_2$ composite photocatalysts and PS/ CeO_2 core/shell abrasives. 2021 , 570, 151141	7
276	All-optical half adder based on non-linear triangular lattice photonic crystals with improved contrast ratio. 2021 , 15, 20-26	1
275	Gallium arsenide (GaAs) structure, phase diagram, equation of state. 1-7	1
274	Dynamics of High-Power Diode Lasers. 2000 , 55-81	5
273	Analysis of Channeled-Substrate-Planar Double-Heterostructure Lasers Using the Effective Index Technique. 1990 , 74-143	2
272	Band Structures of Selected Semiconductors and Their Alloys. 1995 , 233-331	7
271	On the Influence of Resonant States on Ballistic Transport in Open Quantum Dots: Spectroscopy and Tunneling in the Presence of Multiple Conducting Channels. 2003 , 209-276	14
270	Gallium Arsenide (GaAs). 1999 , 213-226	2
269	Interfaces in III-V High Efficiency Solar Cells. 2014 , 545-570	1
268	The Einstein Relation in Compound Semiconductors Under Magnetic Quantization. 2009 , 51-105	1
267	Modulation Efficiency Limited High Frequency Performance of the MODFET. 1987 , 181-183	4
266	Near Band Gap Photoemission in $\text{Al}_{0.27}\text{Ga}_{0.63}\text{As}/\text{GaAs}$ Quantum Wells. 1988 , 185-188	2
265	Mode-Controlled Semiconductor Lasers. 1990 , 211-316	11
264	Semiconductor Integrated Optic Devices. 1990 , 317-395	7
263	Introduction. 1996 , 1-26	2

262	Introduction. 1999 , 1-26	1
261	Operating Principles of VCSELs. 2003 , 53-98	29
260	XRD and Raman Study of Low Temperature AlGaAs/GaAs (100) Heterostructures. 2010 , 225-236	1
259	Long Wave Polar Optical Phonons in Heterostructures. 1993 , 1-12	2
258	X-Ray Diffraction Analysis of Strains and Stresses in Thin Films. 1988 , 27, 143-200	35
257	The Electrodynamics of Superlattices. 1989 , 459-541	1
256	Temperature dependence of commercial 4H-SiC UV Schottky photodiodes for X-ray detection and spectroscopy. 2017 , 859, 76-82	12
255	Magneto-optical absorption in Pöschl-Teller-like quantum well. 2020 , 592, 412279	3
254	Gunn instabilities in power HEMTs. 2001 , 37, 530	5
253	Singular localised states in quasiperiodic GaAs/Al _x Ga _{1-x} As Fibonacci superlattices. 2006 , 35, 113-116	2
252	Recent advances in mechanical strain engineering of low-dimensional semiconductors and their applications in high-performance quantum emitters. 2020 , 35, 103002	2
251	Power loss mechanisms in n-type modulation-doped AlGaAs/GaAsBi quantum well heterostructures. 2020 , 35, 095038	1
250	Al _{0.6} Ga _{0.4} As x-ray avalanche photodiodes for spectroscopy. 2020 , 35, 095026	5
249	30 GHz bandwidth temperature stable 980 nm vertical-cavity surface-emitting lasers with AlAs/GaAs bottom distributed Bragg reflectors for optical data communication. 2020 , 2, 035008	2
248	Optical and structural analysis of ultra-long GaAs nanowires after nitrogen-plasma passivation. 2020 , 1, 020019	2
247	Quantum Dot Lasers. 2003 ,	120
246	Quantum-dot edge-emitting lasers. 2003 , 130-154	2
245	Design rules for modulation-doped AlAs quantum wells. 2017 , 1,	11

244	Working principles of doping-well structures for high-mobility two-dimensional electron systems. 2020 , 4,	8
243	Optical nonlinearities of InP/ZnS core/shell and inverted core/shell quantum dot. 2018 , 12, 1	3
242	Controlling the light propagation in one-dimensional photonic crystal via incoherent pump and interdot tunneling. 2018 , 57, 1	2
241	Material Removal Rate of 4H-SiC Polishing with Polystyrene/CeO ₂ Core/shell Abrasives. 2020 , 9, 104001	3
240	Intervalley Scattering and the Role of Indirect Band Gap AlAs Barriers: Application to GaAs/AlGaAs Quantum Cascade Lasers. 2008 , 113, 891-902	2
239	Optoelectronic optimization of graded-bandgap thin-film AlGaAs solar cells. 2020 , 59, 1018-1027	9
238	Ultrahigh-Q AlGaAs-on-insulator microresonators for integrated nonlinear photonics. 2020 , 28, 32894-32906	14
237	Dispersive optomechanics of supercavity modes in high-index disks. 2020 , 45, 5238-5241	2
236	Concentration-size dependences for the electron energy in Al _x Ga _{1-x} As/GaAs/Al _x Ga _{1-x} As nanofilms. 2014 , 17, 160-164	1
235	Temperature changes in the exciton absorption band observed in flat double nanoheterostructures GaAs/Al _x Ga _{1-x} As. 2015 , 18, 128-133	1
234	Collective plasma excitations in two-dimensional electron systems. 2020 , 63, 975-993	3
233	Effect of the Aluminium Fraction on Subminiband Structures of Fibonacci Al _x Ga _{1-x} As/GaAs Superlattices. 2006 , 6, 3140-3144	3
232	A two-dimensional electron gas sensing motion of a nanomechanical cantilever. 2017 , 8, 111-115	1
231	Analysis of electric-field domain formations and carrier transport phenomena in GaAs/AlAs asymmetric double-quantum-well superlattices.	
230	Phase transition, band structure, optical spectra and magnetic moment of MnO magnetic material upon compression. 2021 , 94, 1	0
229	Accurate and fully analytical expressions for quantum energy levels in finite potential wells for nanoelectronic compact modeling. 1	1
228	Asymmetric doping induced nonlinear electron mobility in double V-shaped quantum well based FET structure under external electric field. 2021 , 96, 124047	
227	Highly coherent and multi-octave mid-infrared supercontinuum generations in a reverse-strip AlGaAs waveguide with three zero-dispersion wavelengths. 2021 , 60, 9994-10001	0

- 226 Influence of the confining potential on the linewidth of a quantum well. **2021**, 160, 107068 3
- 225 Optical Investigation of Coupled GaAs/Al_{0.3}Ga_{0.7}As Double Quantum Wells Separated by AlAs Barriers. **2000**, 91-95 2
- 224 Second harmonic generation in 1-D photonic crystal based cavities. **2001**,
- 223 Chemical Vapor Epitaxy of Al_xGa_{1-x}As. **2001**, 1187-1191
- 222 Generation and detection of picosecond acoustic phonon pulses in a double quantum well structure. **2001**, 871-872
- 221 Characterization of AlGaAs/AlAs Waveguides for Optical Parametric Generation. **2001**, 35-41
- 220 Optische Sender: Grundlagen. **2002**, 594-621
- 219 Physical properties of amorphous gallium arsenide. **2002**, 369-401
- 218 All-optical AND and XOR logic gates in a single device. **2002**,
- 217 Carrier Dynamics in Semiconductors under MIR FEL Excitation. **2003**, 31, 818-823
- 216 Conclusions. **2003**, 264-264
- 215 Fabrication techniques and methods for semiconductor quantum dots. **2003**, 45-61 0
- 214 Power characteristics of quantum dot lasers. **2003**, 202-225
- 213 Quantum dot vertical-cavity surface-emitting lasers. **2003**, 226-263
- 212 Long-wavelength emitters on GaAs. **2003**, 155-201
- 211 Introduction. **2003**, 3-44
- 210 Structural and electronic properties of self-organized quantum dots. **2003**, 62-102 1
- 209 Optical gain and threshold characteristics of a self-organized quantum dot diode laser. **2003**, 105-129

- 208 Reduced Phonon Scattering in an Asymmetric Triple Barrier Resonant-Tunneling Diode at High Magnetic Fields. **2006**, 75, 114702
- 207 The Einstein Relation in Bulk Specimens of Compound Semiconductors. **2009**, 13-50
- 206 Photoemission from Bulk Optoelectronic Materials. **2009**, 219-235 2
- 205 Optical Properties of InN and Related Alloys. **2009**, 243-272
- 204 Impact of Photoelastic Effect on Phase-Matching Wavelengths in Periodically-Inverted AlGaAs Waveguides. **2011**,
- 203 Field Emission from Quantum Wires of Nonparabolic Semiconductors. **2012**, 3-70
- 202 The EEM in Ultrathin Films (UFs) of Nonparabolic Semiconductors. **2012**, 3-72
- 201 MOVPE Processes. **2012**, 27-53
- 200 Nonlinear Optics and Saturation Behavior of Quantum Dot Samples Under Continuous Wave Driving. **2012**, 251-295 0
- 199 Appendix Eleven: Strained Bandgaps. 647-656
- 198 Optical Properties and Charge Transport.
- 197 Suggestion for Experimental Determinations of 2D and 3D DSLs and Few Related Applications. **2014**, 213-250
- 196 Surface and interface phonon-polaritons in four layer systems consisting of polar ternary mixed crystals. **2014**, 63, 107105
- 195 Semiconductor Materials. **2014**, 1-66
- 194 Analytical Evaluation of Energy and Electron Concentrations in Quantum Wells of the High Electron Mobility Transistors. **2014**, 04, 137-141
- 193 Towards the Quantum Computer: Information Processing with Single Electrons. **1987**, 154-165
- 192 New Developments and Recent References. **1987**, 653-654
- 191 SIMULATIONS OF NONLINEAR TRANSPORT IN AlGaAs/GaAs SINGLE WELL HETEROSTRUCTURES. **1988**, 349-350

- 190 Ausbreitung elektromagnetischer Wellen. **1989**, 19-47
- 189 Photoemission from AlGaAs/GaAs Heterojunctions and Quantum Wells under Negative Electron Affinity Conditions. **1989**, 317-332
- 188 Monte-Carlo Simulation of Femtosecond Carrier Relaxation in Semiconductor Quantum Wells. **1989**, 561-584
- 187 Indirect GaAs/AlAs Superlattices. **1989**, 293-304
- 186 Postgrowth Characterization Methods. **1989**, 159-214
- 185 Direct Time-Resolved Observation of Coherent-Phonon Oscillations in III-V Compounds. **1990**, 337-339
- 184 Formation of AlGaAs by ion beam mixing of Al films on GaAs. **1990**, 48, 690-691
- 183 Charge Buildup, Intrinsic Bistability and Energy Relaxation in Resonant Tunneling Structures: High Pressure and Magnetic Field Studies. **1991**, 229-242 1
- 182 Technology for III/V-Semiconductor HFET Devices. **1991**, 277-313
- 181 Advances in Nonradiative Processes in Semiconductors. **1991**, 197-217
- 180 Time-Resolved Resonant Tunneling between GaAs/Al_{0.35}Ga_{0.65}As Quantum Wells: A Coherent Process?. **1991**, 319-329
- 179 Mechanism of σ Electron Transfer in Type II (Al)GaAs/AlAs Superlattices and Multiple Quantum well Structures. **1991**, 191-199
- 178 Materials for Waveguide Optoelectronics. **1992**, 1-19
- 177 Monte Carlo Simulation of GaAs_{1-x}Ga_x as Field-Effect Transistors. **1992**, 235-275
- 176 Ausbreitung elektromagnetischer Wellen. **1992**, 19-47
- 175 Physikalische Grundlagen optoelektronischer Halbleiterbauelemente. **1992**, 17-97
- 174 An AlGaAs/GaAs OEIC structure for the integration of LEDs, MESFETs and photodetectors. **1993**, 300-303
- 173 ACOUSTO-OPTIC MODULATOR USING A PIEZOELECTRIC FILM OVER GaAs/AlGaAs MQW STRUCTURE. **1993**, 73-76

172 HBT Modelling. **1993**, 74-88

171 Propagation of Electromagnetic Waves. **1993**, 19-47

170 Magneto-Polaron Effect on Shallow Donors in 3D and Q2D Systems. **1993**, 173-184

169 Evaluation of Effective Device Parameters by Comparison of Measured and Simulated C-V Characteristics for Conventional and Pseudomorphic HEMTs. **1993**, 461-464

3

168 Enhanced Linear Electro-Optic Anisotropy in GaAs Quantum Wells. **1993**, 239-245

167 Synthesis of Optical Interconnects and Logic Gates. **1995**, 177-186

166 Dünnschichtsolarzellen. **1995**, 155-233

165 Dynamics of Optical Excitations in Semiconductors. **1995**, 15-56

164 Thermodynamics of Microwave Devices. **1995**, 137-166

163 Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. **1996**, 99-147

162 Electro-optic Effects in Optoelectronic Materials. **1996**, 101-130

161 Hot-Electron Scattering from Electron-Hole Plasma and Coupled Plasmon-Lo-Phonon Modes in GaAs Quantum Wires. **1996**, 265-267

160 Thermal Characterization of Multistriple Heterostructure Lasers. **1997**, 167-177

159 Component Evaporation, Defect Annealing, and Impurity Diffusion in the III-V Semiconductors. **1997**, 113-148

158 Material-Charakterisierung von Halbleiter-Heterostrukturen. **1997**, 69-91

157 Material Issues for New Devices. **1997**, 193-201

1

156 Halbleiter-Materialsysteme. **1997**, 3-17

155 Polar optical modes in layered structures. **1998**, 83-122

- 154 Phonons in bulk crystals. **1998**, 1-11
- 153 Study of coherent folded acoustic phonons in GaAs/AlAs superlattices by two-color pump-probe technique. **1998**, 269-271
- 152 Aluminum Gallium Arsenide (Al_xGa_{1-x}As). **1998**, 513-558 1
- 151 General Remarks. **1999**, 279-286
- 150 Aluminum Arsenide (AlAs). **1999**, 156-165
- 149 The ER in Quantum Wells of HD Non-parabolic Semiconductors. **2015**, 1-116
- 148 The EP from Quantum Wells (QWs) of Heavily Doped (HD) Non-parabolic Semiconductors. **2015**, 3-137
- 147 Concentration, And Temperature Dependences Of Exciton Transition Energies In Al_xGa_{1-x}As/GaAs/Al_xGa_{1-x}As Nanofilms. **2015**, 60, 458-467
- 146 Heterostructure-based diode with the cathode static domain. **2015**, 20, 66-71 1
- 145 Chemical Vapor Epitaxy of Al_xGa_{1-x}As. **2016**,
- 144 Elasticity and Phonons. **2017**, 1-40
- 143 Elasticity and Phonons. **2018**, 111-150 1
- 142 Ultra-small mechanical deformation sensor using a hybrid fiber optic-based triangular photonic crystal structure. **2018**,
- 141 Ultrafast Time-Domain Spectrometer in the 25 T Split Florida-Helix Magnet. **2019**,
- 140 Design and fabrication of 940 nm vertical-cavity surface-emitting lasers. **2019**, 68, 064207 1
- 139 VENUS: a comprehensive electro-thermo-opto VCSEL simulator. **2019**, 0
- 138 Exploring the formation of thermally detuned transverse patterns in a broad-area square VCSEL. **2019**, 44, 3034-3037 1
- 137 50GHz gallium arsenide electro-optic modulators for spaceborne telecommunications. **2019**, 4

- 136 Evaluation of heat dissipation characteristics of quantum cascade laser with diamond submount using structure function and three-dimensional thermal fluid simulation.
- 135 Comparison of the magneto-optical properties of the semi-parabolic well with those of the parabolic and rectangular wells under the combined influences of aluminum concentration and hydrostatic pressure. **2021**, 161, 110456 1
- 134 Engineering AlGaAs-on-insulator toward quantum optical applications. **2020**, 45, 6763-6766 1
- 133 The effect of hydrostatic pressure on binding energy and polaron effect of bound polaron in wurtzite $\text{Al}_y\text{Ga}_{1-y}\text{N}/\text{Al}_x\text{Ga}_{1-x}\text{N}$ parabolic quantum well. **2021**, 35, 2150008
- 132 Piezoelectric III-V and II-VI Semiconductors. **2022**, 35-49 1
- 131 Electronic Properties of Heterostructures. **2020**, 115-175
- 130 Effect of different oxide surroundings on terahertz radiation absorption in GaAs quantum dot. **2020**,
- 129 Elasticity and Phonons. **2020**, 1-40
- 128 Optical Properties of Compound Semiconductor Heterostructures. **2020**, 289-337
- 127 Impact Ionization in Graded Gap Transferred Electron Diode. **2021**,
- 126 Fully Analytical Compact Model for the I-V Characteristics of Resonant Tunneling Diodes. **2021**, 1
- 125 Influence of piezoelectricity, doping and magnetostatic field on Brillouin amplification in compound (AIIIBV and AIIIVI) semiconductors. 0
- 124 Enhanced efficiency of graded-bandgap thin-film solar cells due to concentrated sunlight.. **2021**, 60, 10570-10578 0
- 123 Nonlinear Dielectric Nanoantennas and Metasurfaces: Frequency Conversion and Wavefront Control. 9
- 122 Influence of pressure and temperature on mechanical and thermal behaviors of InAsSb and GaAsSb alloys. **2021**, 96, 125718 2
- 121 Effect of magnetic field, size and donor position on the absorption coefficients related a donor within the core/shell/shell quantum dot. **2021**, 53, 1 1
- 120 Fast Control of Quantum States in Quantum Dots: Limits due to Decoherence. **2005**, 301-315
- 119 Aluminum - Lithium. 19-31

118 2.1.12 AlAs. 38-41

117 General Introduction. 1-47

116 General Introduction. 1-47

115 Gallium arsenide (GaAs), conduction band effective masses and related parameters. 1-12

114 Al(x)Ga(1-x)As, band structure, energy gaps. 1-5

113 Al(x)Ga(1-x)As, optical properties. 1-28

112 Aluminum arsenide (AlAs), intra- and interband transition energies, spin-orbit splitting. 1-5

111 Electrical-stress driven oxidation in 940 nm oxide-confined VCSEL.

1

110 Wavelength temperature insensitivity of surface-trapped optical modes in microcavities. **2021**, 29, 41990

1

109 Thermal processes contributions to the temperature dependence of the energy gap in dilute bismuth III-V alloys. **2022**, 343, 114649

0

108 Rashba effect in cylindrical quantum well wire with finite confining potential. 1

107 Transport Properties of the $\text{LaInO}_3/\text{BaSnO}_3$ Interface Analyzed by Poisson-Schrödinger Equation. **2022**, 17,

4

106 Unit cell distortion and surface morphology diversification in a $\text{SnTe}/\text{CdTe}(001)$ topological crystalline insulator heterostructure: influence of defect azimuthal distribution.

2

105 Optical properties of 87Rb atomic vapor near the 1D photonic crystal bandgap and all-optical switching of transmitted light. **2022**, 97, 035503

0

104 Spectral tuning in quantum rings by magnetic field: detection from NIR to FIR regime. **2022**, 54, 1

103 Thermo-optical reshaping of second-harmonic emission from dimer all-dielectric nanoresonators.. **2022**, 47, 1992-1995

0

102 Modeling free-carrier absorption in ultrathin III-V solar cells with light management.. **2022**, 30, 7096-7109

1

101 Effect of the nonparabolicity on the resonant lifetimes and resonant energies of symmetric GaAs/ $\text{Al}_x\text{Ga}_{1-x}\text{As}$ double barrier nanostructures. **2022**, 632, 413711

1

- 100 The HUP and the ES in Quantum Wells (QWs) of HD Non-parabolic Materials. **2022**, 87-108
- 99 Geometrical Optimization of Gallium Arsenide (GaAs) nanostructure based Solar Cells. **2022**, 0
- 98 Thermal response of electronic, optical, mechanical properties, phonon frequencies, and sound velocity of $\text{InP}_x\text{As}_y\text{Sb}_{1-x-y}/\text{InAs}$ quaternary semiconductor system. **2022**, 54, 1
- 97 First principles study the effect of Zn doped MgO on the energy band gap using GGA approximation. **2022**, 18, 11-20 1
- 96 Impact of Substrates on the Electronic and Mechanical Properties of $\text{Al}_x\text{In}_{1-x}\text{PySb}_{1-y}$ Alloys. 1 0
- 95 A theoretical study of the effects of ThomasFermi and Hermanson's dielectric functions and temperature on photoionization cross-section of a donor impurity in GaAs quantum dots of circular and rectangular cross-sections. **2022**, 95, 1
- 94 Record-quality GaAs two-dimensional hole systems. **2022**, 6, 1
- 93 Carrier dynamics of AlGaAs/AlAs asymmetric double quantum wells with different barrier thickness. **2022**, 12, 1291
- 92 Review of the mechanisms for the phonon bottleneck effect in III-V semiconductors and their application for efficient hot carrier solar cells. 2
- 91 Intersubband absorption linewidth in a semi-parabolic quantum well: Comparison among three different phonon models. **2022**, 413901 2
- 90 Impacts of KF Post-Deposition Treatment on the Band Alignment of Epitaxial Cu(In,Ga)Se Heterojunctions.. **2022**, 0
- 89 Two-dimensional XY monolayers (X = Al, Ga, In; Y = N, P, As) with a double layer hexagonal structure: A first-principles perspective. **2022**, 590, 152998 3
- 88 Investigation of the low contact resistance via alloying of Au/Ni/AuGe-GaAs contact structures. **2022**, 318, 132140
- 87 Characteristics of 1520 nm InGaAs multijunction laser power converters. **2021**, 119, 243902 5
- 86 Mid-Infrared Frequency Generation via Intermodal Difference Frequency Generation in AlGaAs-On-Insulator Waveguides. **2022**, 2, 0
- 85 Degree of Polarization of High-Power Laser Diodes: Modeling and Statistical Experimental Investigation. **2022**, 12, 3253 1
- 84 Tunneling in matched AlGaAs/GaAsBiN superlattices. **2022**, 128, 1 0
- 83 Active multi-mode interferometer semiconductor optical amplifier on quantum-dots toward high saturated output power under high temperature.

- 82 Chiral quantum optics in broken-symmetry and topological photonic crystal waveguides. **2022**, 4, 2
- 81 Evaluation of the external electric- and magnetic field-driven mathieu quantum dot's optical observables. **2022**, 413991 0
- 80 Enhanced performance of GaAs-based betavoltaic batteries by using AlGaAs hole/electron transport layers. **2022**, 55, 304002
- 79 Combined influences of temperature, pressure, and alloy-composition on magneto-optical properties of the semi-parabolic well under all four different phonon models. **2022**, 207236 0
- 78 Density functional study of electronic, elastic and optical properties of GaAs_{1-x}N_x (x=0, 0.25. **2022**, 31, e00689
- 77 Exciton properties, optical phonon modes, polaron characteristics and plasma frequency of GaSb upon compression. **2022**, 147, 106694 0
- 76 Cyclotron resonance linewidth due to electron scattering by five different phonon modes in semiparabolic quantum wells. **2022**, 167, 110757 0
- 75 Improvement of thermal resistance in InGaAs/GaAs/AlGaAs microdisk lasers bonded onto silicon. 1
- 74 Hole-Confined Polar Optical Phonon Interaction in Al_{0.35}Ga_{0.65}As/GaAs/Al_{0.25}Ga_{0.75}As Quantum Wells. **2022**, 7, 82-86
- 73 Nonlinear electron mobility due to asymmetric doping in V-shaped double quantum well FET structure. 1
- 72 Shallow-donor impurity effects on the far infrared electron-electron optical absorption coefficient in single and core/shell spherical quantum dots with Konwent-like confinement potential. **2022**, 54, 0
- 71 Homogeneous Photon-Absorbing Layer. **2021**, 55-82
- 70 Elasticity and Phonons. **2022**, 1-43
- 69 Optical absorption engineering in two-dimensional quantum rings: design and optimization for FIR to MIR detection applications. **2022**, 54, 0
- 68 Theoretical study of 1D gradient photonic structures with quartic polynomial dielectric profile formed by AlGa_{1-l}As varying pressure and temperature under oblique incidence. **2022**,
- 67 Improving the Performance of Direct Bonded Five-Junction Solar Cells by Optimization of AlInP Window Layer. **2022**, 9, 404 0
- 66 Hot Electron Transport in N-Type Modulation-Doped Al_{0.15}Ga_{0.85}As/GaAs_{0.96}Bi_{0.4} Quantum Well Structure.
- 65 On-Demand Source of Dual-Rail Photon Pairs Based on Chiral Interaction in a Nanophotonic Waveguide. **2022**, 3, 1

- 64 TRANSIT TIME MODEL ANALYSIS THROUGH THE BASIS IN THE CASE OF DRIFT TRANSISTORS HBT. **2022**, 22, 507-516
- 63 Modulated Photoluminescence at Low Temperature Measurements with Controlled Electron Concentration in Asymmetric GaAs/GaAlAs/GaAs Quantum Wells. **2022**, 250, 119109
- 62 Optical dielectric function and Electronic Band structure of Dilute GaAsBi-GaAs Multiquantum wells by Using Variable Angle Spectroscopic Ellipsometry. **2022**, 169745
- 61 Response of mechanical and optoelectronic properties for $\text{InP}_x\text{As}_y\text{Sb}_{1-x-y}/\text{InAs}$ system to composition.
- 60 Signature of miniband nodes in magneto-optical properties of one-dimensional superlattice of planar quantum rings. **2022**, 448, 128324
- 59 Series on Semiconductor Science and Technology. **2003**, i-i
- 58 Copyright Page. **2003**, iv-iv
- 57 Preface. **2003**, vii-ix
- 56 Photonic Materials Cloud: An Online Interactive Open Tool for Creating, Comparing, and Testing Photonic Materials. **2022**, 12, 2585
- 55 Group III-V semiconductors as promising nonlinear integrated photonic platforms. **2022**, 7, ○
- 54 Nonlinear optical characteristics of thermodynamic effects- and electric field-triggered Mathieu quantum dot. **2022**, 207371 ○
- 53 Simulation of an AlGaInAs/InP Electro-Absorption Modulator Monolithically Integrated with Sidewall Grating Distributed Feedback Laser by Quantum Well Intermixing. **2022**, 9, 564 1
- 52 Effects of hydrostatic pressure and temperature on the nonlinear optical properties of GaAs/GaAlAs zigzag quantum well. 1-16
- 51 The spatial electric field effect on the impurity binding energy and self-polarization in a double quantum dot. **2022**, 137, 1
- 50 Very long wave infrared quantum cascade detector with a twin-well absorption region. **2022**, 121, 061101 ○
- 49 Performance optimization of AlGaAs/GaAsBiN resonant tunneling diode. **2022**, 268, 169793 ○
- 48 Modulation of Electronic Properties in Double Quantum Well-Based FET Structure. **2023**, 79-88 ○
- 47 Critical Role of Terminating Layer in Formation of 2DEG State at the $\text{LaInO}_3/\text{BaSnO}_3$ Interface. 2201781 ○

- 46 Joule heating and the thermal conductivity of a two-dimensional electron gas at cryogenic temperatures studied by modified 3D method. **2022**, 132, 104302 ○
- 45 Features of impact ionization occurring in semiconductor compounds InGaN and InAlN. **2021**, 19-28 ○
- 44 Energy spectrum and interlevel transitions within the conduction band of a D_{2^+} complex confined in a spherical quantum dot. **2022**, 54, ○
- 43 Metal-Semiconductor AsSb-Al_{0.6}Ga_{0.4}As_{0.97}Sb_{0.03} Metamaterial. **2022**, 15, 7597 1
- 42 GaAs a model system to study the role of electron-phonon coupling on ionization stimulated damage recovery. **2022**, 55, 505301 ○
- 41 Improving the efficiency of a GaInP solar cell using an AlGaAs buffer layer by optimizing the thicknesses of the PN junction. **2022**, 17, 1191-1202 ○
- 40 Comprehensive analysis of hot electron transport in as-grown and thermally annealed n-type modulation-doped Al_{0.15}Ga_{0.85}As/GaAs_{0.96}Bi_{0.4} quantum well structure. **2023**, 154, 107227 ○
- 39 Influence of Molar Composition on Electron Mobility in Solid Solution AlGaAs. **2022**, ○
- 38 Applications of Optical Microcombs. ○
- 37 Entanglement of three-level atomic system and spontaneous emission fields in a vacuum and near the 1D photonic crystal band gap. **2022**, 18, 687-693 ○
- 36 Analytical Physics-Based Compact Current-Voltage Model for 2D-2D Resonant Tunneling Diodes. **2022**, 21, 752-762 ○
- 35 Chemical Bath Deposition Grown ZnO Thin Films: Role of Manganese Doping. 76, 107-130 ○
- 34 Numerical modeling of p-i-n GaAs solar cell performance. **2022**, 18, 769-779 ○
- 33 Investigation of GaAlAs photocathode with nanostructures sensitive to narrow band 532 nm wavelength. **2022**, ○
- 32 Pseudo-Potential Calculations of Al_xIn_{1-x}PySb_{1-y} Alloys Under the Effect of Hydrostatic Pressure: Phonon Frequencies and Related Parameters. **2022**, 11, 123007 ○
- 31 Impact of pressure on the resonant energy and resonant frequency for two barriers Ga_{1-x}Al_xAs/GaAs nanostructures. **2023**, 98, 015809 ○
- 30 Reflection-mode nanostructured GaAlAs photocathode with narrow-band response to 532 nm. ○
- 29 Study on electro-optic noise in crystalline coatings toward future gravitational wave detectors. **2023**, 107, ○

- 28 Strain evolution and confinement effect in InAs/AlAs short-period superlattices studied by Raman spectroscopy. **2023**, 13, ○
- 27 Optical properties of Mandelbrot quantum dots: does fractality have an essential effect?. 1-14 ○
- 26 Raman scattering study on dilute nitride-bismide GaNAsBi alloys: behavior of photo-excited LO phonon-plasmon coupled mode. ○
- 25 Computational Investigation of c-GaN/GaAs_x/GaAs Heterojunction Solar Cell. **2023**, 1-7 ○
- 24 Elasticity and Phonons. **2023**, 113-155 ○
- 23 Study on small spacing total internal reflection quantum well infrared focal plane array device. **2023**, ○
- 22 Summary of the design principles of betavoltaics and space applications. **2023**, 293-345 ○
- 21 Cyclotron resonance in the Pöschl-Teller quantum well under the influence of the asymmetric parameters. **2023**, 414724 ○
- 20 BX Transfer in Tunneling through Single AlAs Barriers. **1989**, ○
- 19 Nonlinear Optical Switching in GaAlAs Waveguides. **1989**, ○
- 18 Direct Time Resolved Observation of Coherent Phonon Oscillations in III-V-compounds. **1990**, ○
- 17 Multisubband Electron Mobility in Parabolic Coupled Double Quantum Well Structure. **2022**, ○
- 16 Origins of the short circuit current of a current mismatched multijunction photovoltaic cell. ○
- 15 Non-Hermitian fermions with effective mass. **2023**, 150, 115682 ○
- 14 Simultaneous effects of anisotropy and internuclear distance on the D2+ complex-related self-polarization in quantum dots. **2023**, 659, 414868 ○
- 13 Analysis of mixed optical transitions in dilute magnetic AlAs/GaAs/GaMnAs quantum wells grown on high substrate index by molecular beam epitaxy. **2023**, 290, 116349 ○
- 12 Aluminum nitride photonic integrated circuits: from piezo-optomechanics to nonlinear optics. **2023**, 15, 236 ○
- 11 Plasmonic biosensor with annular aperture array integrated on a resonant cavity LED. **2023**, 535, 129336 ○

- 10 Electronic Optical Bistability in a GaAs/AlGaAs Strip-Loaded Waveguide. **1988**,
- 9 Electron Tunneling Time Measured by Photoluminescence Excitation Correlation Spectroscopy. **1989**,
- 8 Tridimensional electric field effect on diamagnetic susceptibility and polarisability of a donor impurity in a double quantum dot. 1-16
- 7 Impact of thermal oxidation uniformity on 150 mm GaAs- and Ge-substrate VCSELs. **2023**, 56, 154002
- 6 Pressure and temperature influences on the nonlinear optical rectification of an impurity in a symmetrical double quantum dot. **2023**, 138,
- 5 The nonlinear optical rectification and second harmonic generation of a single electron confined in a multilayer spherical quantum dot. **2023**, 55,
- 4 Localized Surface Plasmon Resonance in Metamaterials Composed of As_{1-x}Sb_x Semimetal Nanoparticles in Al_xGa_{1-x}As_{1-y}Sb_y Semiconductor Matrix. **2023**, 13, 1355
- 3 Absorption and emission of longitudinal optical phonons by confined electrons in Pöschl-Teller quantum wells under the effects of the aluminum concentration, temperature, and hydrostatic pressure. **2023**, 179, 111373
- 2 High-harmonic generation from a subwavelength dielectric resonator. **2023**, 9,
- 1 The impact of phosphorus content on the structural, elastic, electronic and dynamic properties of MP As₁-(M = al, Ga, In) alloys: Application in solar cells. **2023**, 662, 414935